

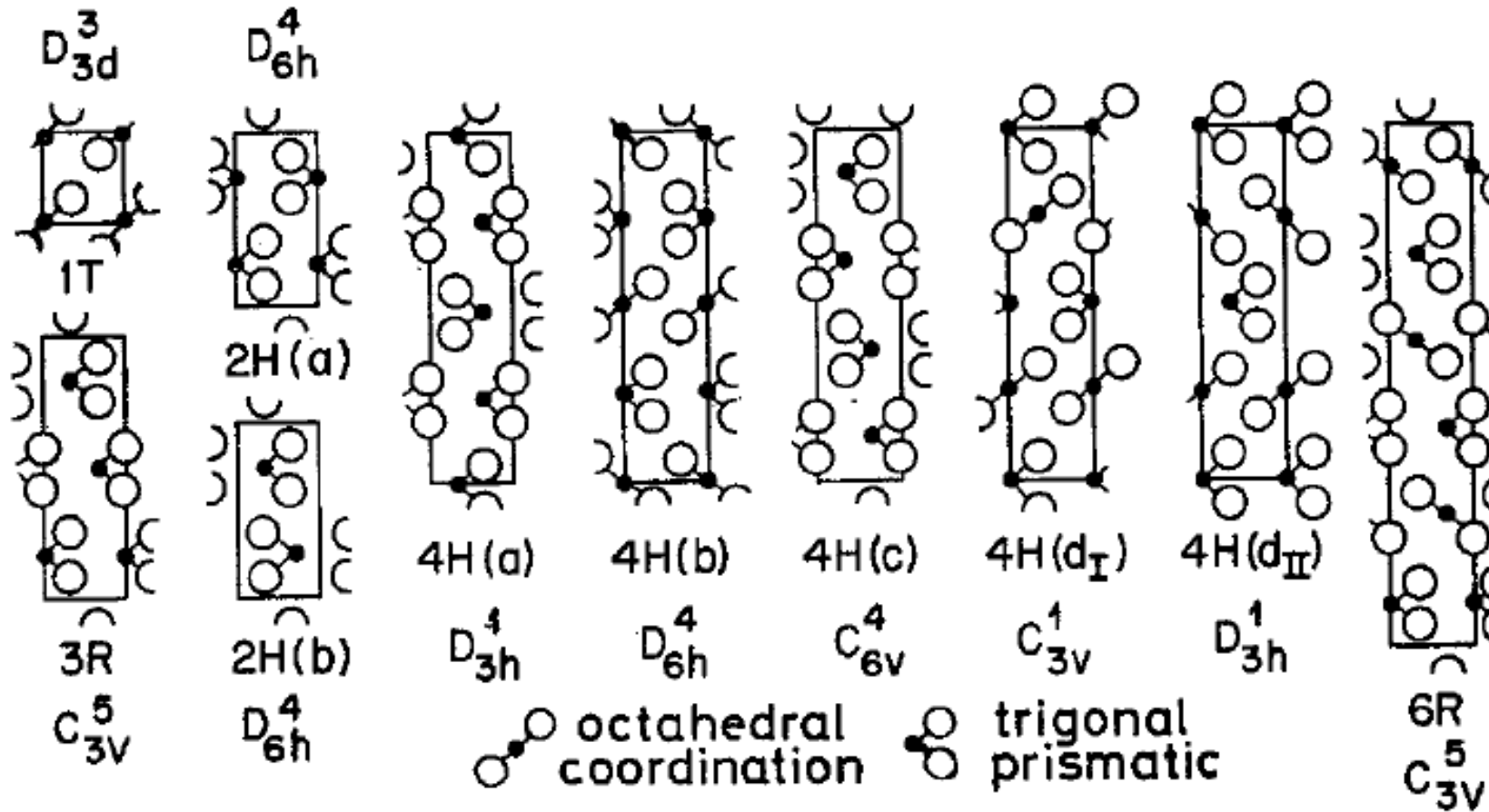
Курс: [Електронна структура та властивості низькорозмірних систем](#)

Лектор: Олександр Кордюк

Лекції 5-6: Хвилі зарядової густини в дихалькогенідах перехідних металів та квазікристали

- Transition metal dichalcogenides: composition, structure, and applications
- Квазідвовимірність та електронна структура
- CDW in TaSe₂: переходи у співрозмірну на неспіврозмірну фази, псевдощілина
- Нестинг, автокореляція та двохчастинкова спектральна функція
- Commensurate vs Incommensurate...
- CDW band gaps
- Плитки Пенроуза та квазікристали

CDW in transition metal dichalcogenides



Various polytypes of the layer structure transition metal dichalcogenides

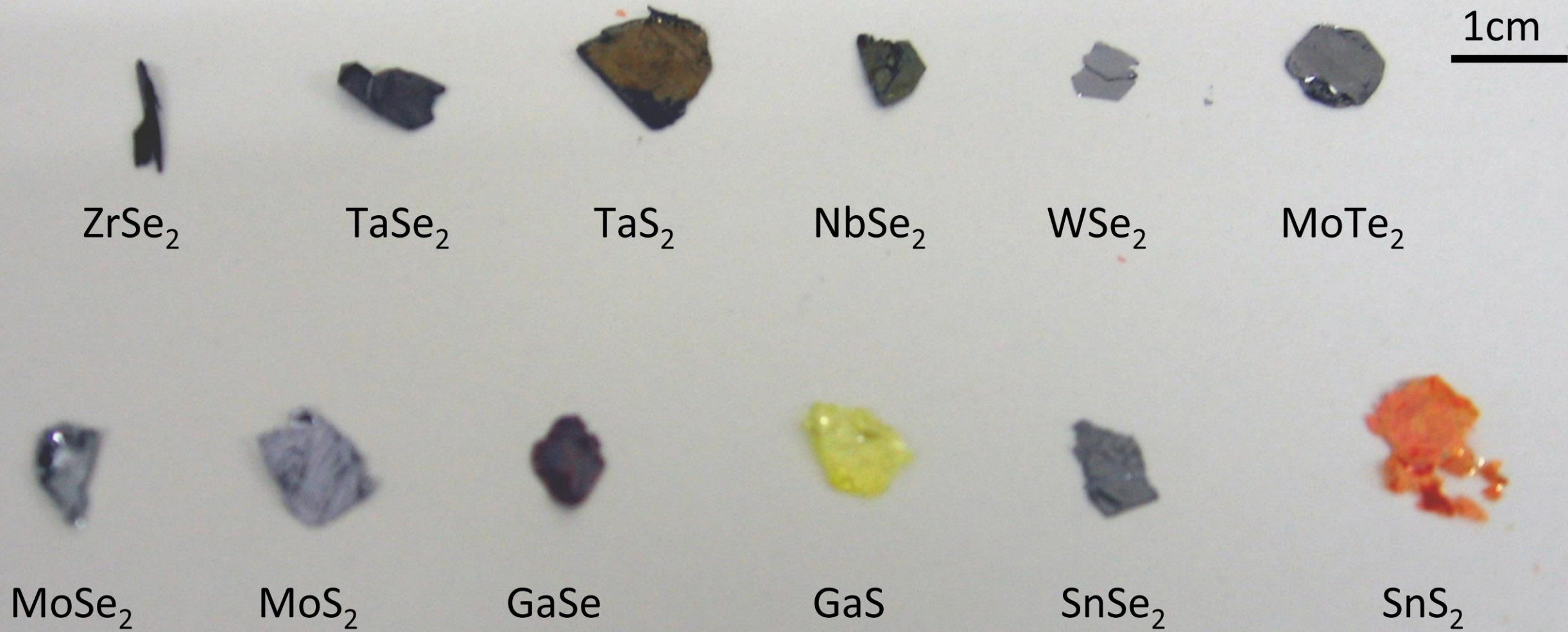
Transition metal dichalcogenides

MX_2 ----- **X = Chalcogen**

M = Transition Metal

H																			He
Li	Be													B	C	N	O	F	Ne
Na	Mg	3	4	5	6	7	8	9	10	11	12		Al	Si	P	S	Cl	Ar	
K	Ca	Sc	Ti	V	Cr	Mn	Fe	Co	Ni	Cu	Zn		Ga	Ge	As	Se	Br	Kr	
Rb	Sr	Y	Zr	Nb	Mo	Tc	Ru	Rh	Pd	Ag	Cd		In	Sn	Sb	Te	I	Xe	
Cs	Ba	La-Lu	Hf	Ta	W	Re	Os	Ir	Pt	Au	Hg		Tl	Pb	Bi	Po	At	Rn	
Fr	Ra	Ac-Lr	Rf	Db	Sg	Bh	Hs	Mt	Ds	Rg	Cn		Uut	Fl	Uup	Lv	Uus	Uuo	

Layered transition metal dichalcogenides

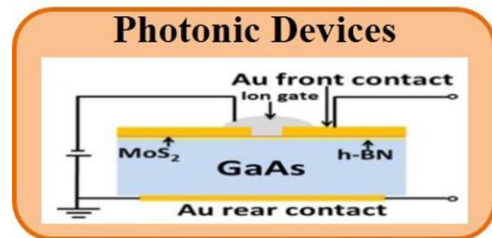


Recent development of 2D transition metal dichalcogenides and their applications



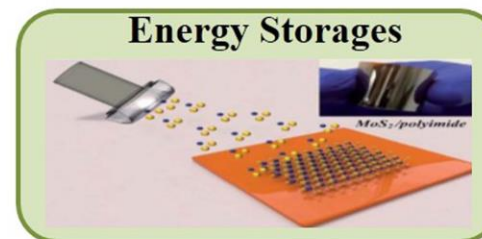
Gas Sensors

- High sensitivity for NO: 1 ppm
- Fast electron transfer rate



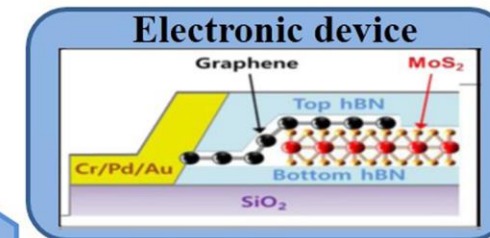
Photonic Devices

- MoS₂/h-BN/GaAs solar cell
- Power conversion efficiency: 9.03%



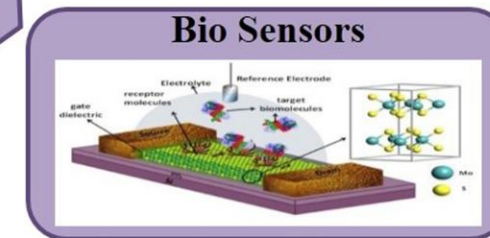
Energy Storages

- Capacitance: $\sim 330\text{F cm}^{-3}$
- Volumetric power: $40 \sim 80\text{ W cm}^{-3}$
- Energy density: $1.6 \sim 2.4\text{ mW h cm}^{-3}$



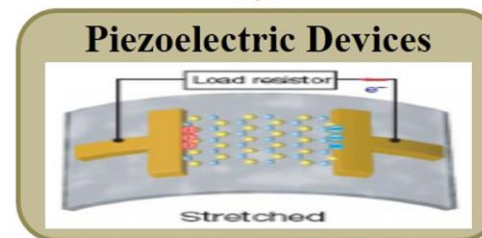
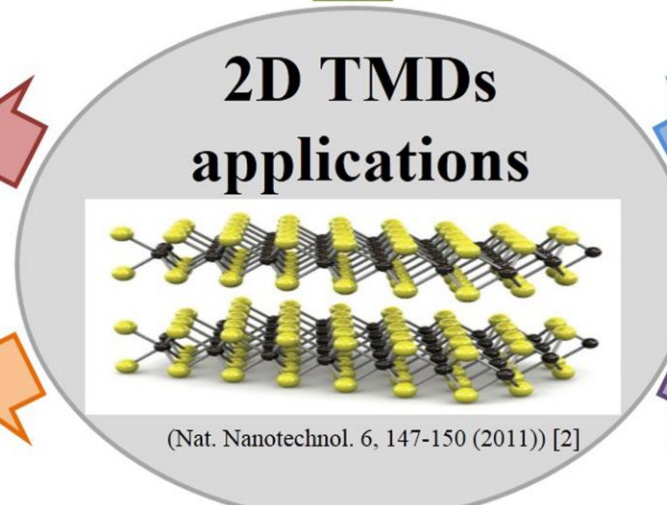
Electronic device

- Hall mobility for monolayer MoS₂ at low temperature: $1,020\text{ cm}^2\text{V}^{-1}\text{s}^{-1}$



Bio Sensors

- High sensitivity of 196 at 100fM concentration for protein .
- High sensitivity of 74 for pH.



Piezoelectric Devices

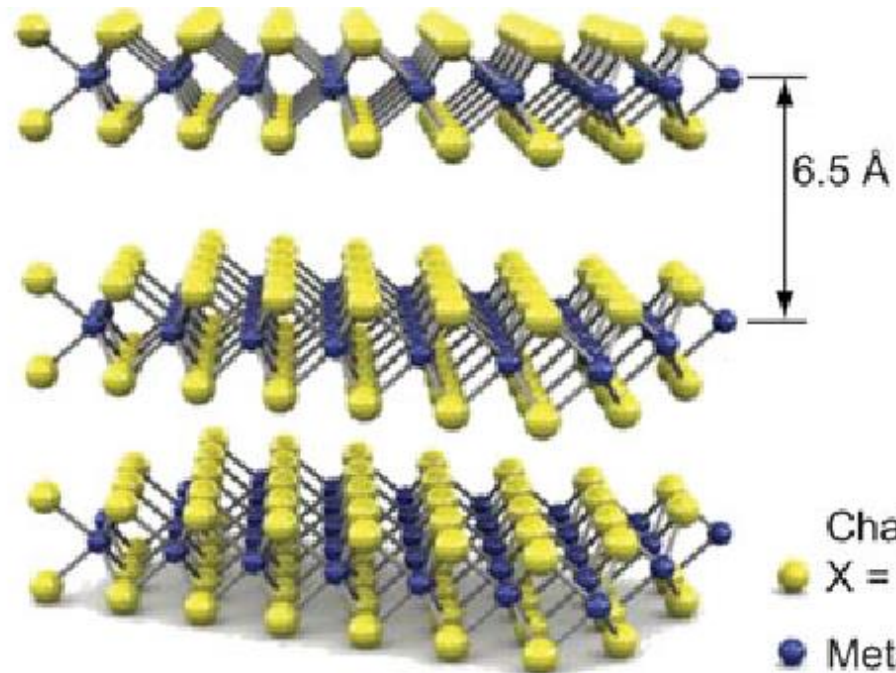
- Power density: 2mWm^{-2}
- Energy conversion: 5.08%

Transition metal dichalcogenides: crystal structure

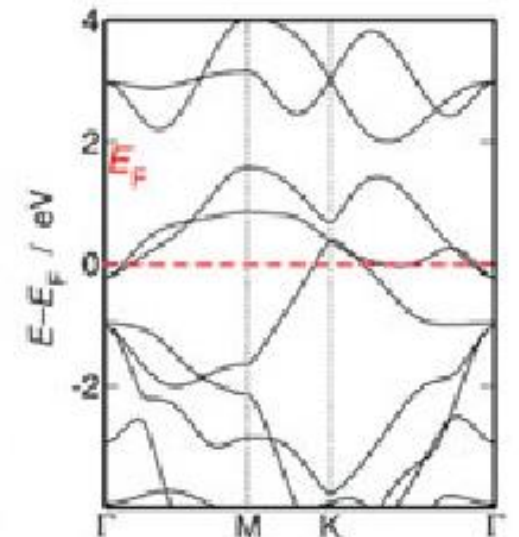
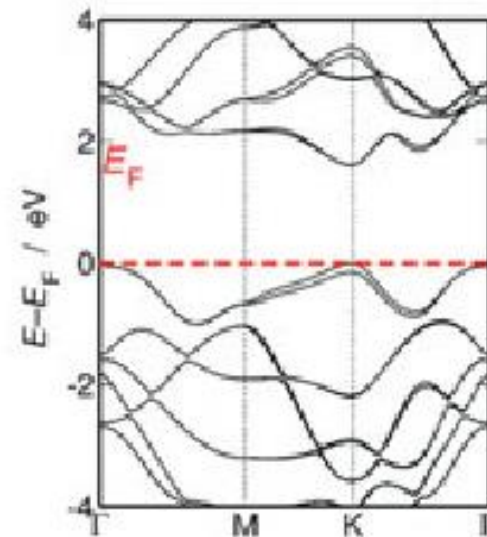
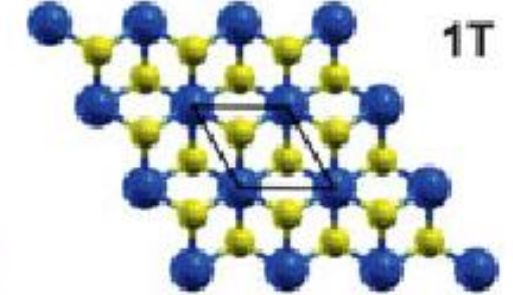
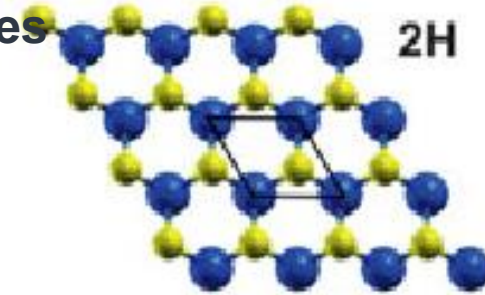
Electronic properties of transition-metal dichalcogenides

A. Kuc (2015) *Mrs Bulletin*

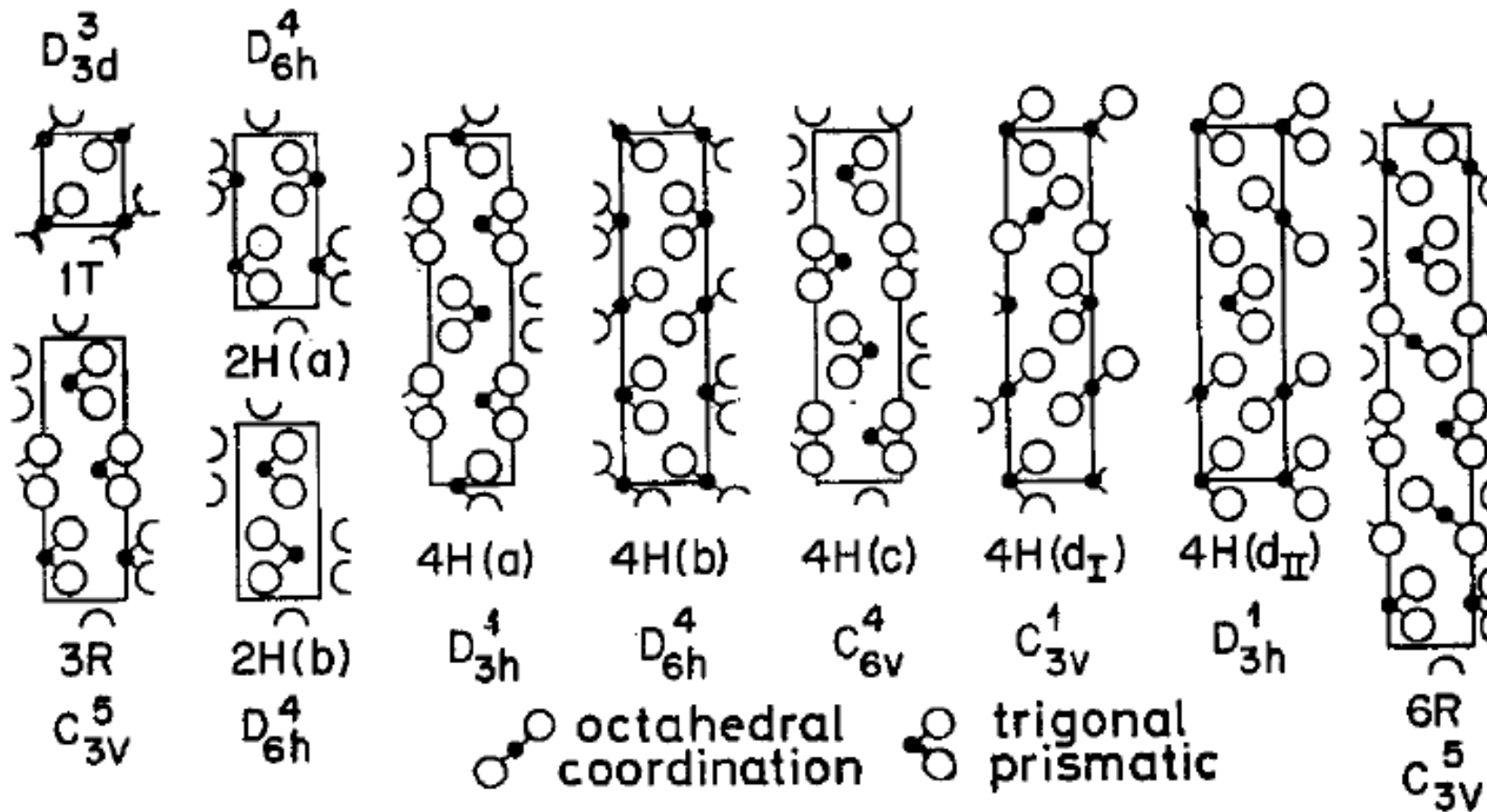
•DOI:[10.1557/MRS.2015.143](https://doi.org/10.1557/MRS.2015.143)



Chalcogenide:
● X = S, Se, Te, ...
● Metal atom:
M = Mo, W, Ti, ...



CDW in transition metal dichalcogenides

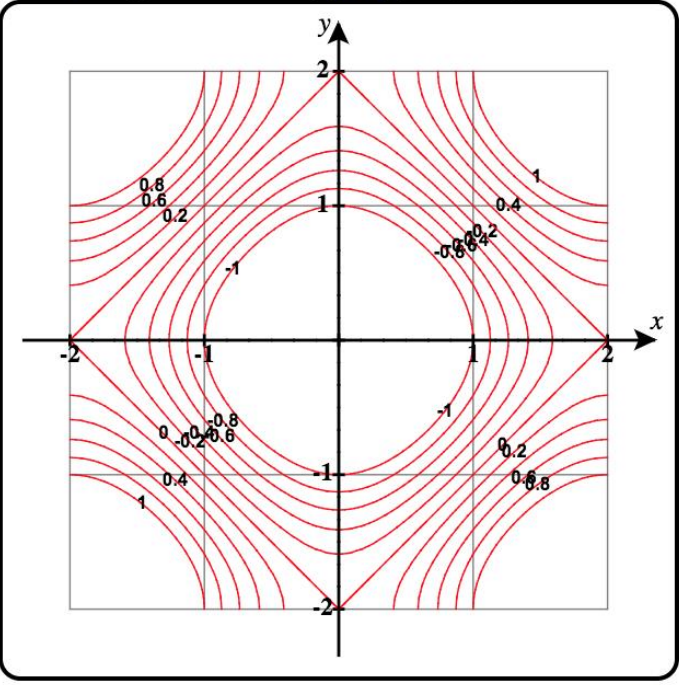


Various polytypes of the layer structure transition metal dichalcogenides



F

Graph 3D Mode



x = 1.963

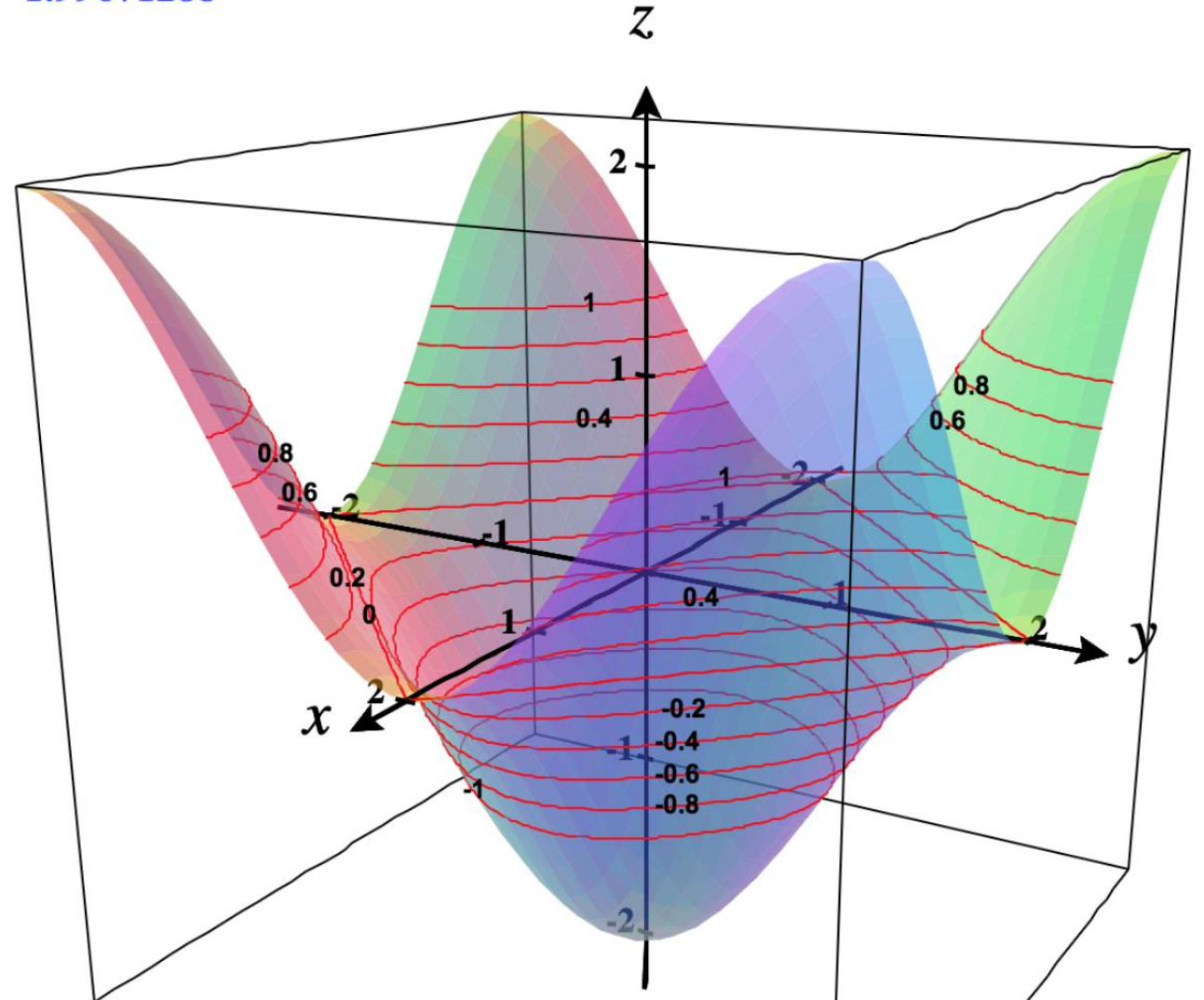
y = 1.963

Add to graph: Select...

z = -cos(pi*x/2)-cos(pi*y/2)

Number of Gridlines 30

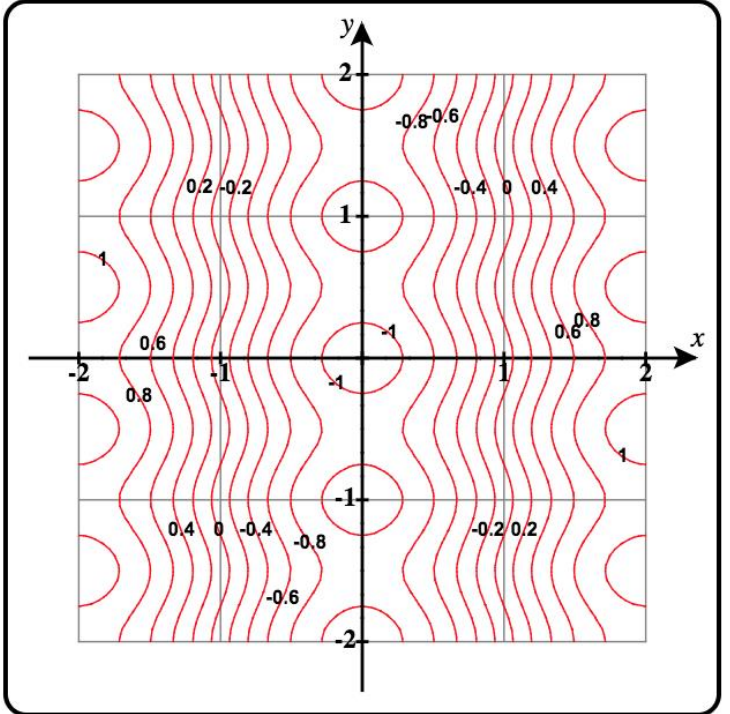
$f(1.9635, 1.9635) = 1.99671288$





F

Graph 3D Mode [grid icons]



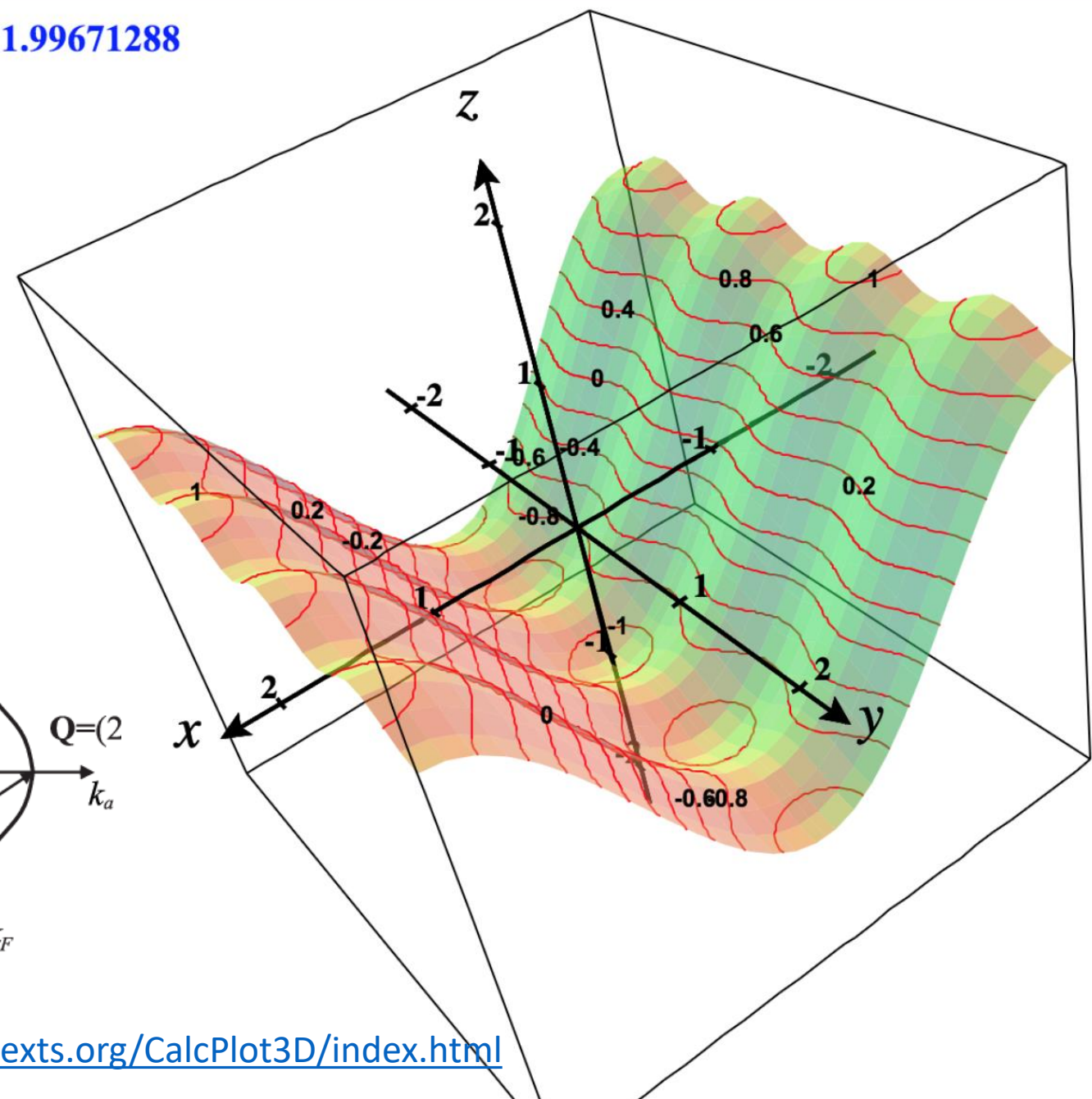
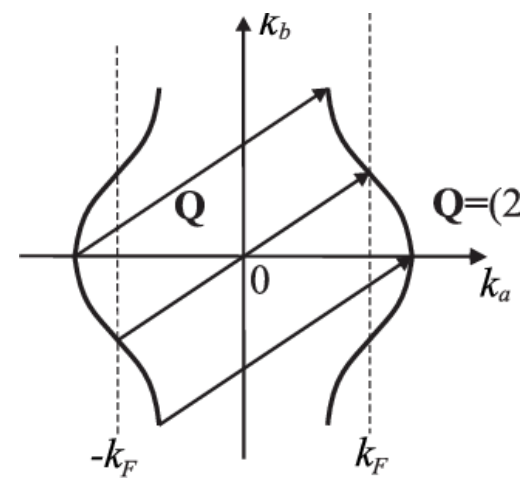
x = 1.963 [slider]
y = 1.963 [slider]

Add to graph: Select...

z = -cos(pi*x/2)-0.1*cos(4*pi*y/2) x

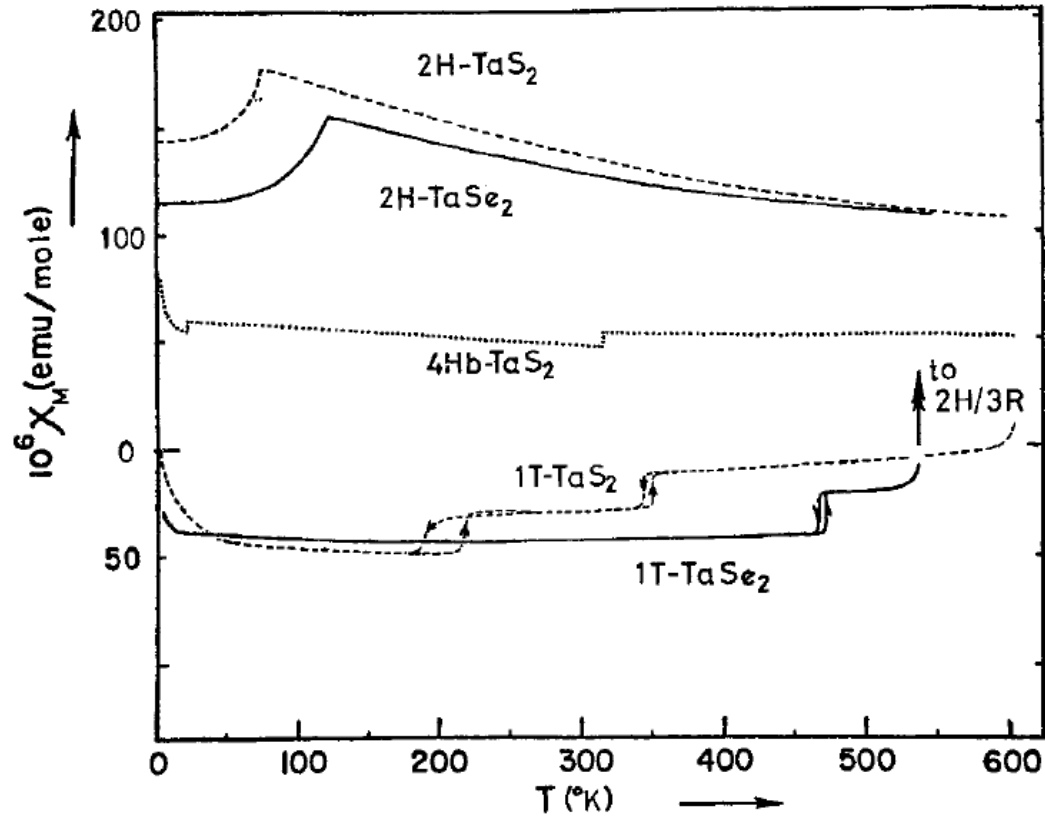
Number of Gridlines 30

$f(1.9635, 1.9635) = 1.99671288$

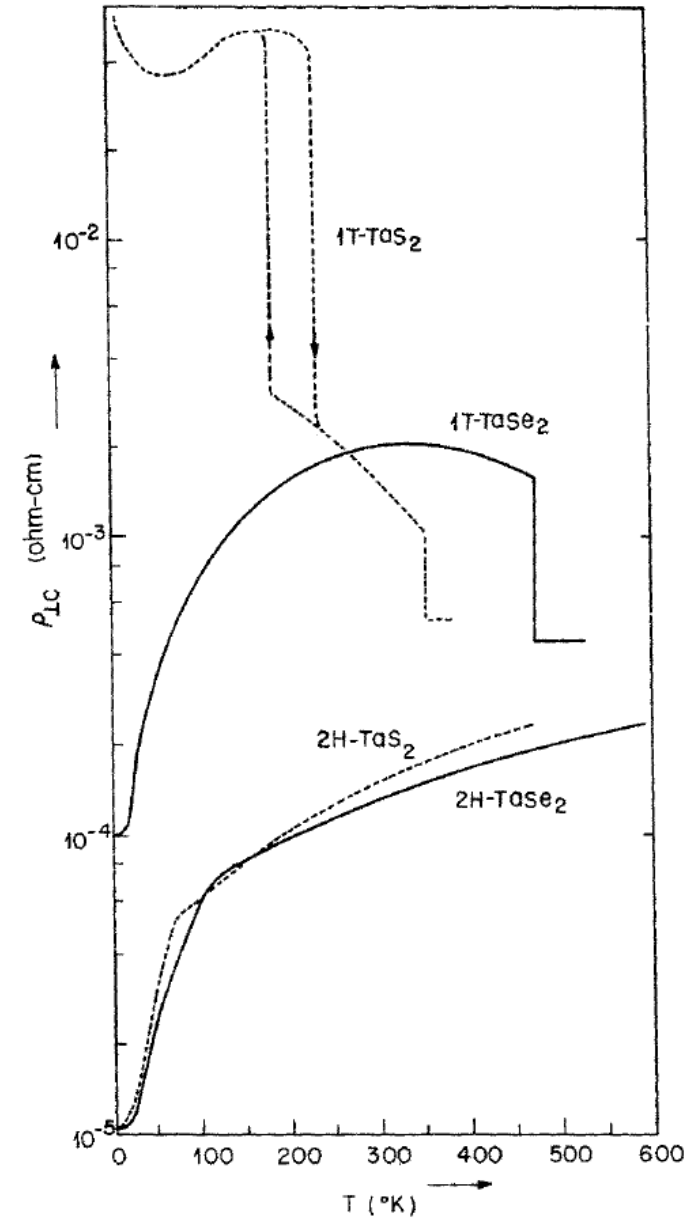


<https://c3d.libretexts.org/CalcPlot3D/index.html>

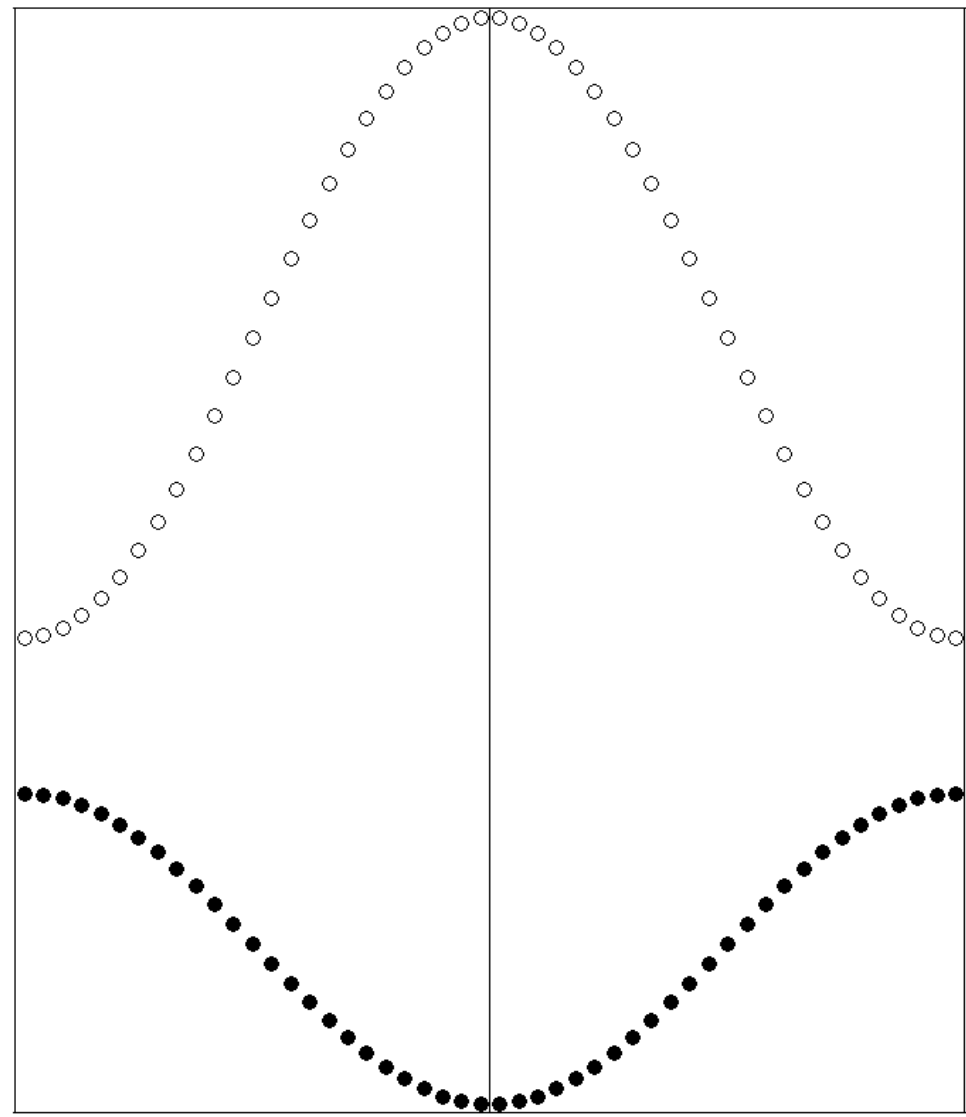
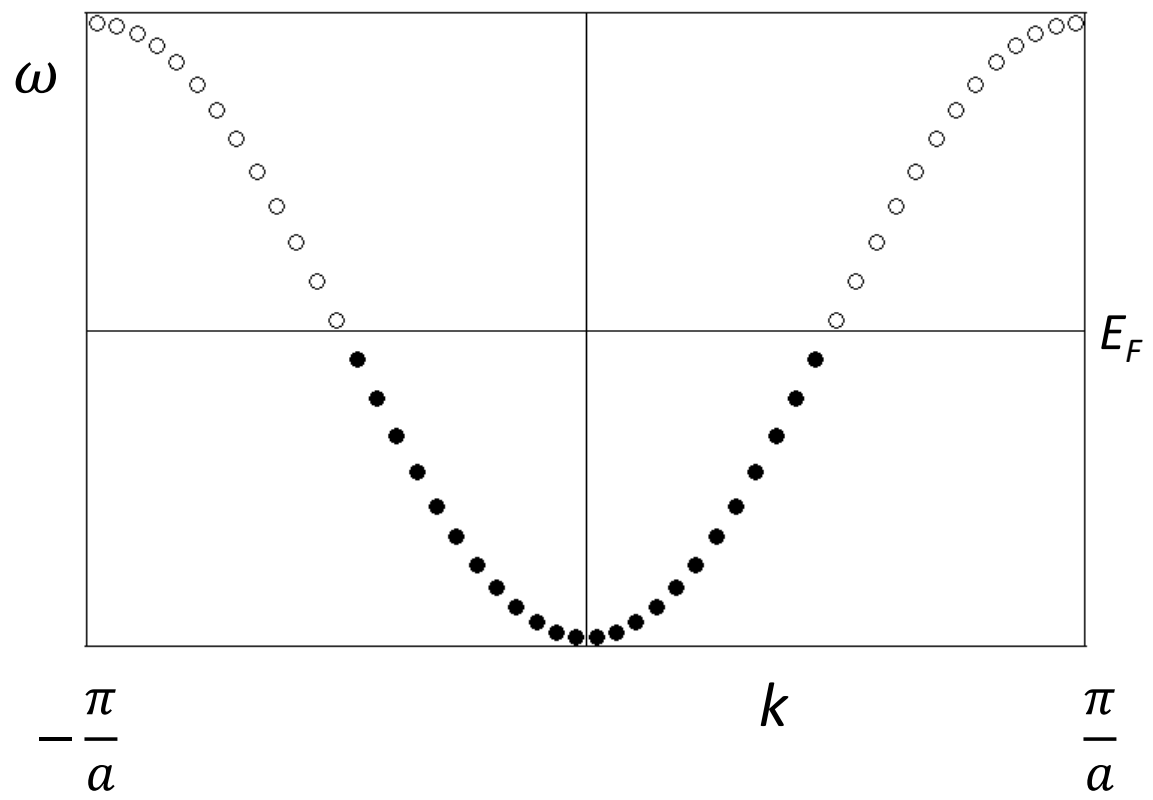
CDW in transition metal dichalcogenides



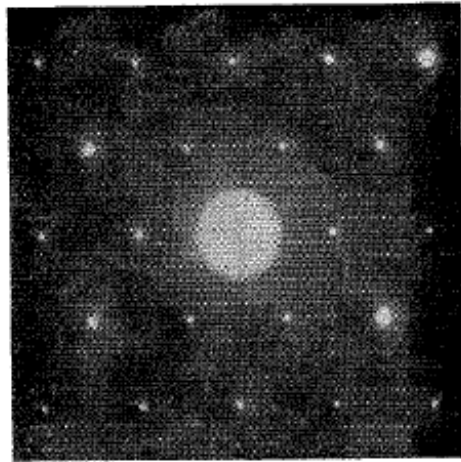
Molar susceptibilities versus T of a variety of tantalum dichalcogenides.



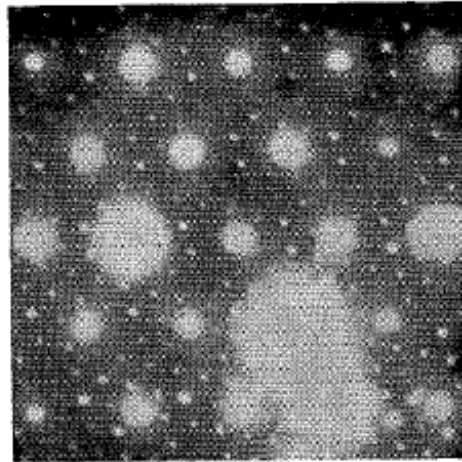
Metal vs Insulator



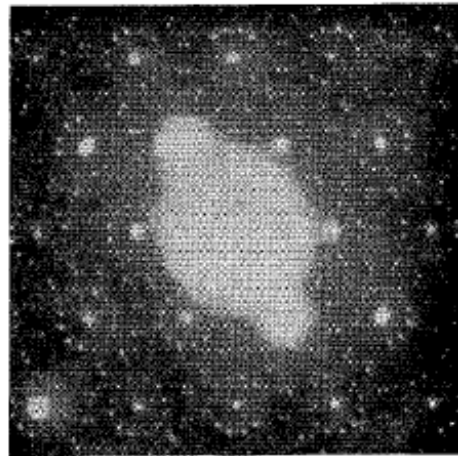
CDW in transition metal dichalcogenides



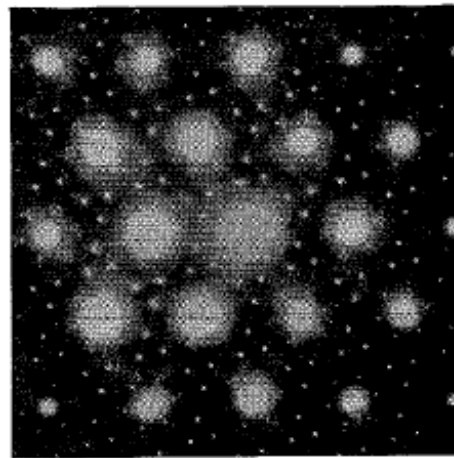
(i)



(ii)



(iii)



(iv)

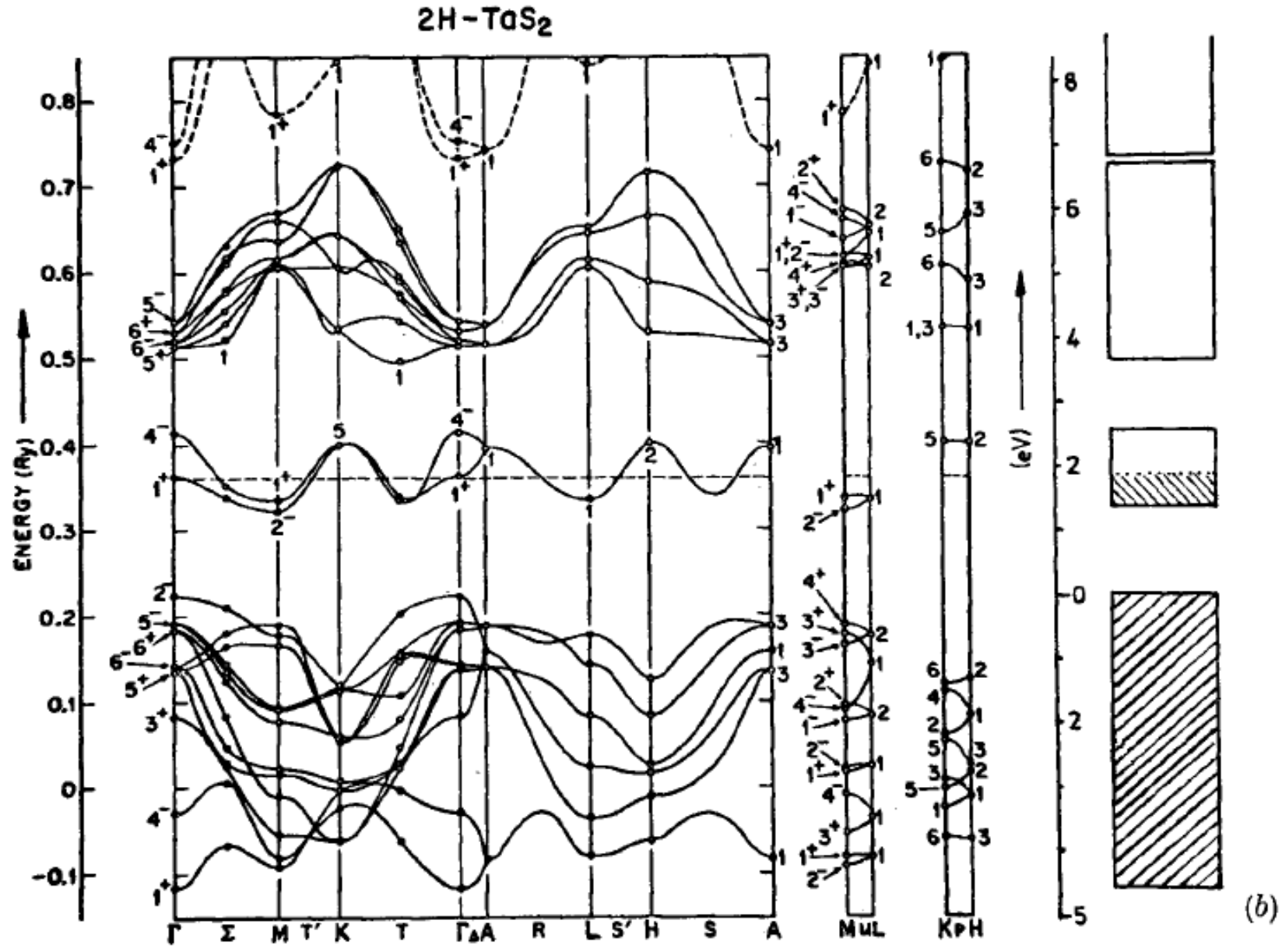
Electron diffraction plates showing superlattice formation. (i) 2H-TaS₂ (300°K).

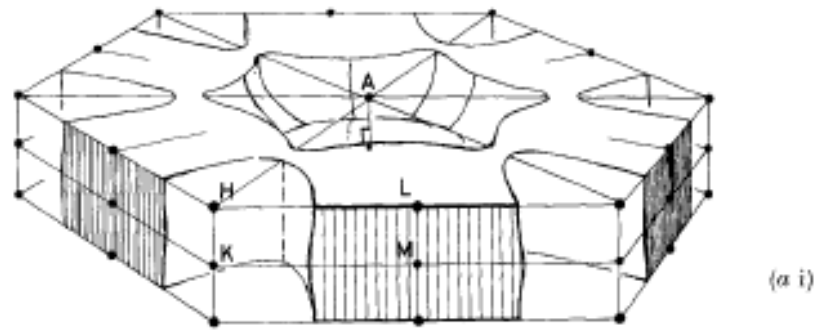
A crystal showing standard a_0 parameter.

(ii) 1T-TaS₂ (300°K). Pattern, for well-oriented sample, from $\sqrt{3} \times \sqrt{3}$ superlattice.

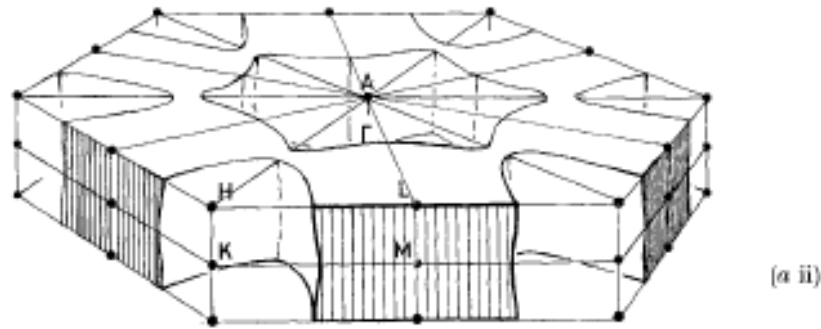
(iii) 4Hb-TaS₂ (300°K). Pattern indexable on $\sqrt{3} \times \sqrt{3}$ superlattice. Equivalent to superposition of $\sqrt{3} \times \sqrt{3}$ and $\sqrt{3} \times \sqrt{3}$ -domain patterns.

(iv) 1T-TaS₂ (300°K). Basically $\sqrt{3} \times \sqrt{3}$ superlattice pattern (here of $\sqrt{3} \times \sqrt{3}$ -domain type), but with complex 'decoration'.

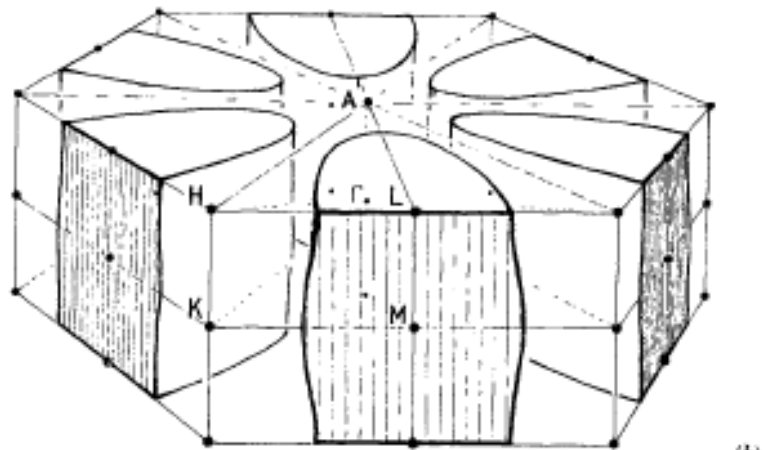




(a i) 2H-TaS₂ lower band



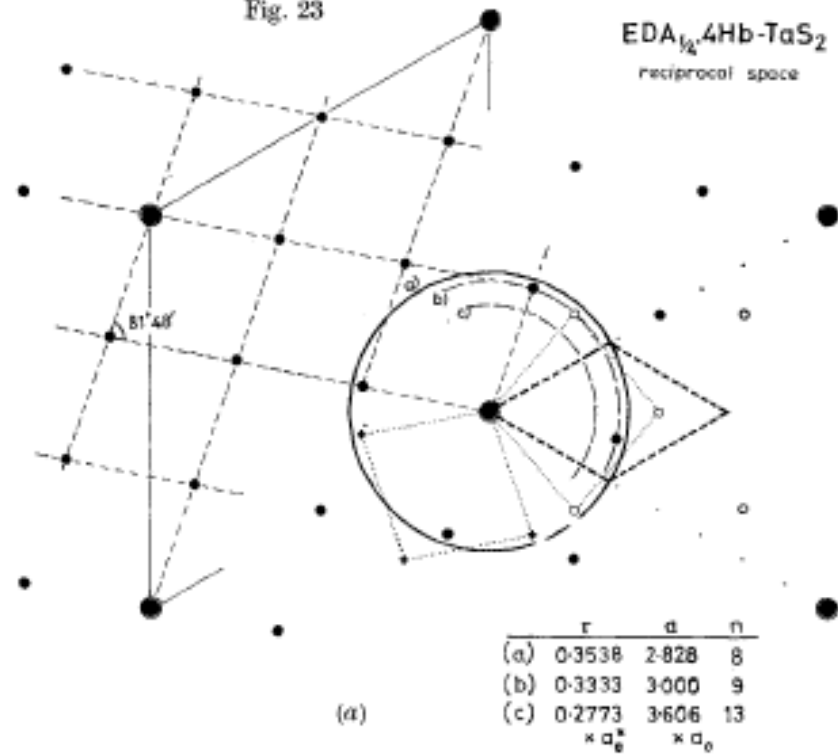
(a ii) 2H-TaS₂ upper band



(b) 1T-TaS₂

Fig. 23

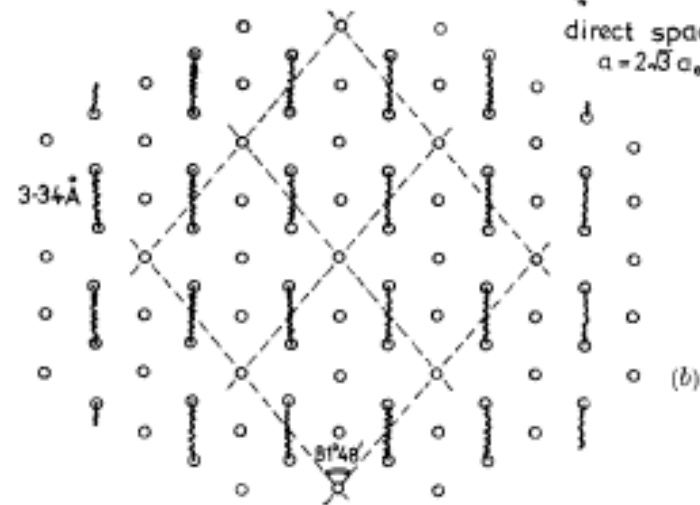
EDA_{1/2}4Hb-TaS₂
reciprocal space



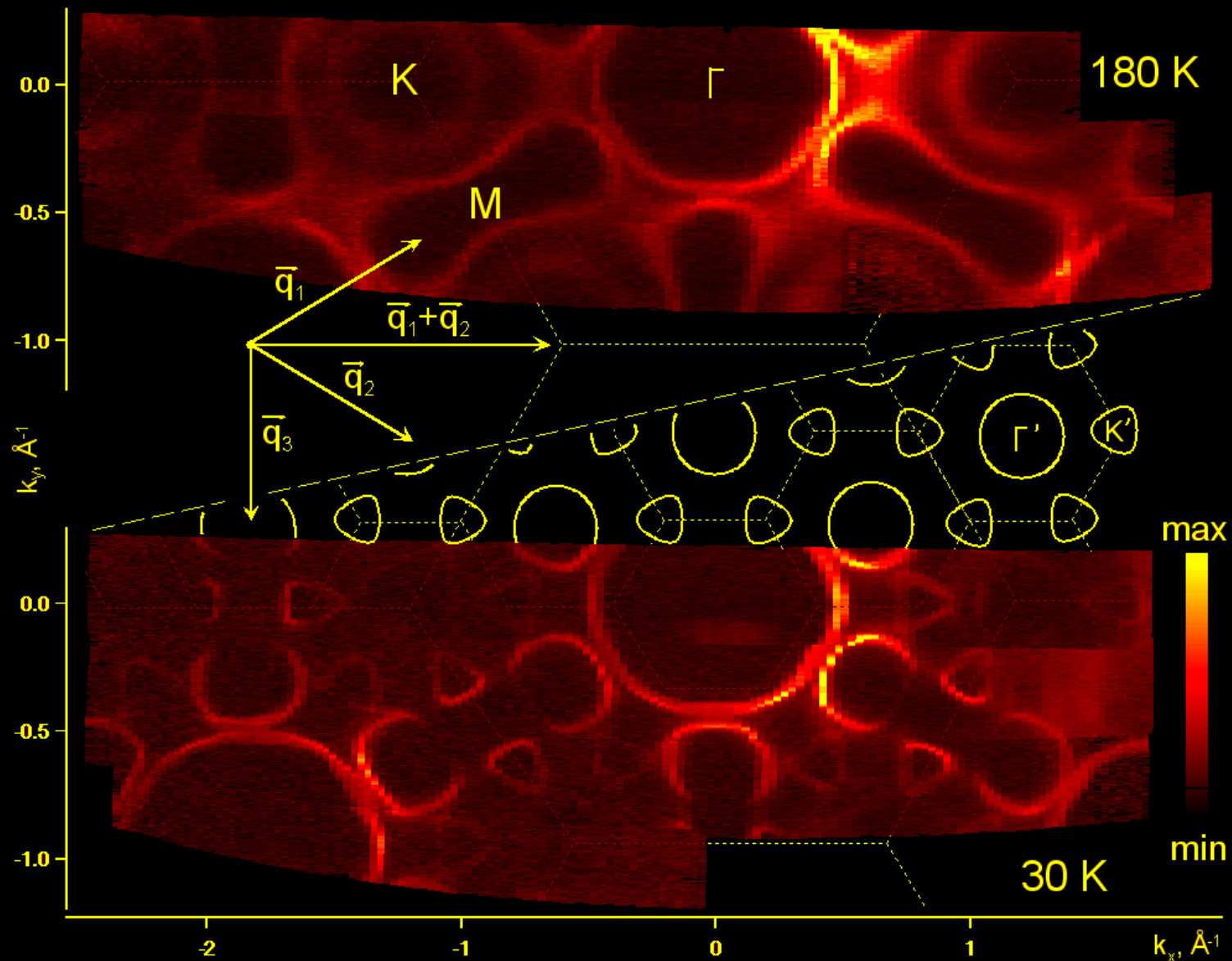
	r	a	n
(a)	0.3538	2.828	8
(b)	0.3333	3.000	9
(c)	0.2773	3.606	13
	$\times a_0^*$	$\times a_0$	

EDA_{1/2}4Hb-TaS₂

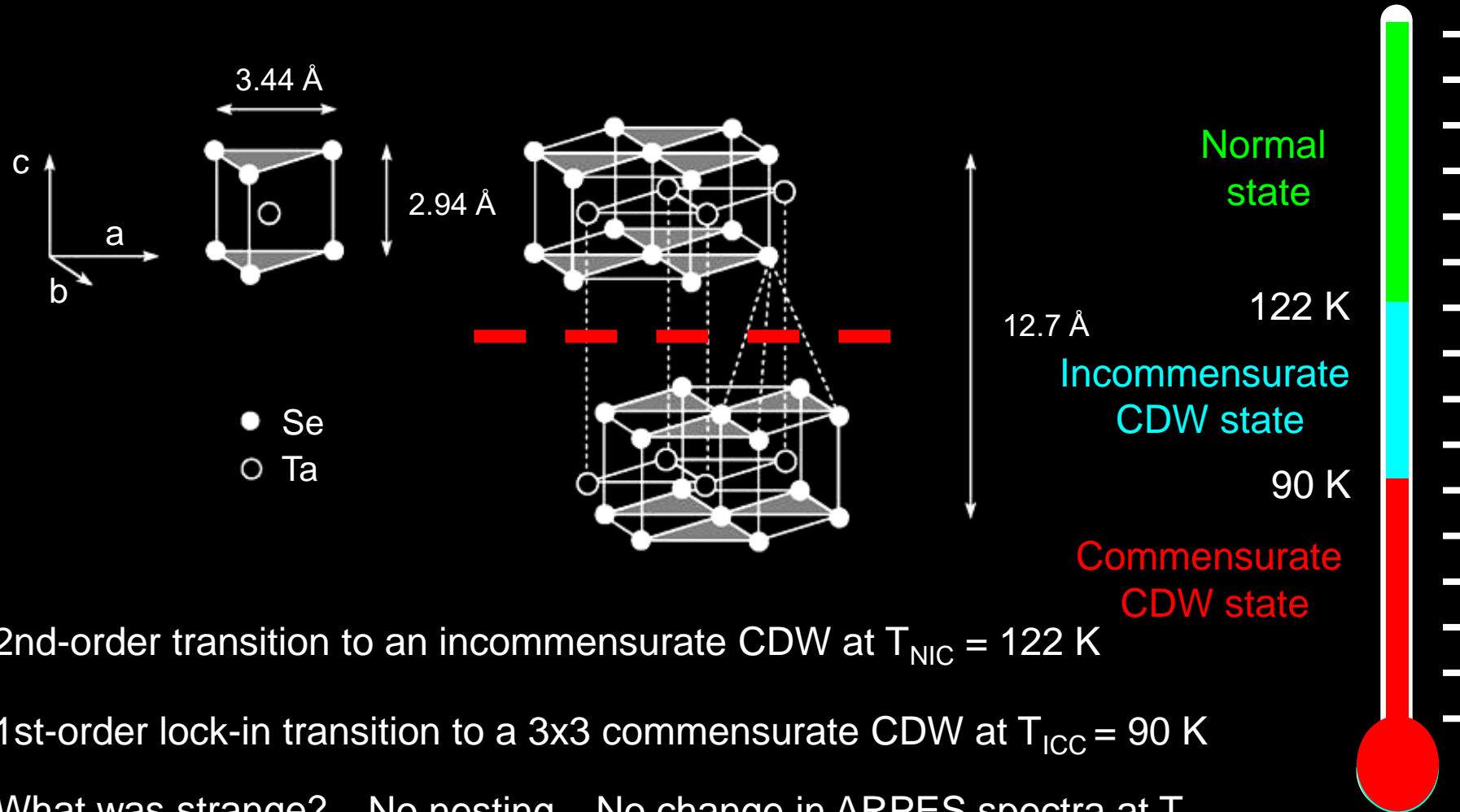
direct space
 $a = 2\sqrt{3} a_0$



CDW in TaSe₂: commensurate CDW state

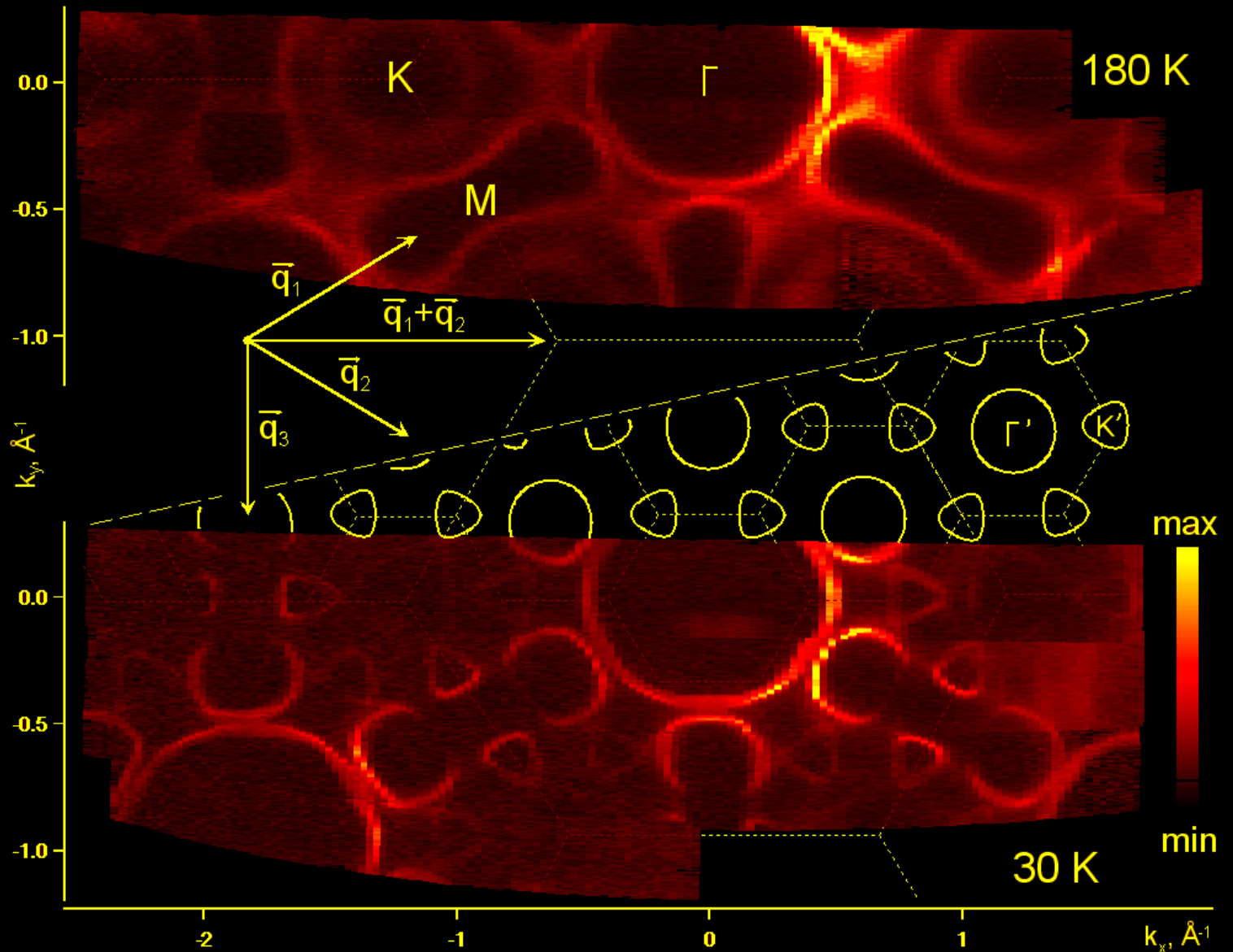
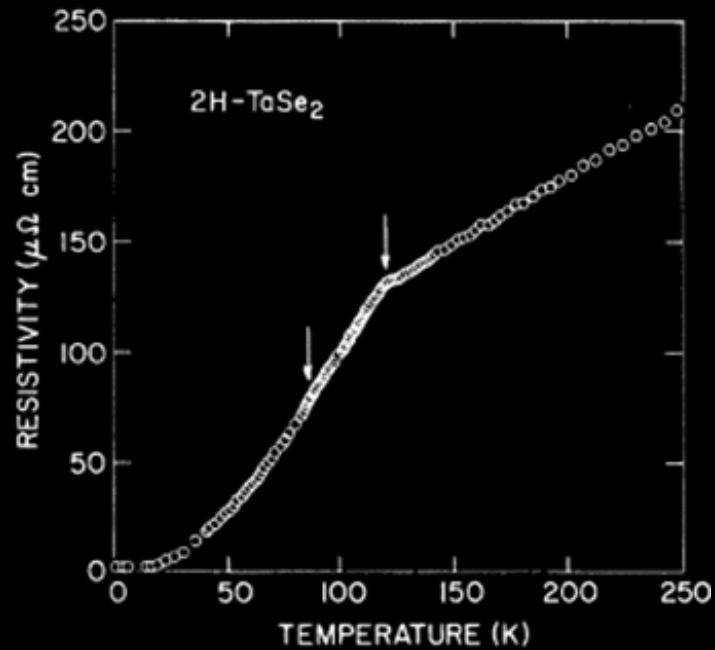
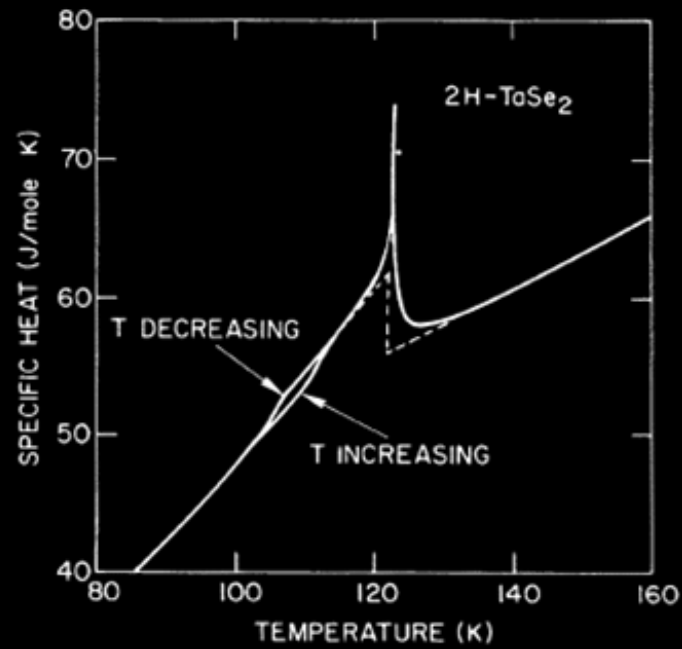


2H-TaSe₂ crystal structure, CDW transitions

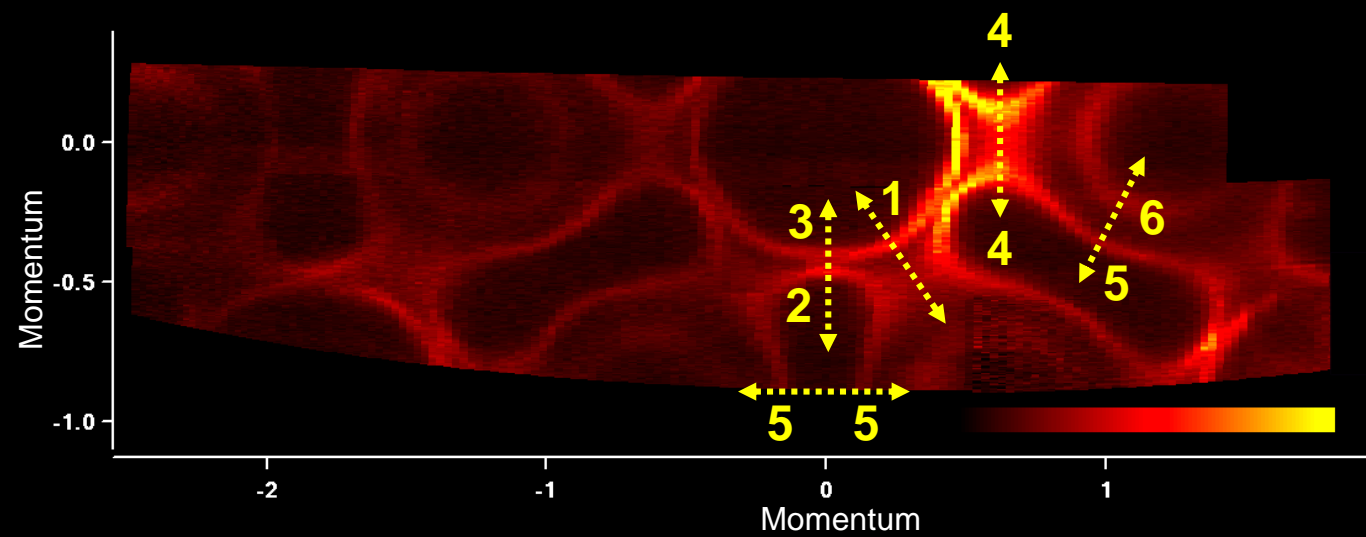
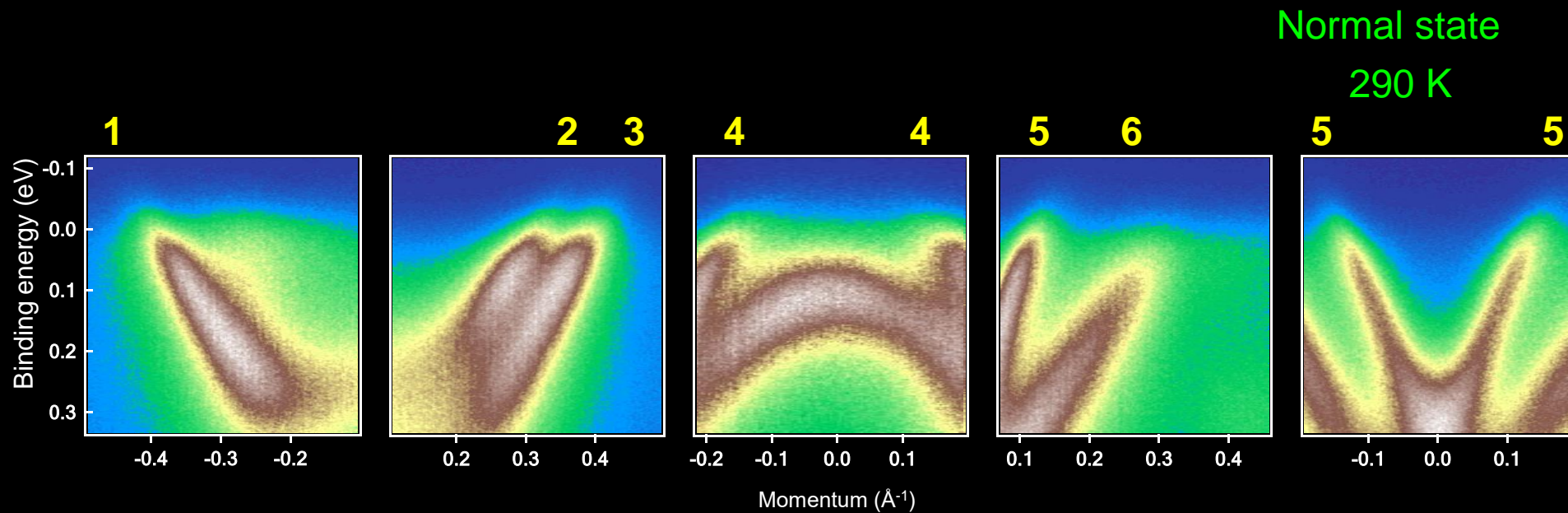


- 2nd-order transition to an incommensurate CDW at $T_{\text{NIC}} = 122$ K
- 1st-order lock-in transition to a 3x3 commensurate CDW at $T_{\text{ICC}} = 90$ K
- What was strange? No nesting. No change in ARPES spectra at T_{NIC} .
Gap of 24-250 meV only below 90K.

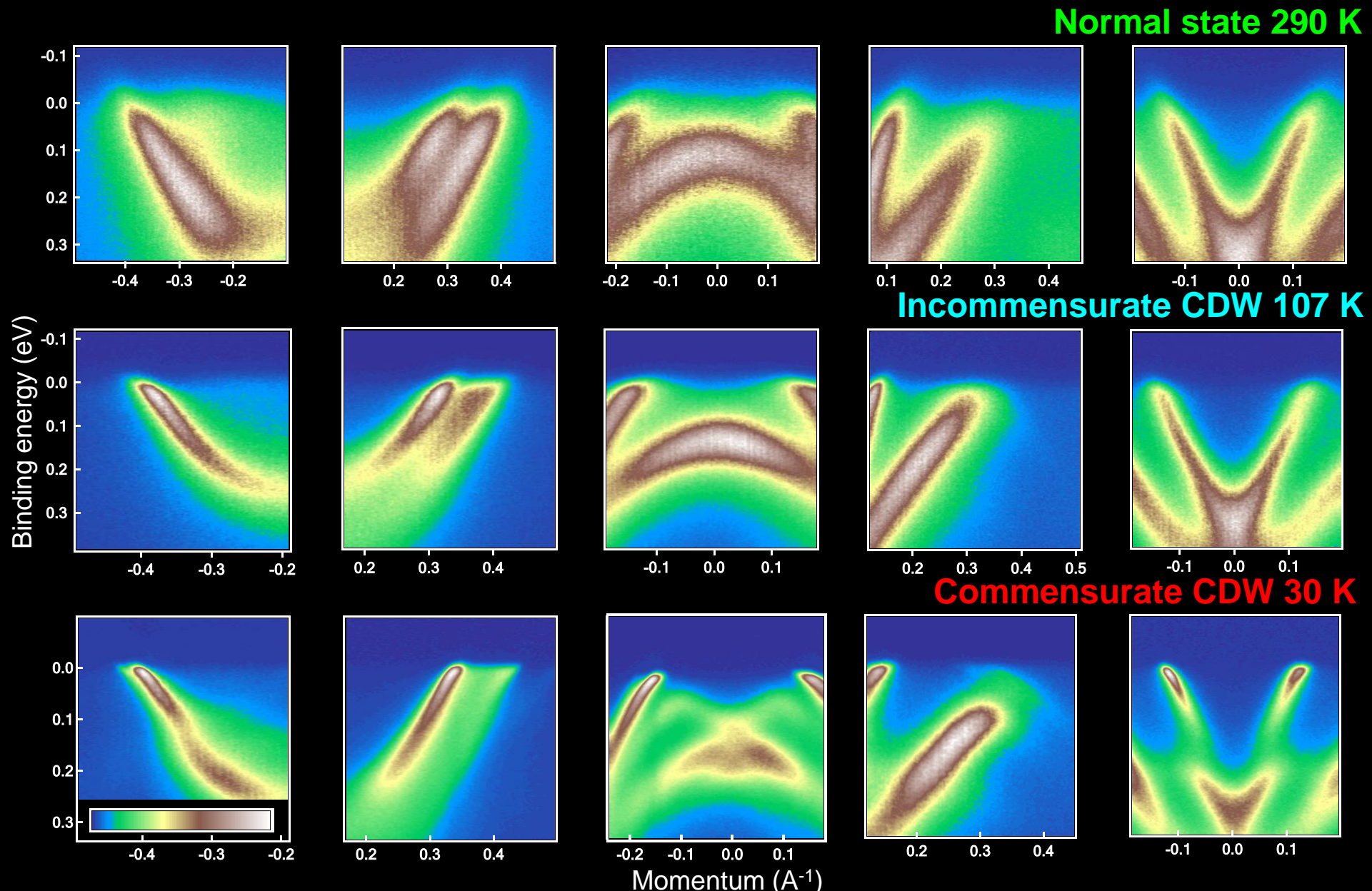
CDW in TaSe₂: commensurate CDW state



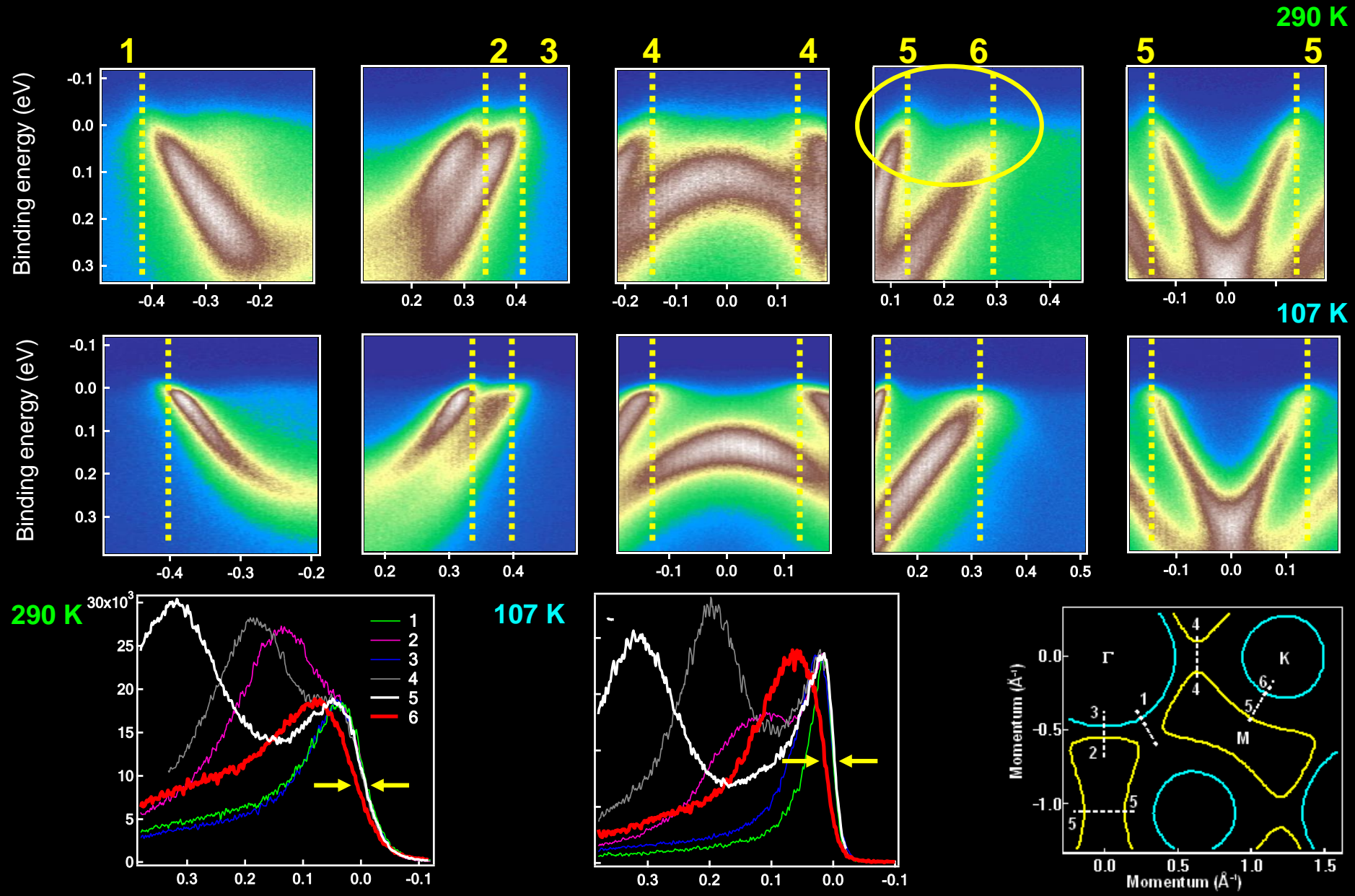
Normal state of 2H-TaSe₂



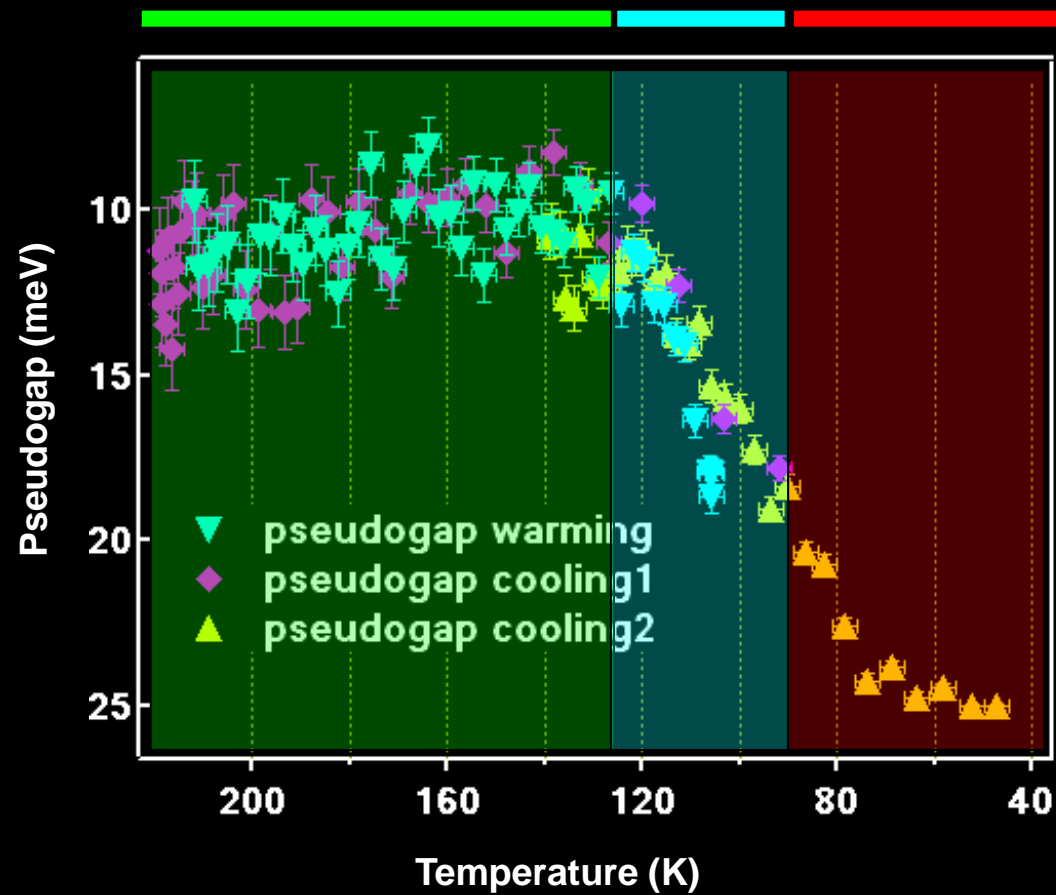
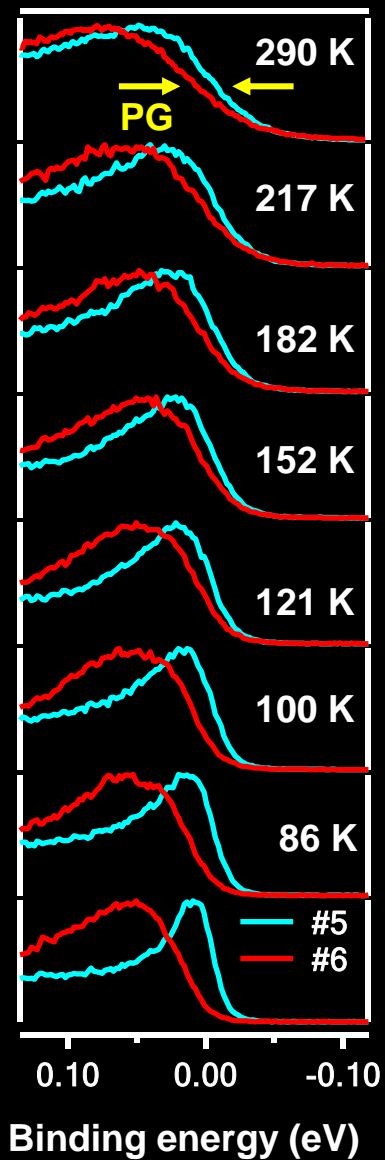
Commensurate CDW state of 2H-TaSe₂



Comparison: IC-CDW and normal state

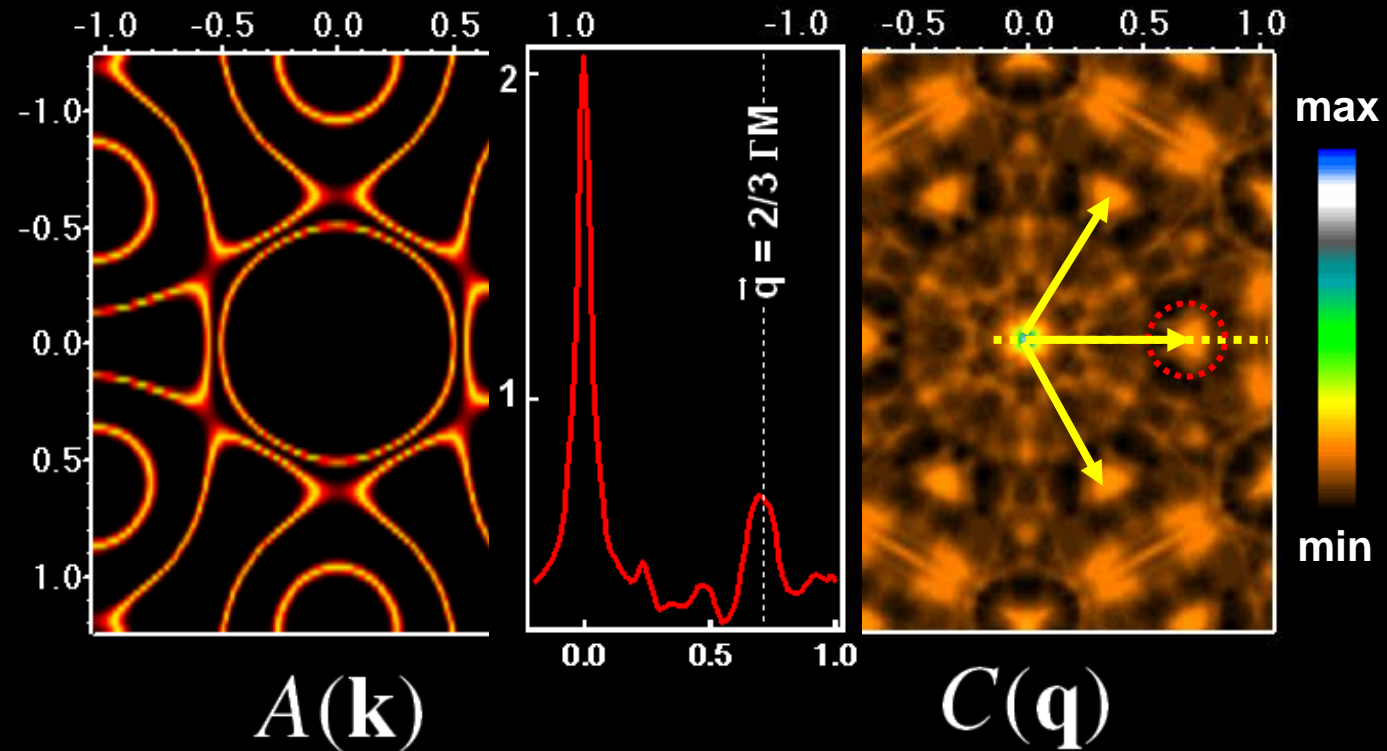


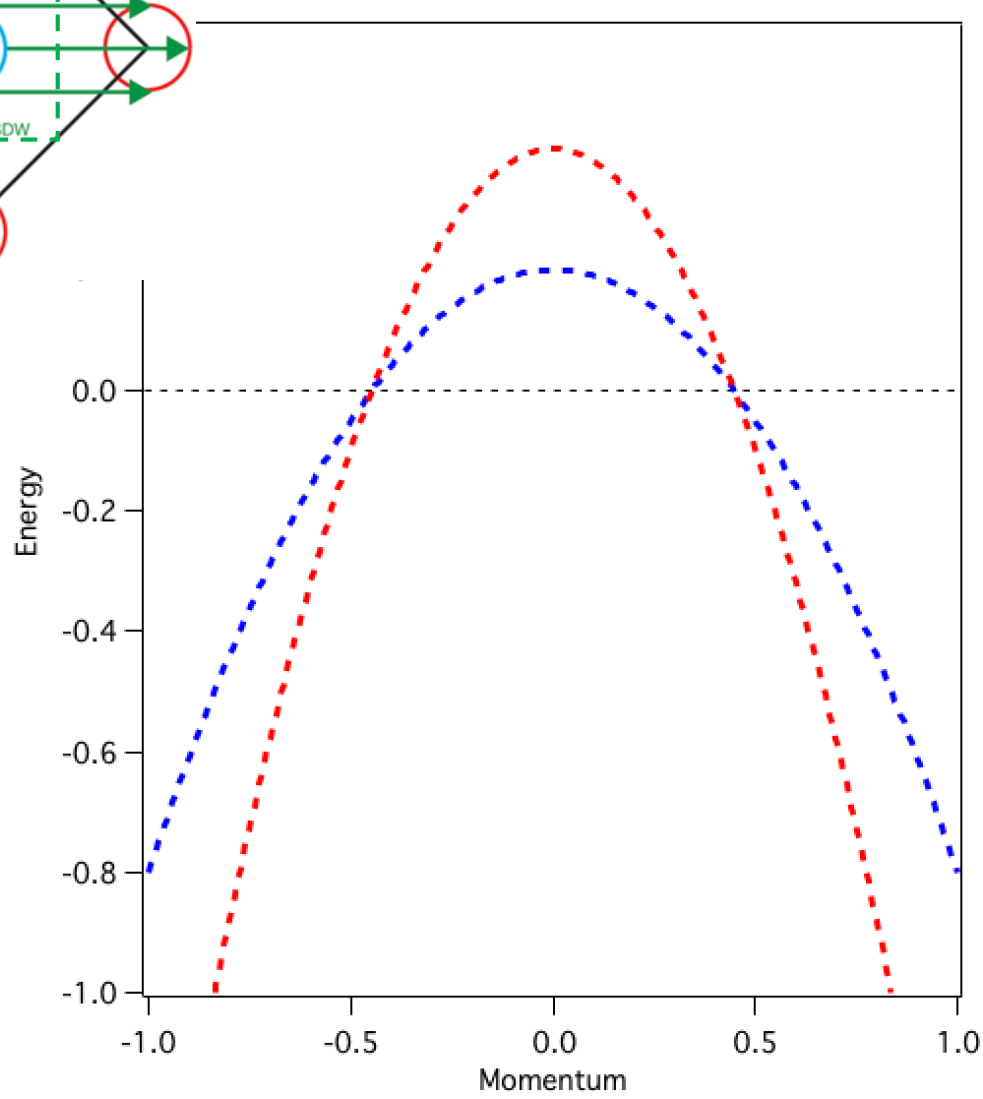
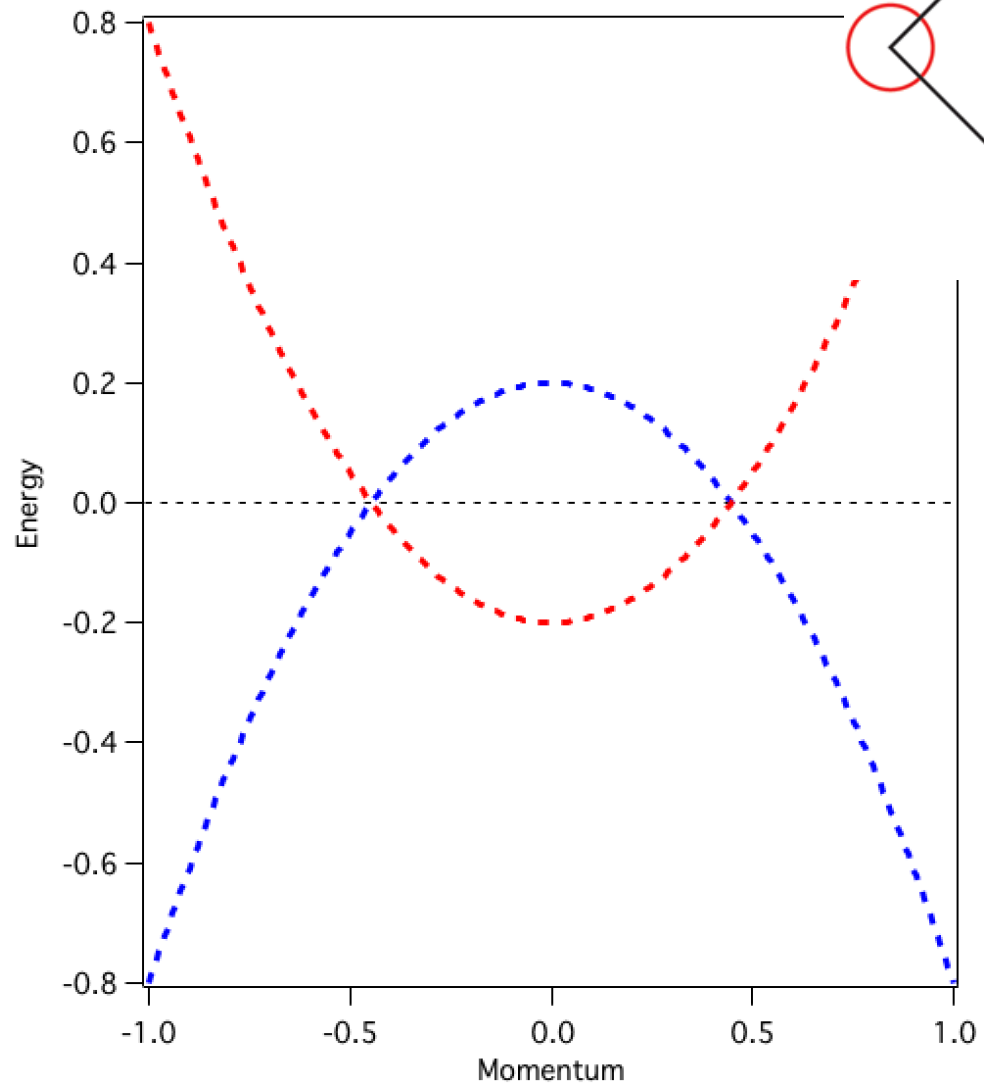
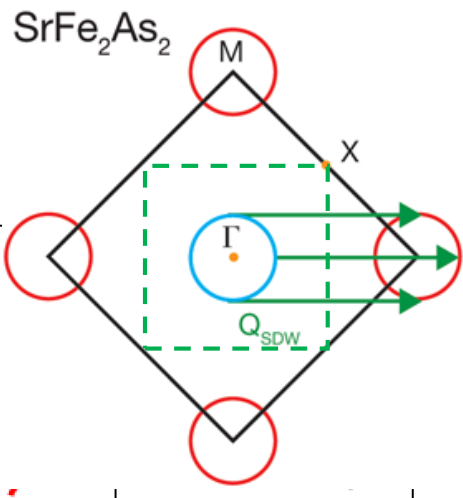
Pseudogap as a function of temperature



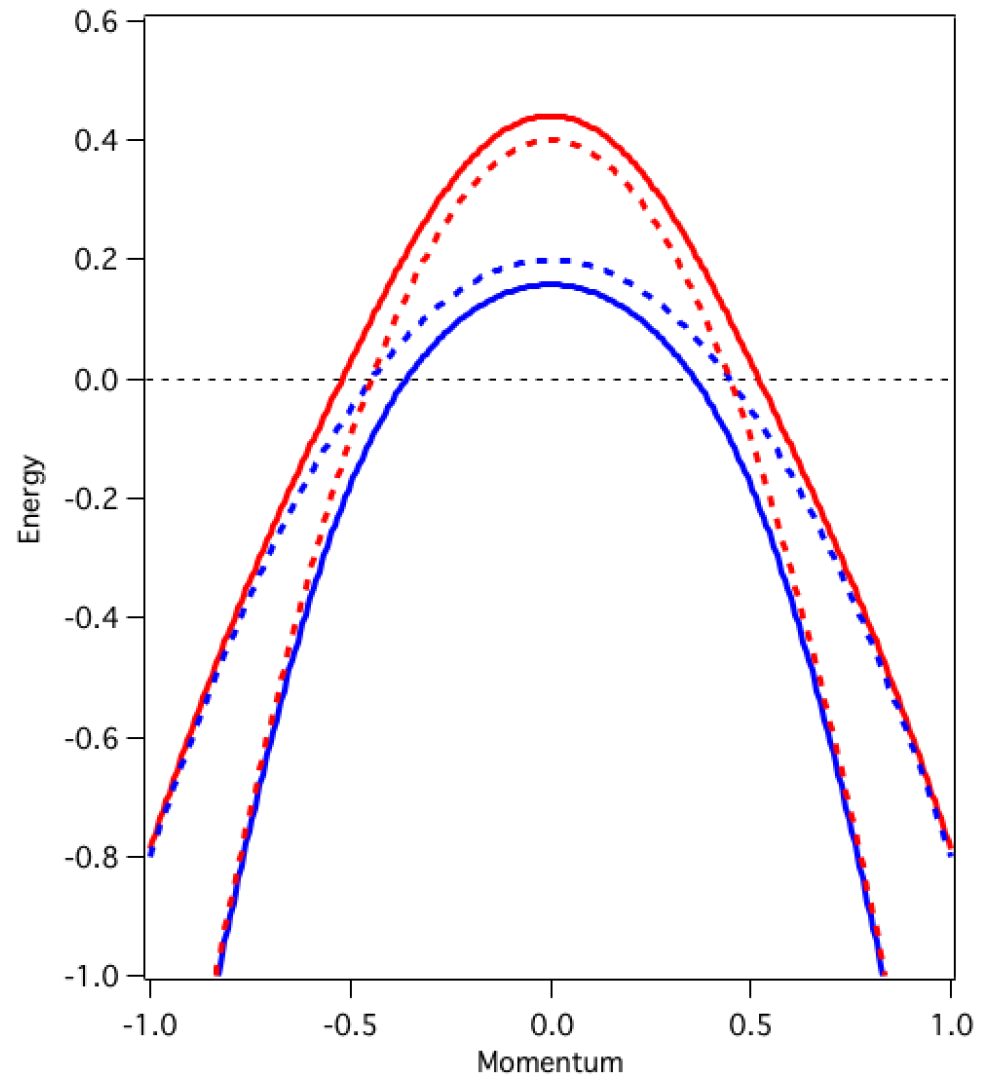
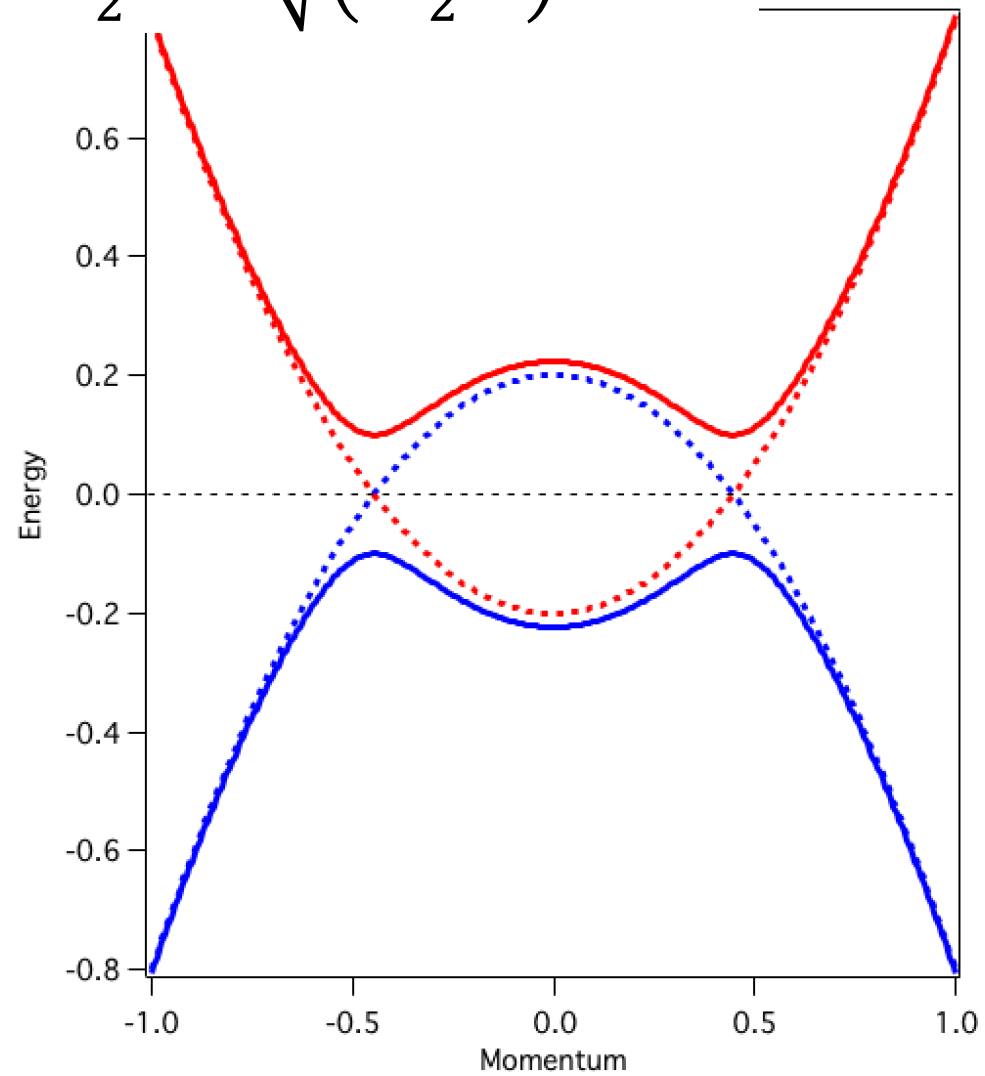
Autocorrelation – measure of nesting

$$\text{AC } A(\mathbf{k}) = \int A(\mathbf{k})A(\mathbf{k} + \mathbf{q}) d\mathbf{k} = C(\mathbf{q}) \quad 290 \text{ K}$$

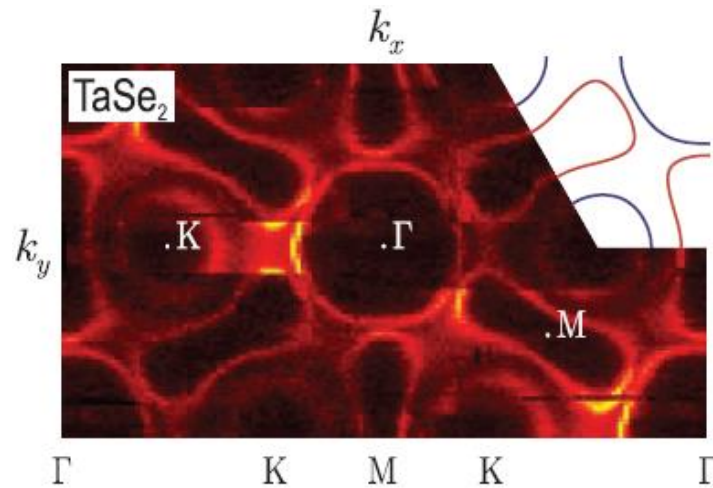




$$\varepsilon_{\pm} = \frac{\varepsilon_1 + \varepsilon_2}{2} \pm \sqrt{\left(\frac{\varepsilon_1 - \varepsilon_2}{2}\right)^2 + \Delta^2}$$

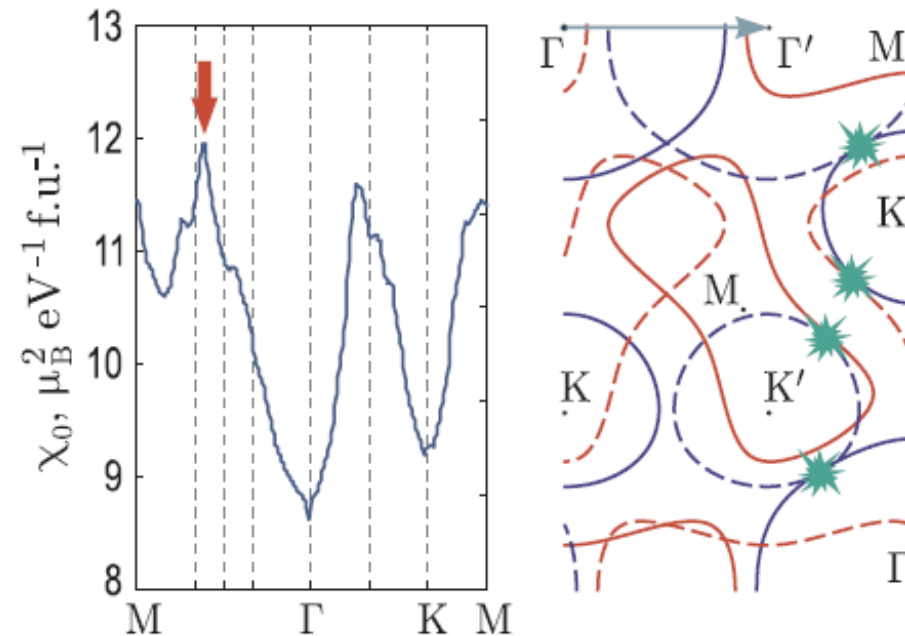
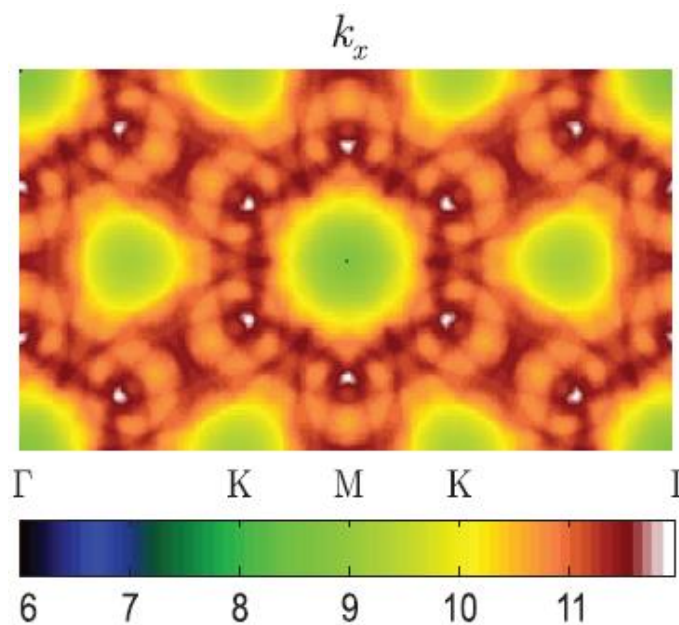


Fermi surface nesting and Lindhard function



$$\chi_{\mathbf{q}} = \sum_{\mathbf{k}} [n_{\text{F}}(\epsilon_{\mathbf{k}}) - n_{\text{F}}(\epsilon_{\mathbf{k}+\mathbf{q}})] / (\epsilon_{\mathbf{k}} - \epsilon_{\mathbf{k}+\mathbf{q}})$$

$$\chi = G \star G$$

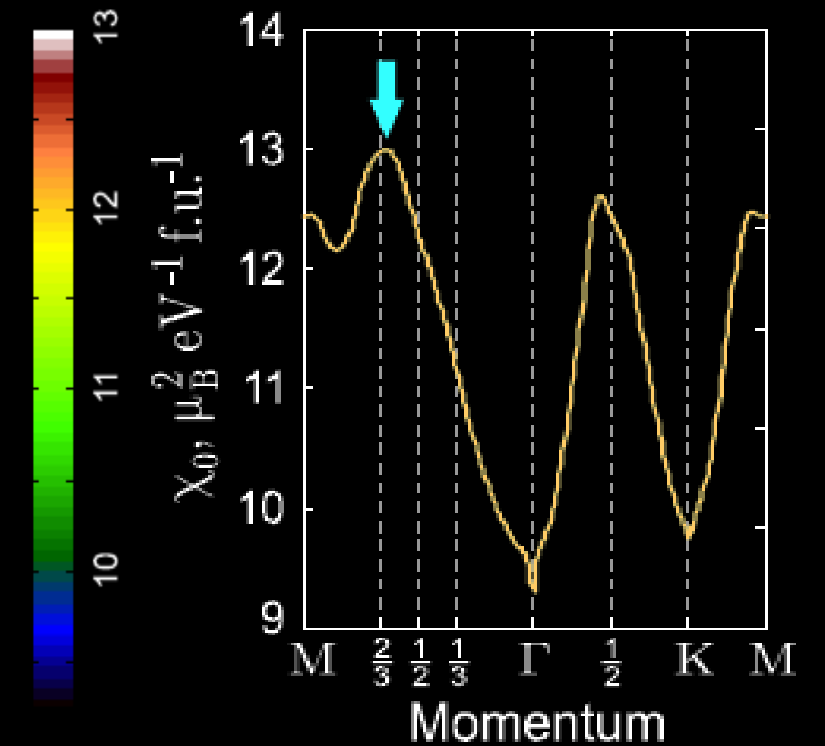
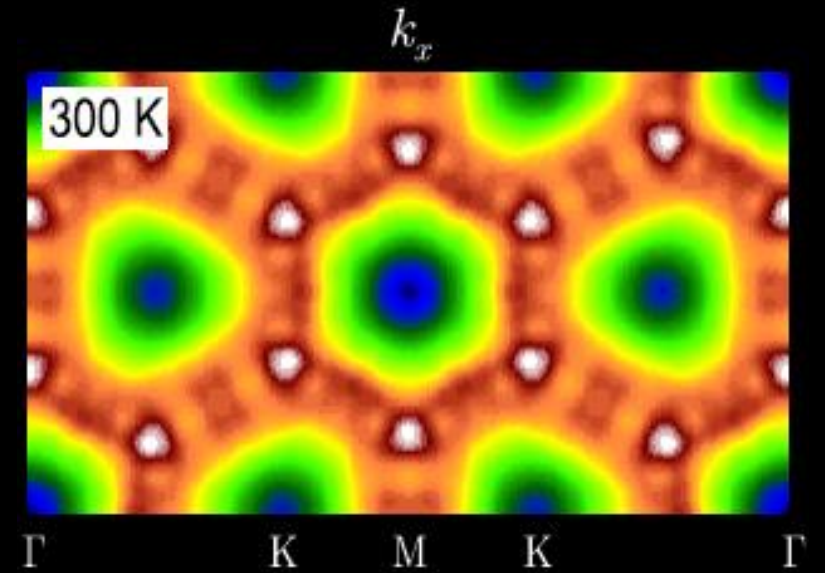


Electron susceptibility

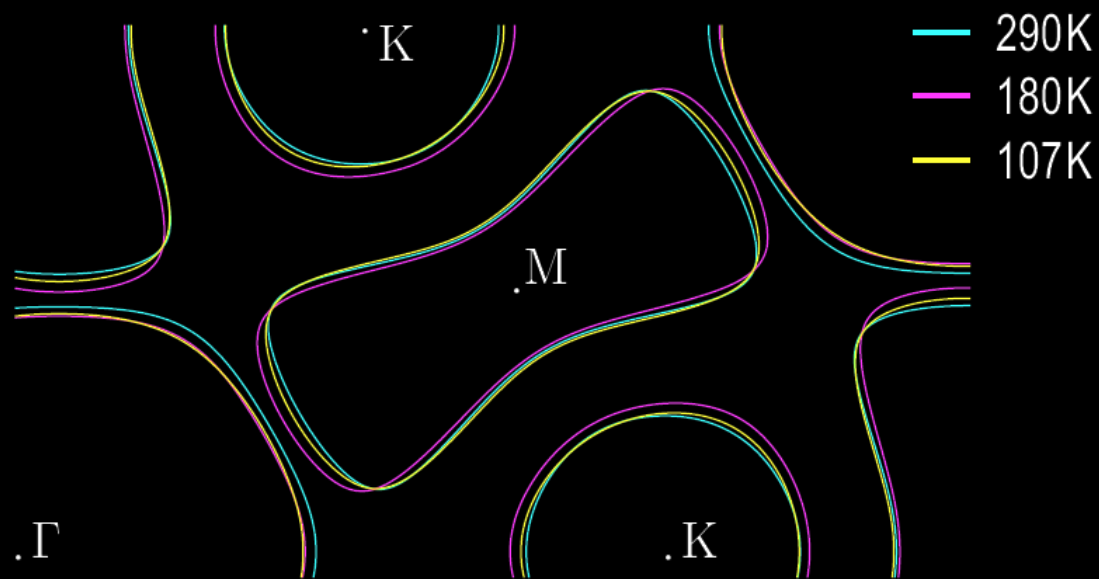
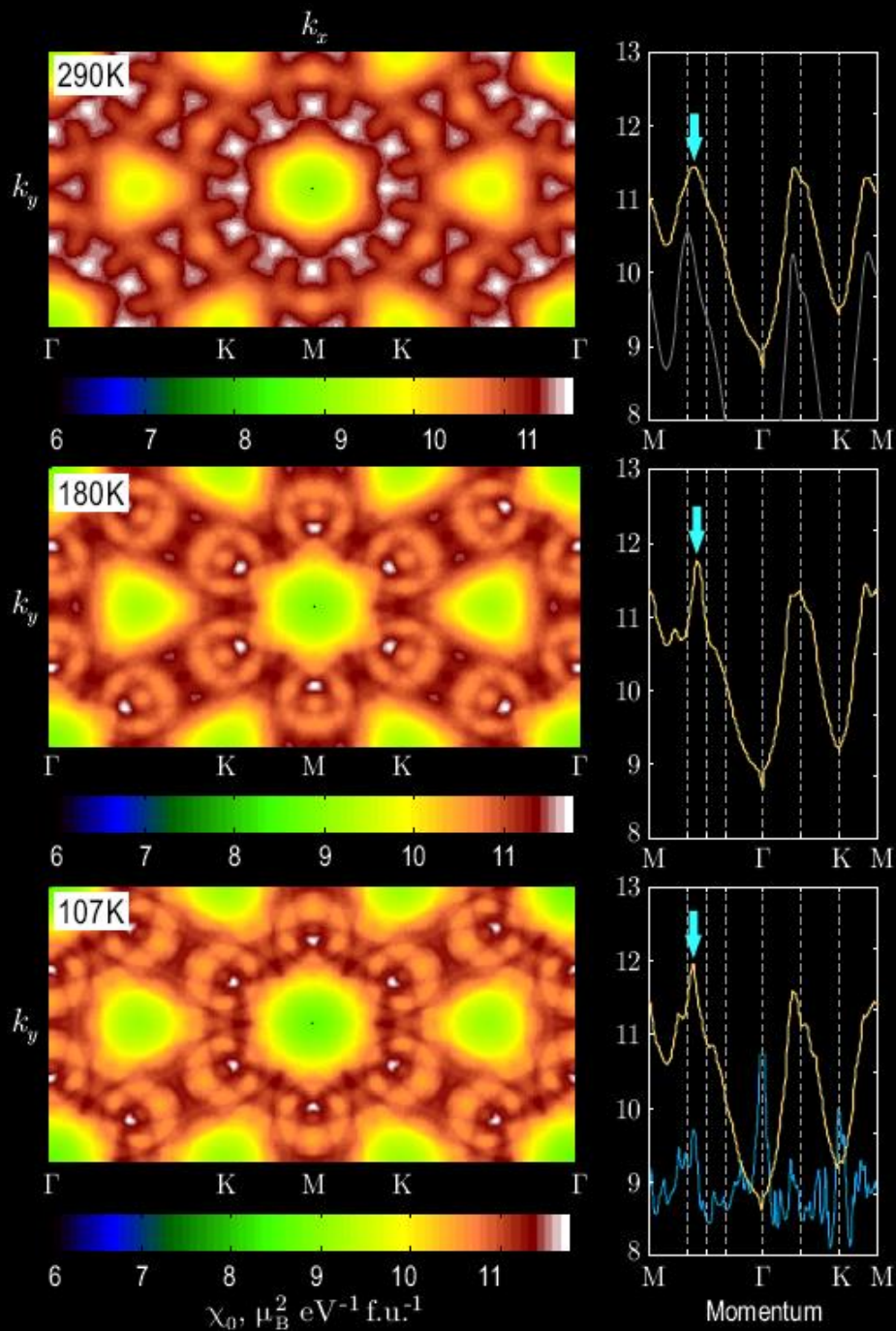
$$\chi_0(\mathbf{q}, \omega) = 2 \int \frac{d\mathbf{k}}{(2\pi)^d} \frac{n_F(\epsilon_{\mathbf{k}}) - n_F(\epsilon_{\mathbf{k}+\mathbf{q}})}{\epsilon_{\mathbf{k}} - \epsilon_{\mathbf{k}+\mathbf{q}} + \omega + i0^+}$$

Lindhard functions at $\omega \rightarrow 0$

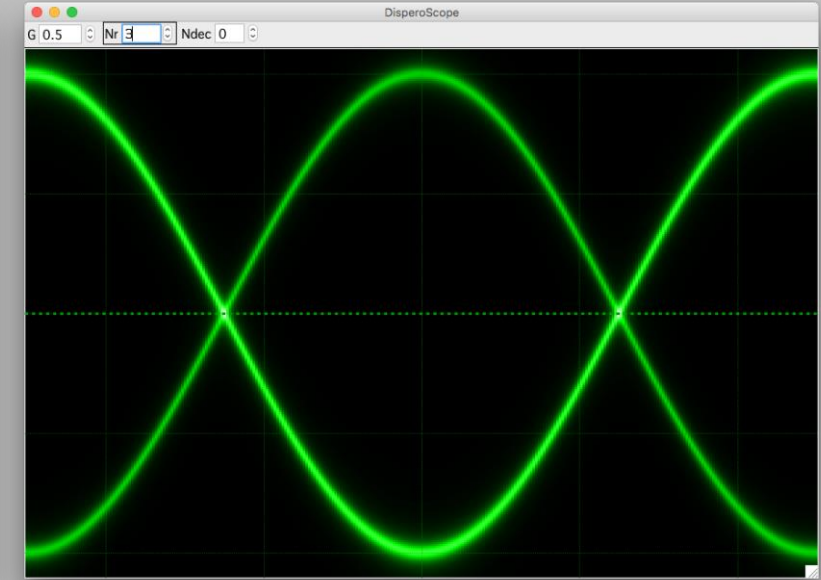
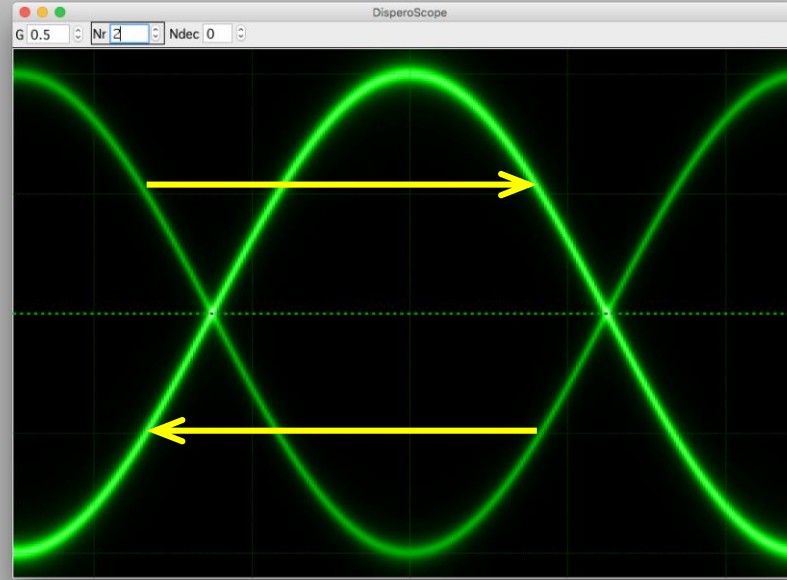
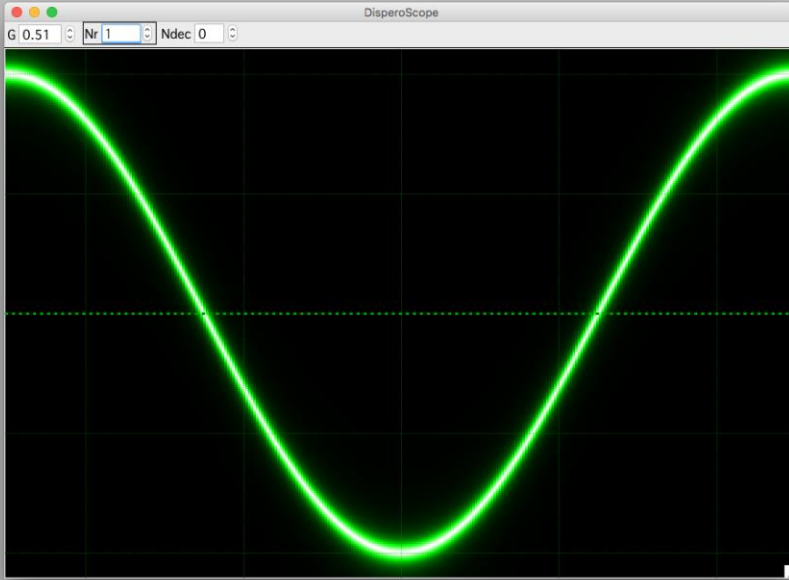
$$\begin{aligned} \chi_{\mathbf{q}} = & \sum_{\mathbf{k}} \frac{n_F(\epsilon_{\mathbf{k}}^a) - n_F(\epsilon_{\mathbf{k}+\mathbf{q}}^a)}{\epsilon_{\mathbf{k}}^a - \epsilon_{\mathbf{k}+\mathbf{q}}^a} + \sum_{\mathbf{k}} \frac{n_F(\epsilon_{\mathbf{k}}^a) - n_F(\epsilon_{\mathbf{k}+\mathbf{q}}^b)}{\epsilon_{\mathbf{k}}^a - \epsilon_{\mathbf{k}+\mathbf{q}}^b} \\ & + \sum_{\mathbf{k}} \frac{n_F(\epsilon_{\mathbf{k}}^b) - n_F(\epsilon_{\mathbf{k}+\mathbf{q}}^a)}{\epsilon_{\mathbf{k}}^b - \epsilon_{\mathbf{k}+\mathbf{q}}^a} + \sum_{\mathbf{k}} \frac{n_F(\epsilon_{\mathbf{k}}^b) - n_F(\epsilon_{\mathbf{k}+\mathbf{q}}^b)}{\epsilon_{\mathbf{k}}^b - \epsilon_{\mathbf{k}+\mathbf{q}}^b} \end{aligned}$$



Temperature variations

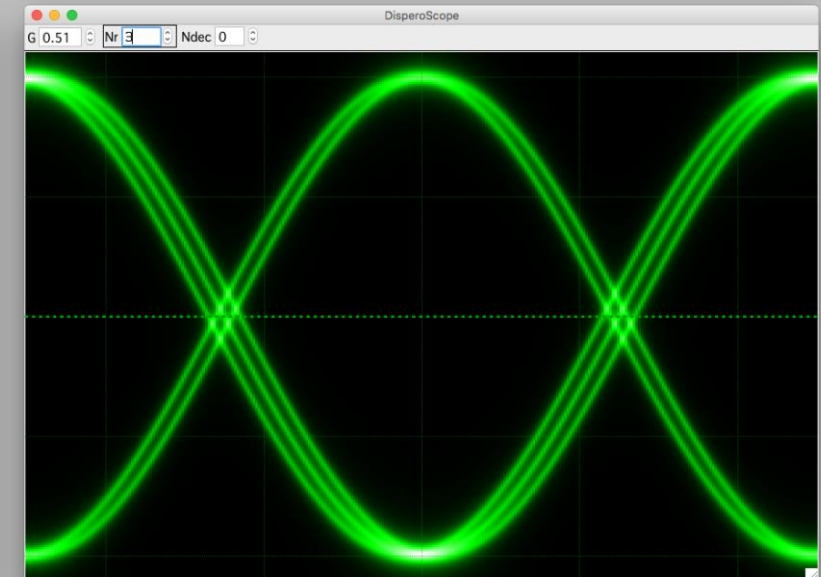
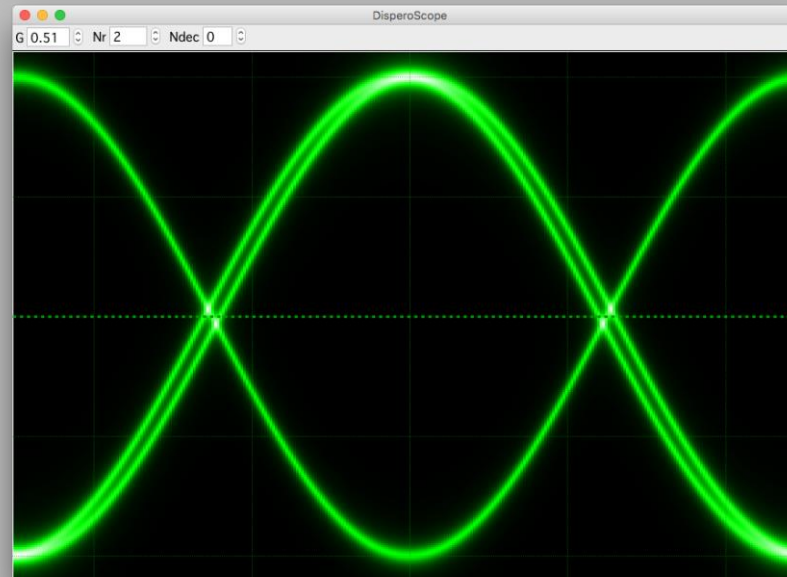


Commensurate vs Incommensurate

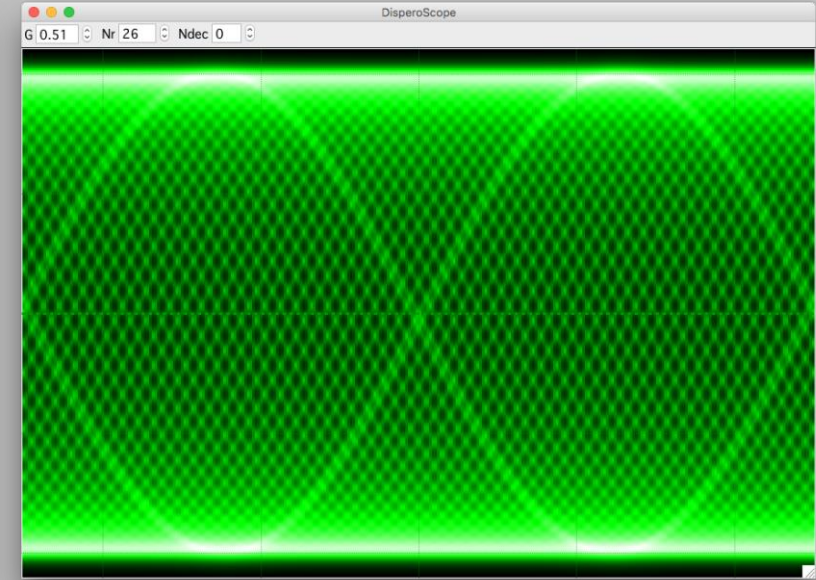
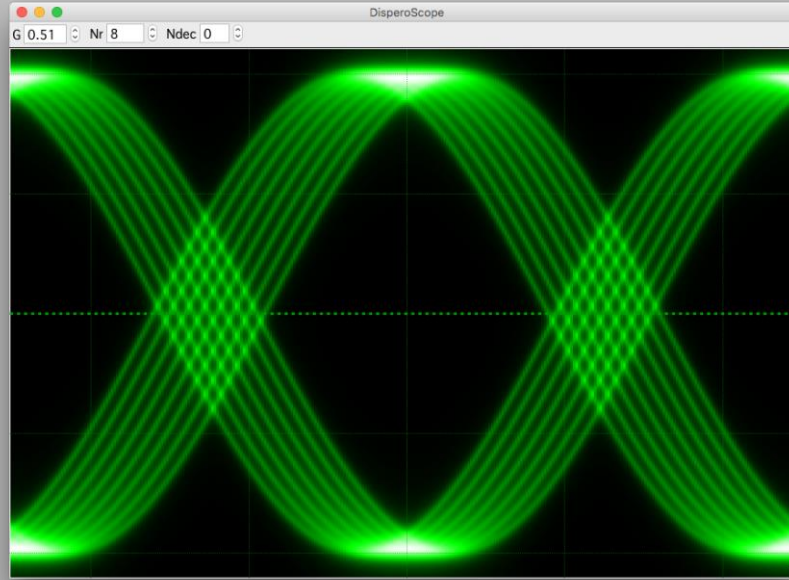
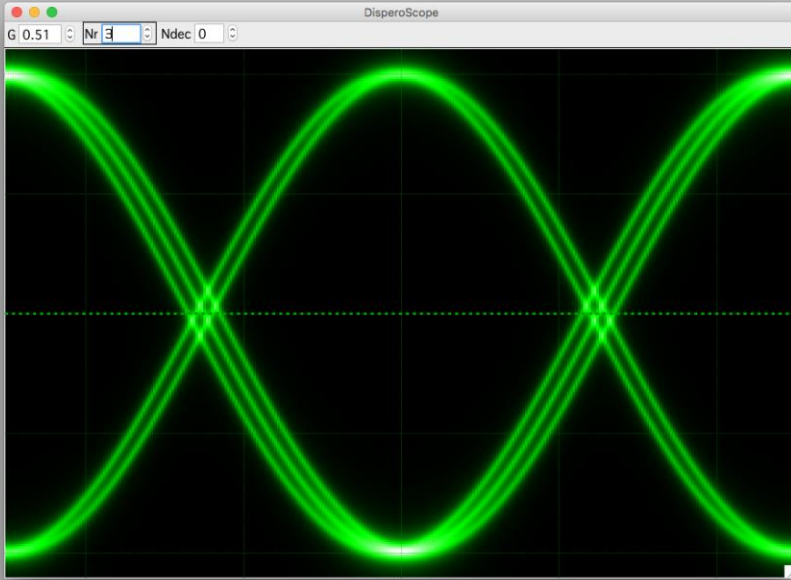


$$A(k, \omega) = \sum_{i=-(Nr-1)}^{Nr-1} \frac{1}{(\omega - \varepsilon_i(k))^2 + \delta^2}$$

$$\varepsilon_i(k) = -\cos[2\pi(x + Gi)]$$

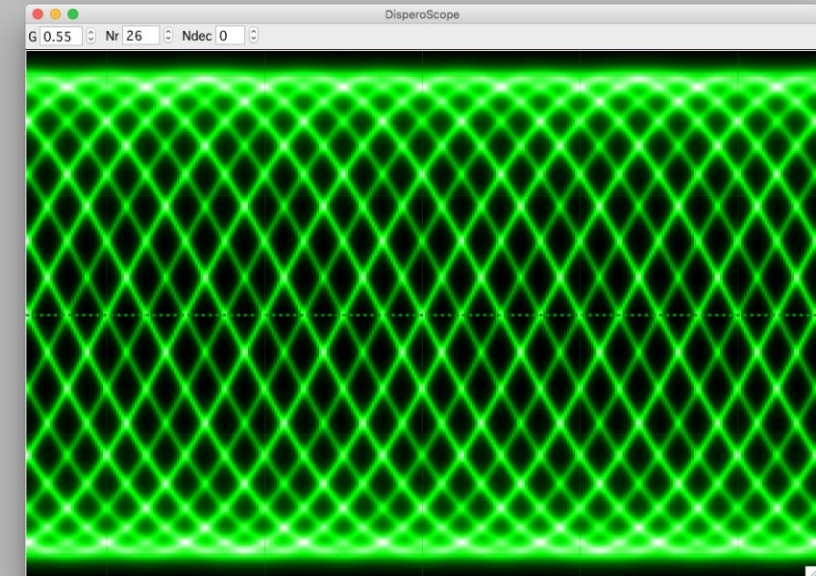
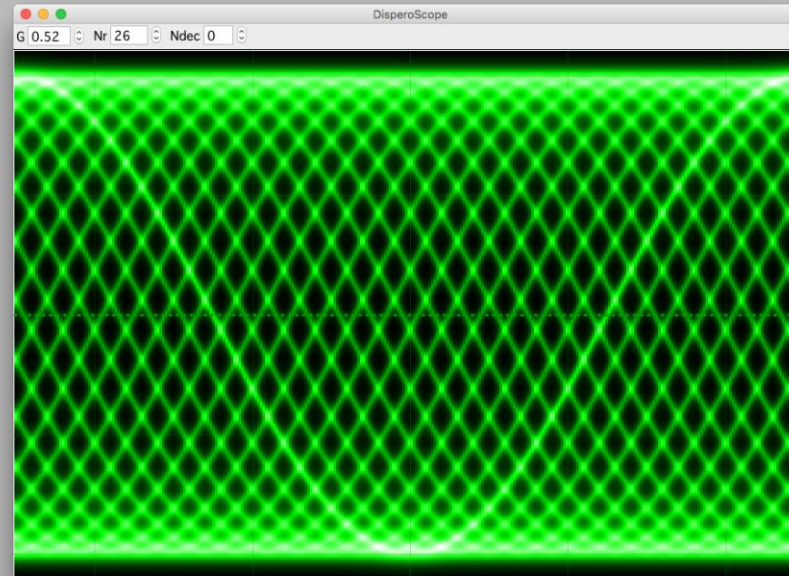


Commensurate vs Incommensurate

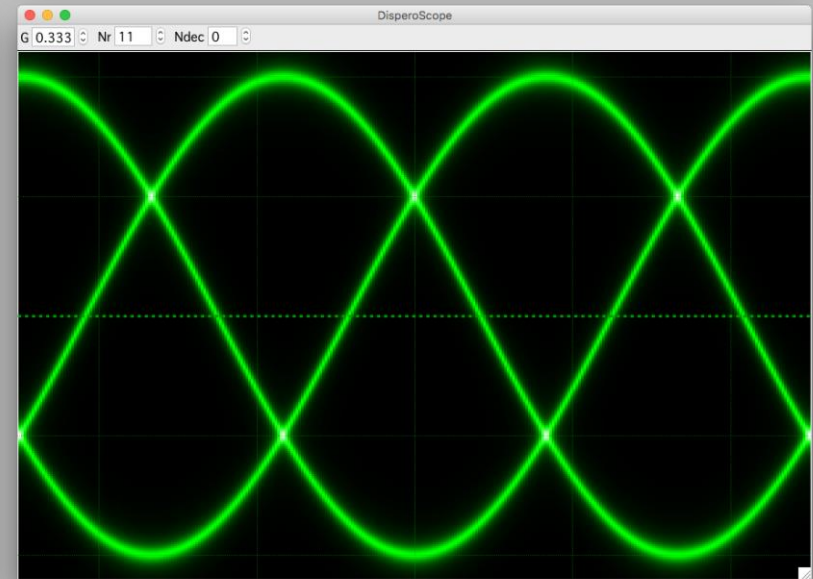
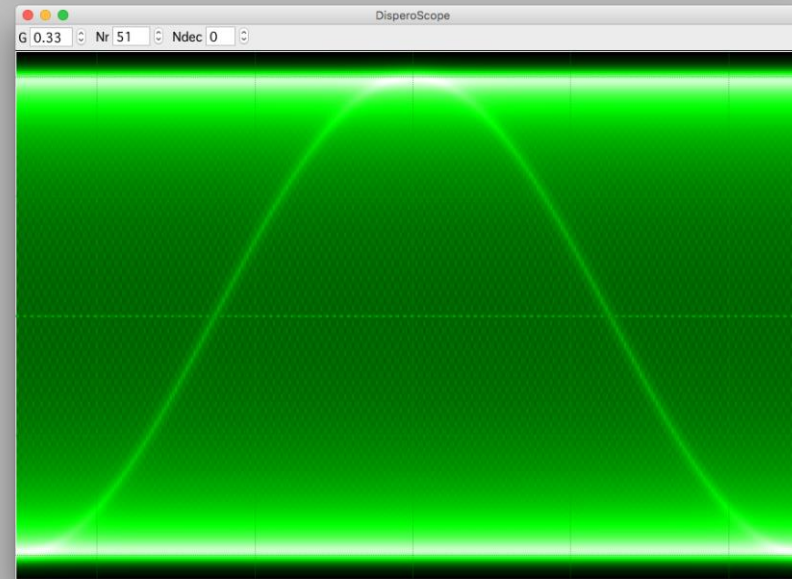
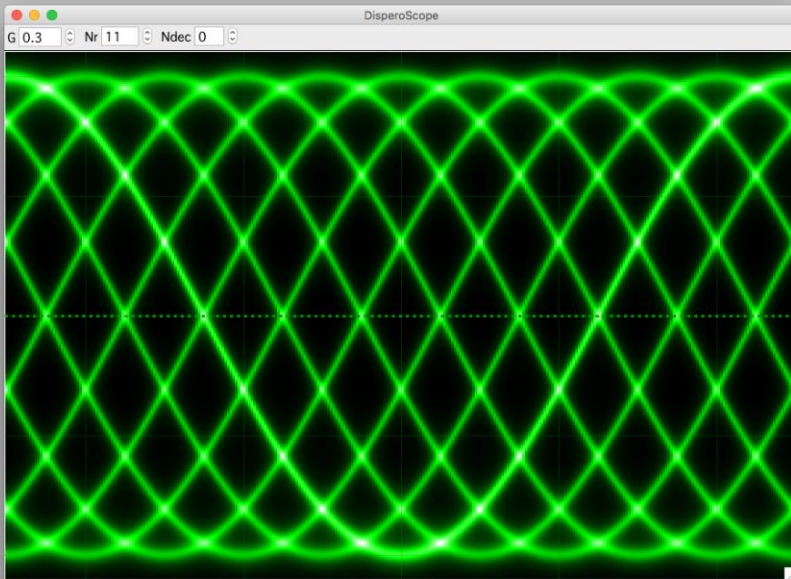
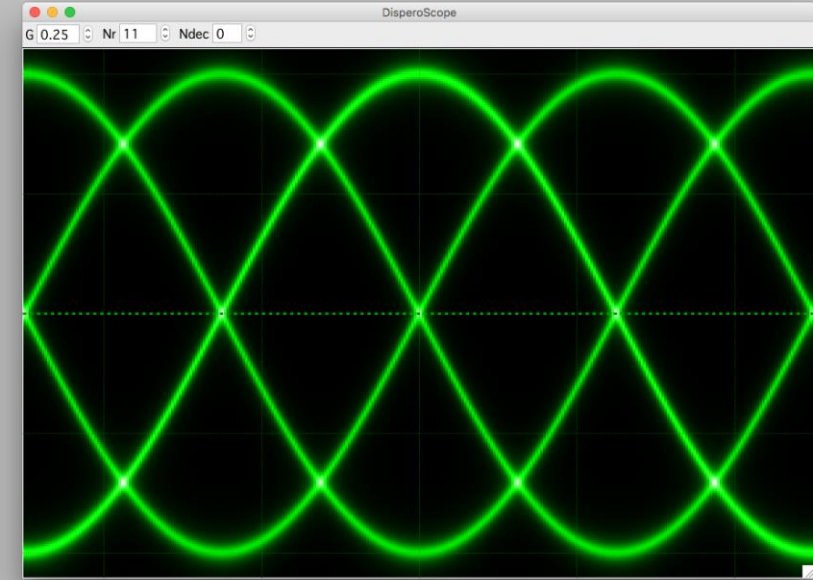
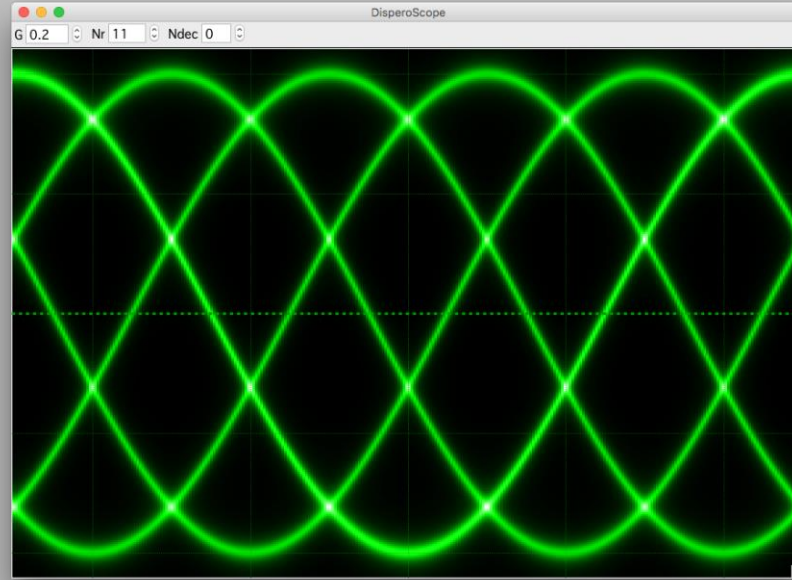
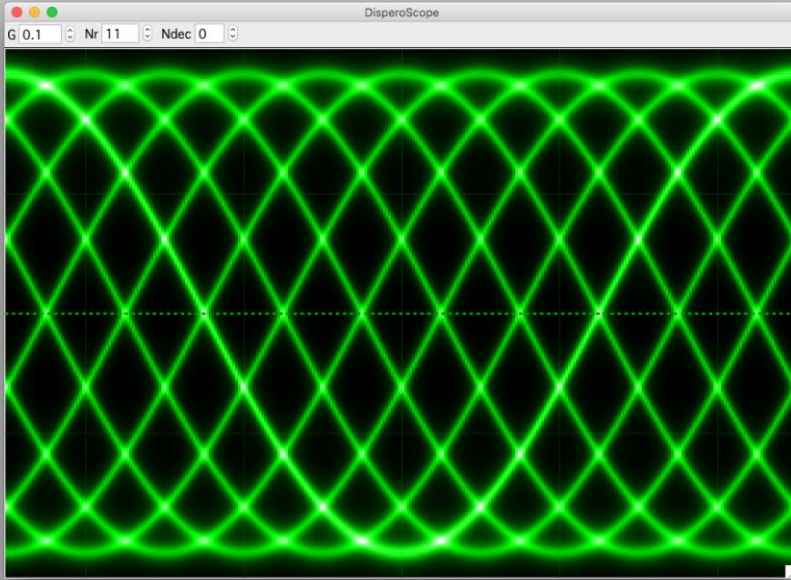


$$A(k, \omega) = \sum_{i=-(Nr-1)}^{Nr-1} \frac{1}{(\omega - \varepsilon_i(k))^2 + \delta^2}$$

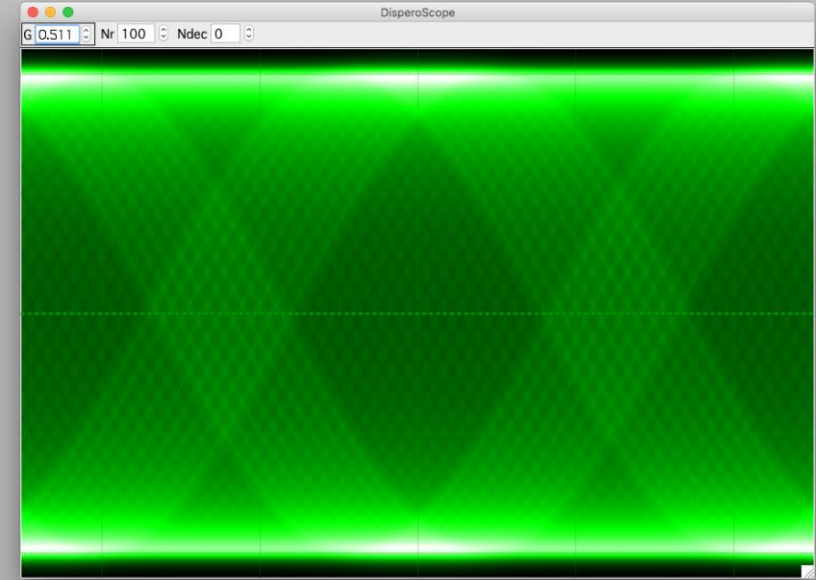
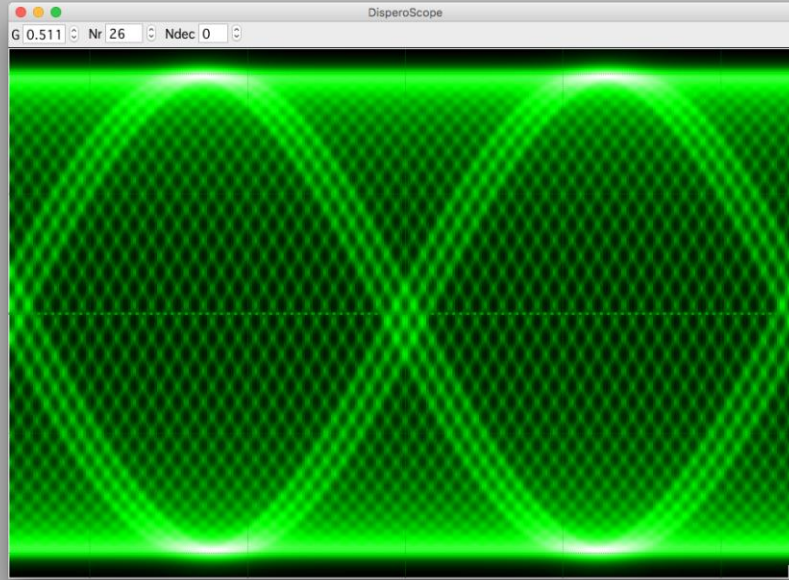
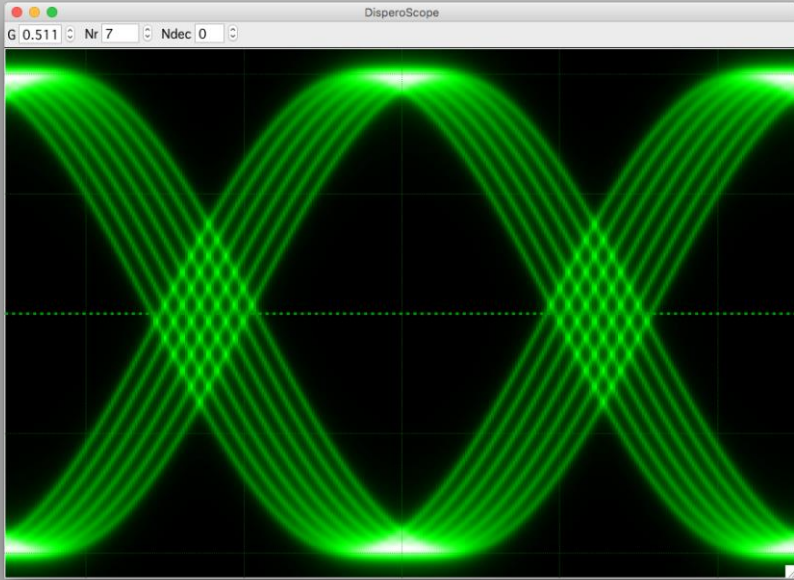
$$\varepsilon_i(k) = -\cos[2\pi(x + Gi)]$$



Commensurate vs Incommensurate

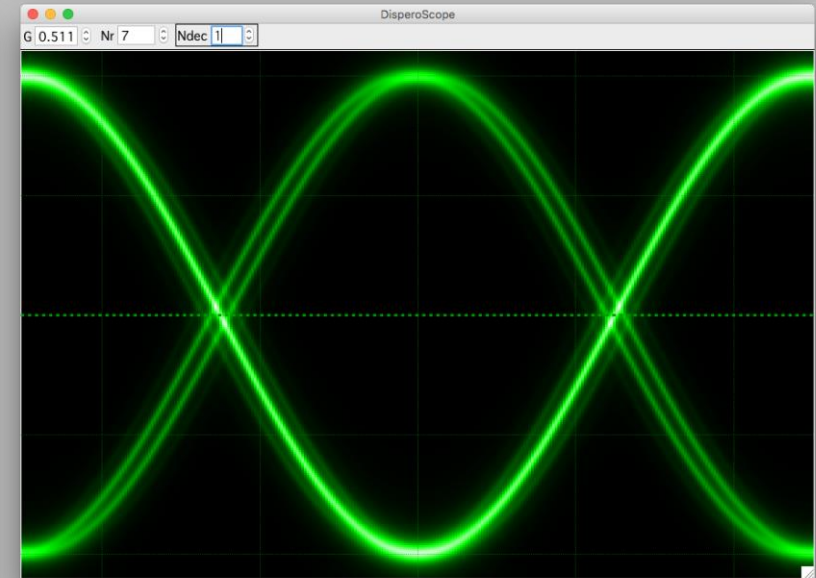
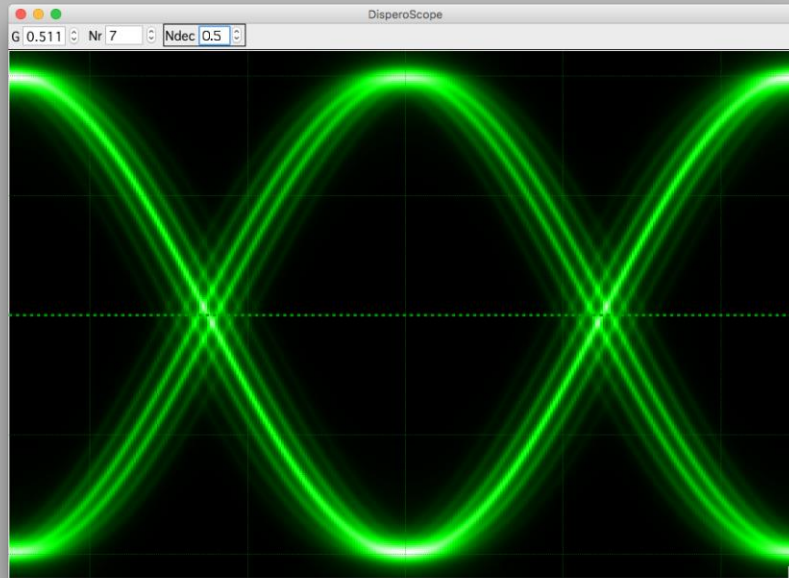


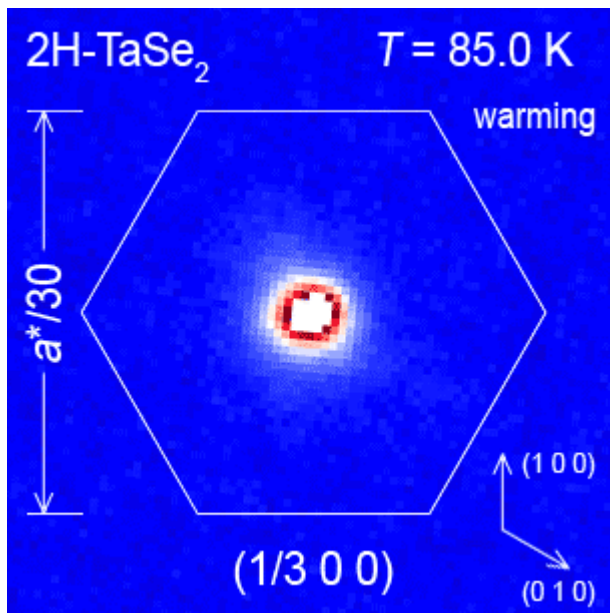
Commensurate vs Incommensurate



$$A(k, \omega) = \sum_{i=-(Nr-1)}^{Nr-1} \frac{\exp(-Di)}{(\omega - \varepsilon_i(k))^2 + \delta^2}$$

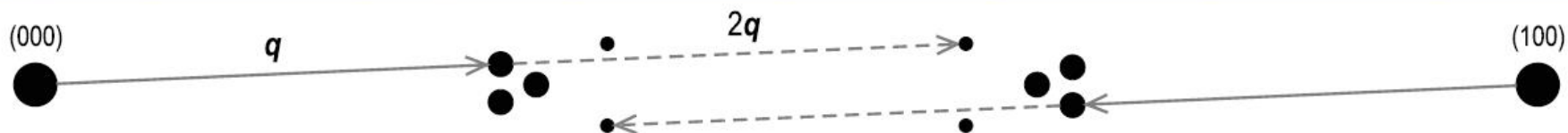
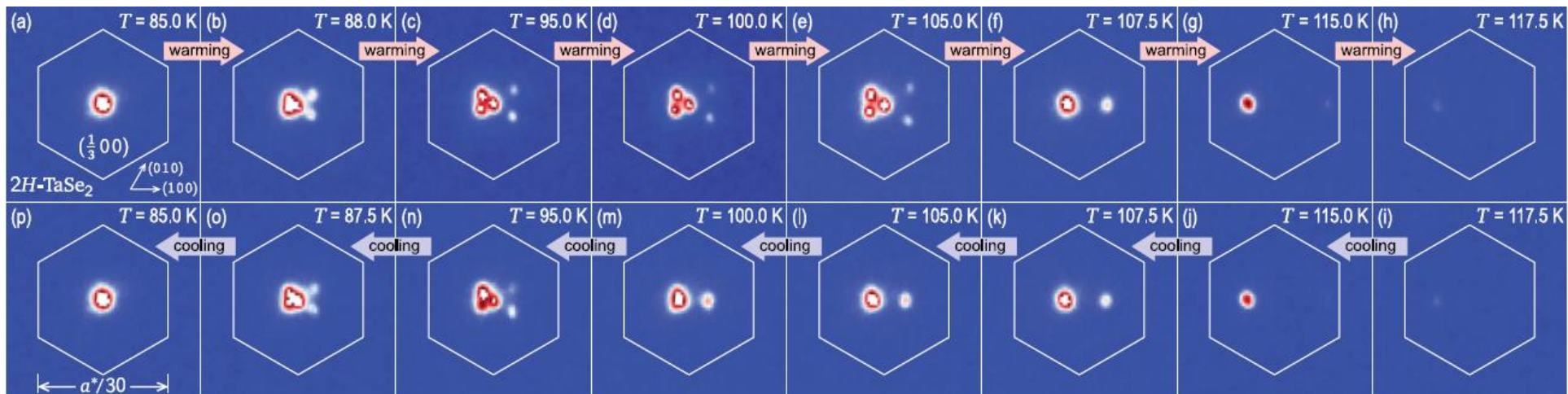
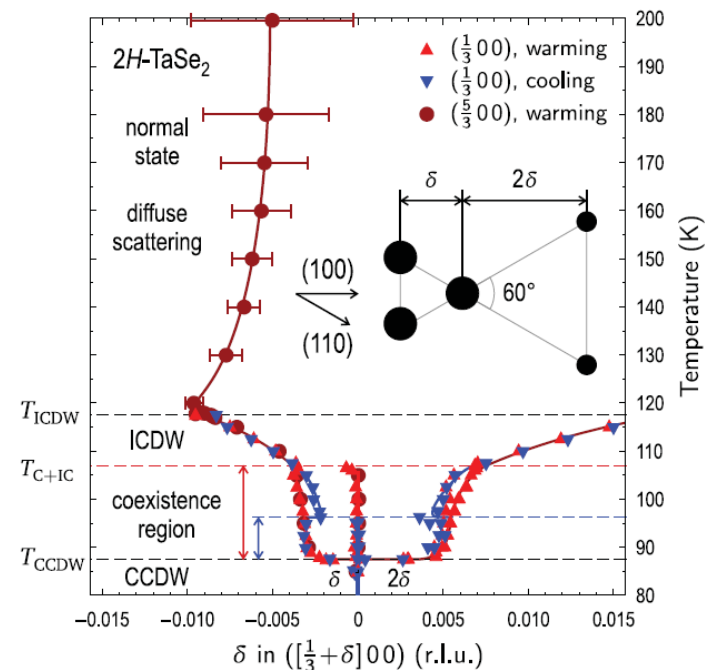
$$\varepsilon_i(k) = -\cos[2\pi(x + Gi)]$$



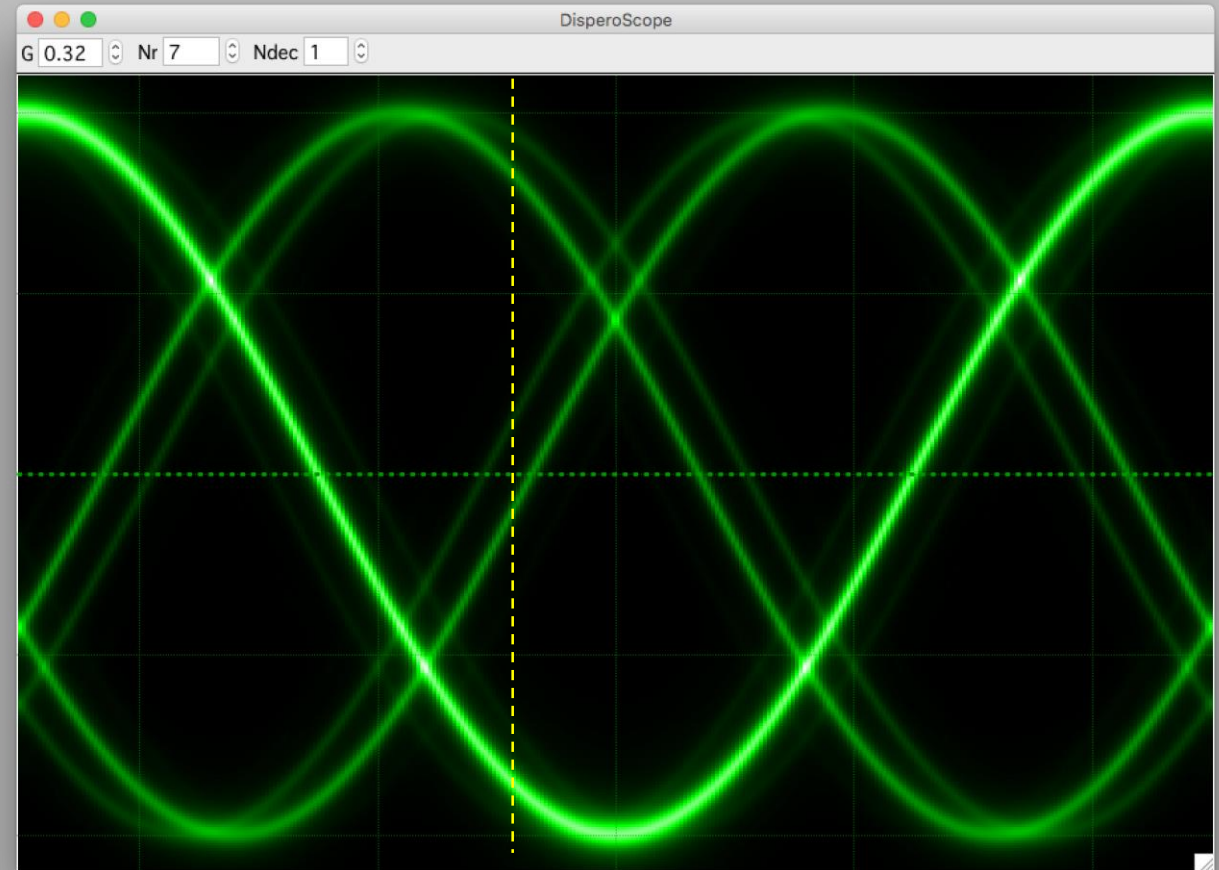
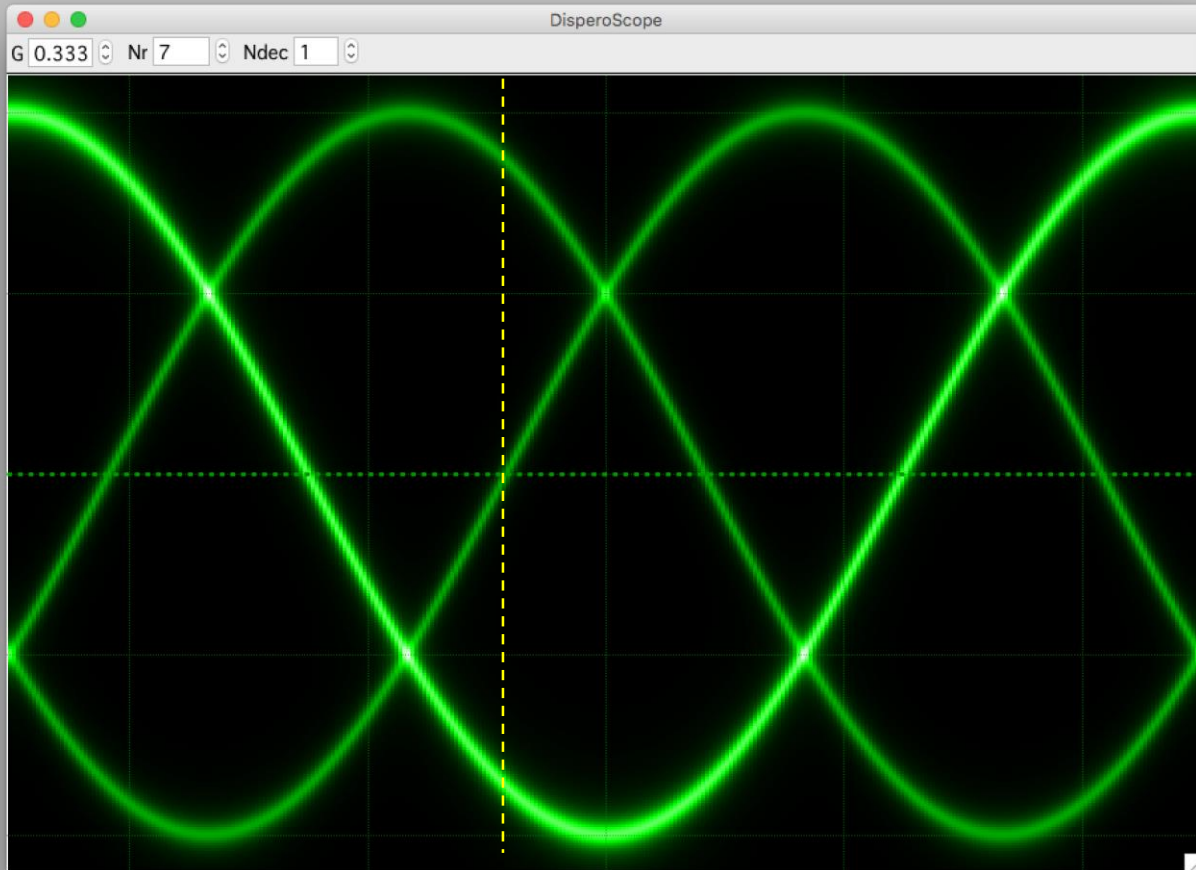


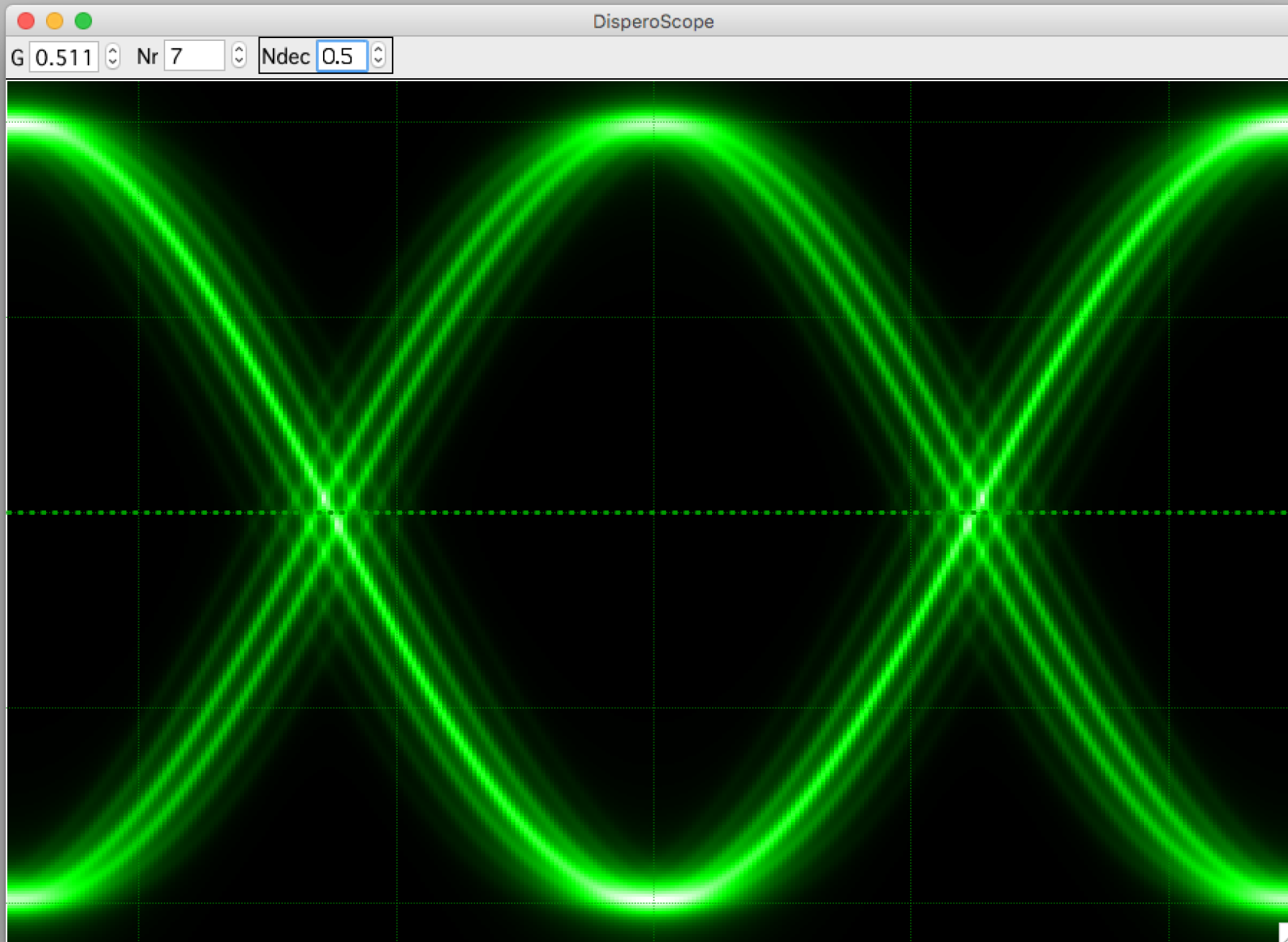
Competing CDW and temperature-dependent nesting in 2H-TaSe₂

Leininger... Inosov, PRB 2011



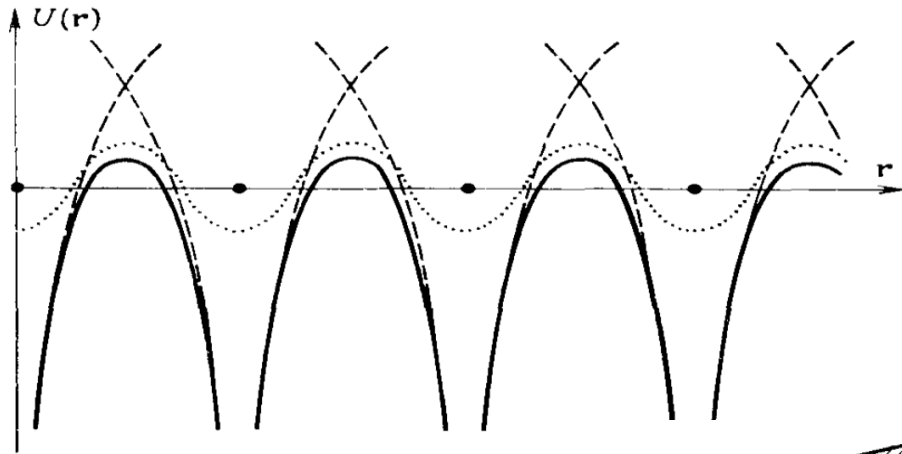
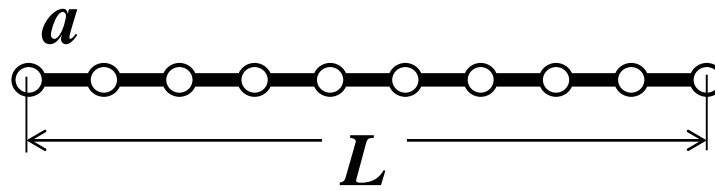
Commensurate vs Incommensurate



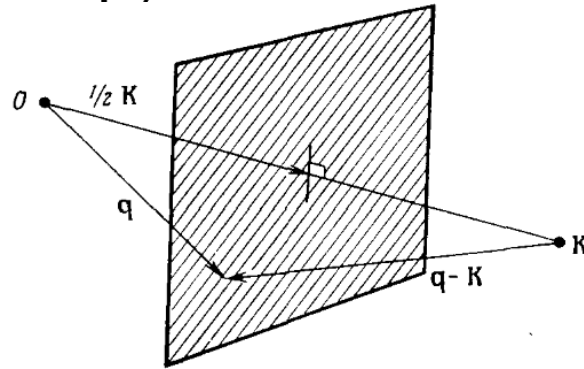


Band gaps

У попередніх лекціях...

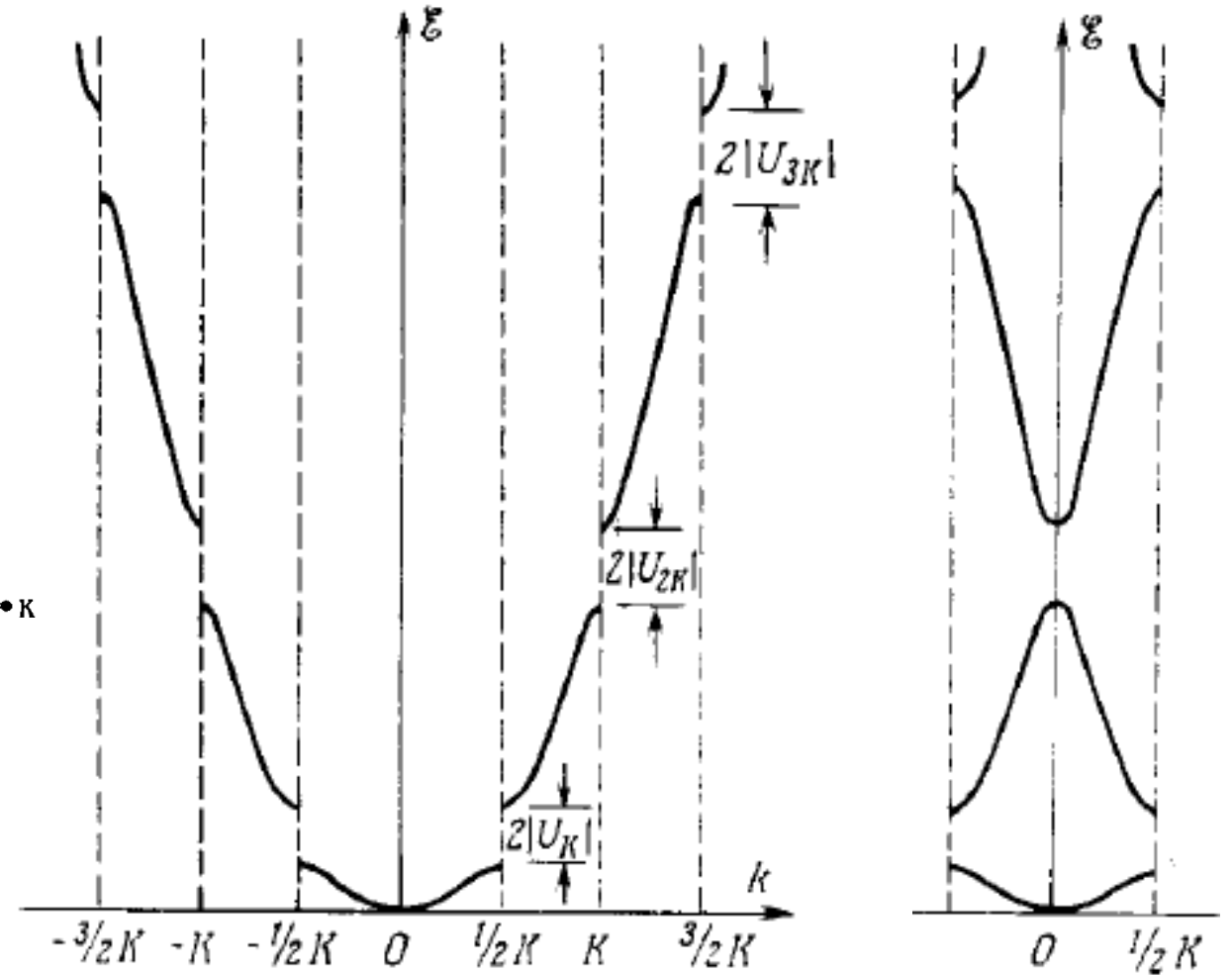


$$\begin{vmatrix} \mathcal{E} - \mathcal{E}_q^0 & -U_K \\ -U_K^* & \mathcal{E} - \mathcal{E}_{q-K}^0 \end{vmatrix} = 0$$



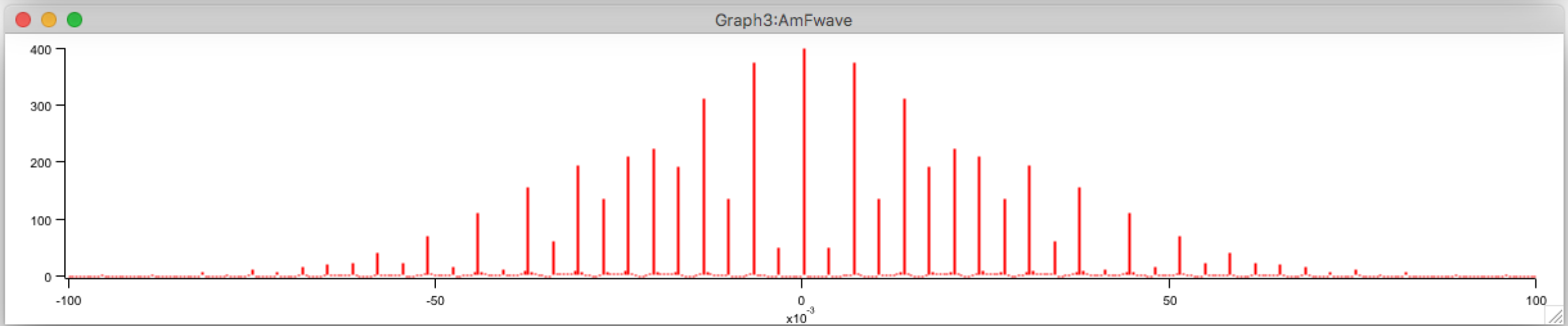
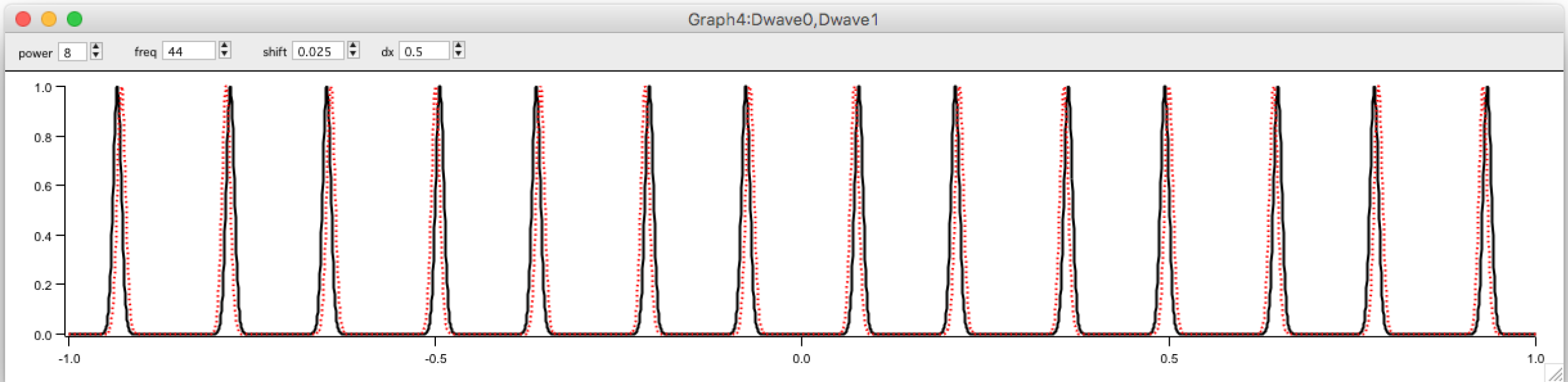
$$(\mathcal{E} - \mathcal{E}_q^0)(\mathcal{E} - \mathcal{E}_{q-K}^0) = |U_K|^2$$

$$\mathcal{E} = \frac{1}{2} (\mathcal{E}_q^0 + \mathcal{E}_{q-K}^0) \pm \left[\left(\frac{\mathcal{E}_q^0 - \mathcal{E}_{q-K}^0}{2} \right)^2 + |U_K|^2 \right]^{1/2}$$

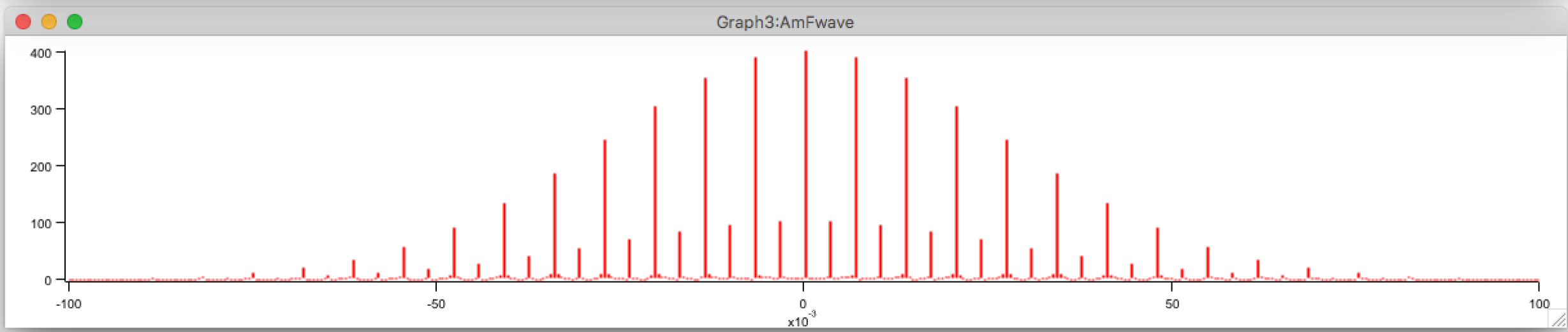
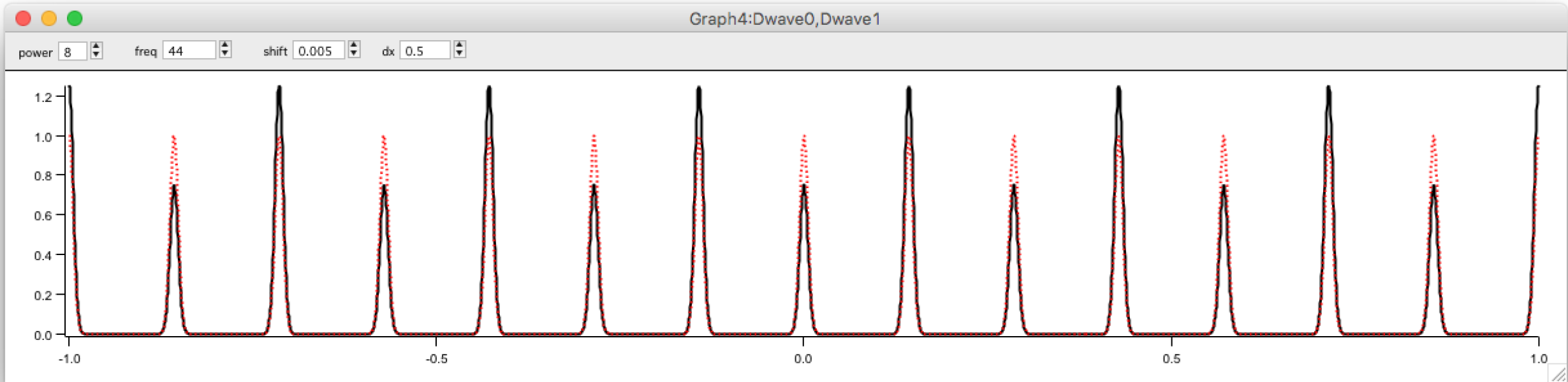
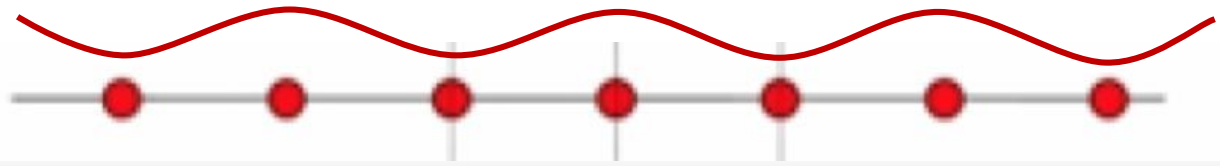


$$K = 2\pi/a$$

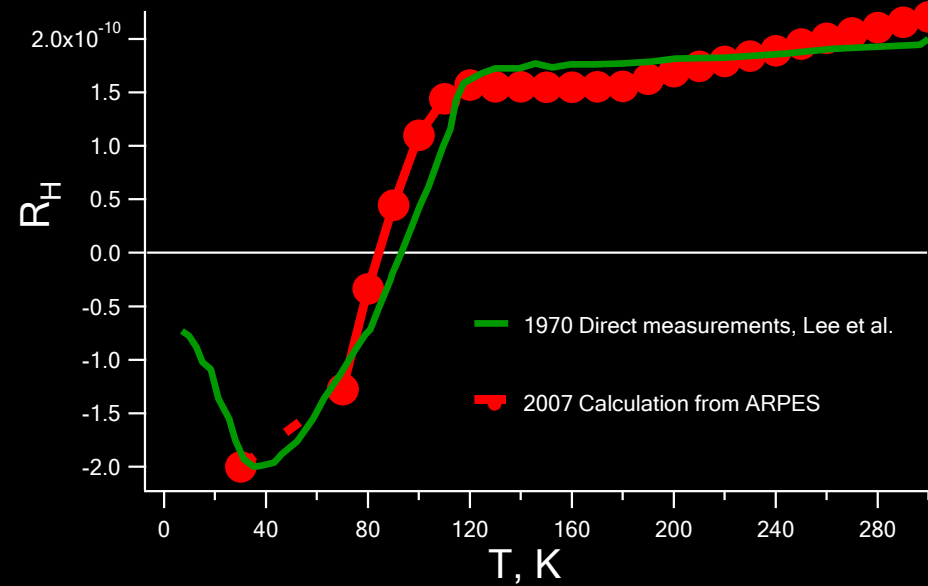
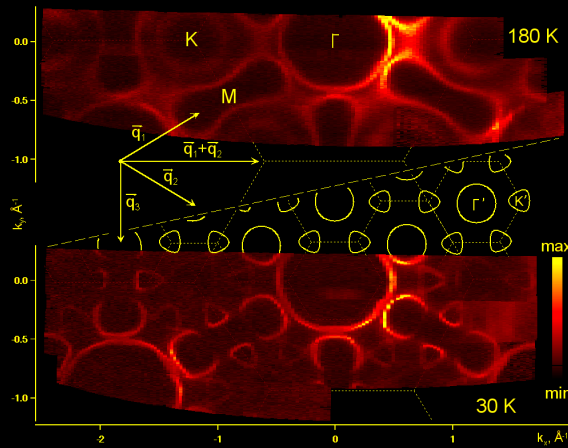
CDW band gaps



CDW band gaps



Hall coefficient of 2H-TaSe₂ from ARPES

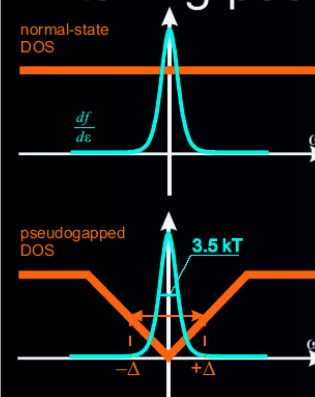


Hall coefficient from electronic structure

$$\tau(\mathbf{k}) = \text{const}$$

$$R_H = \frac{\sigma_{xy}}{H \cdot \sigma_{xx}^2} = \frac{\int \tau(\mathbf{k})^2 \cdot \frac{v_F^2(\mathbf{k})}{\rho(\mathbf{k})} \cdot dk}{\left(\int \tau(\mathbf{k}) \cdot v_F(\mathbf{k}) \cdot dk \right)^2} \downarrow \frac{\int v_F^2(\mathbf{k}) \cdot dk}{\left(\int v_F(\mathbf{k}) \cdot dk \right)^2}$$

taking pseudogap into account

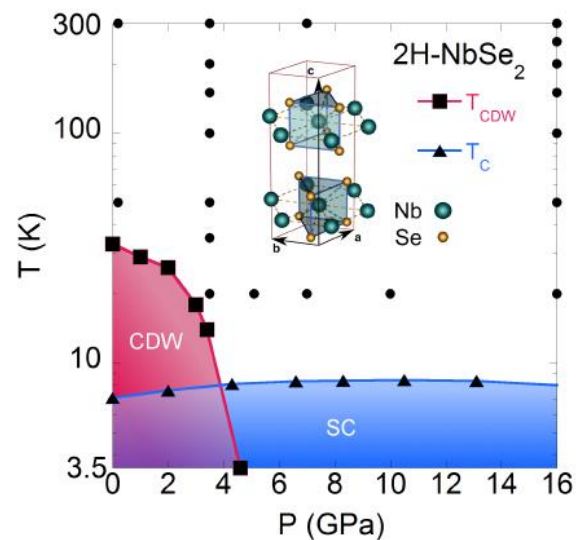
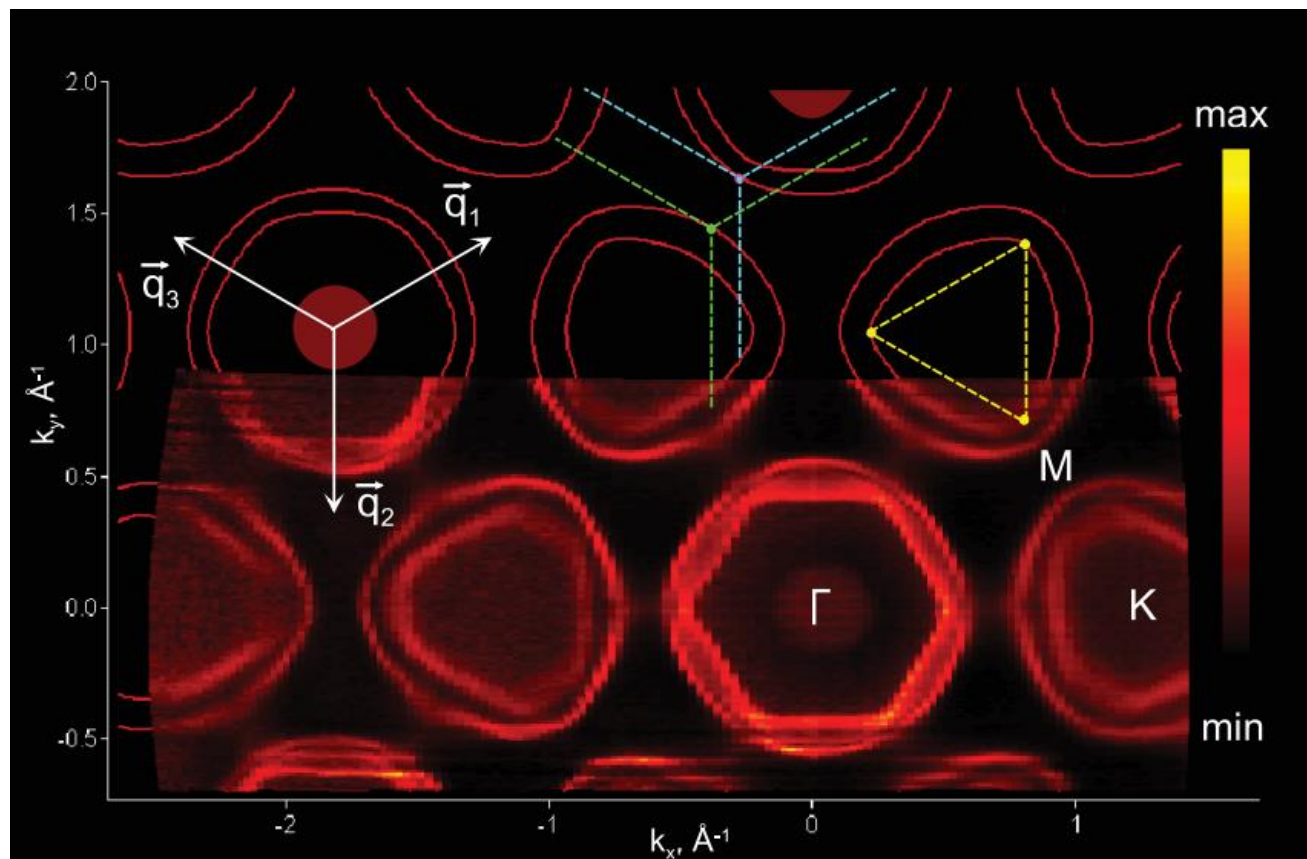


$$D(\mathbf{k}) = - \int_{-\infty}^{\infty} \frac{df}{d\varepsilon} \cdot A(\varepsilon, \mathbf{k}) \cdot d\varepsilon \leq 1$$

$$\sigma_{xy} \propto \int D(\mathbf{k}) \cdot \frac{\tau^2(\mathbf{k}) \cdot v_F^2(\mathbf{k})}{\rho(\mathbf{k})} \cdot dk$$

Two Energy Gaps and Fermi-Surface “Arcs” in NbSe₂

S. V. Borisenko,¹ A. A. Kordyuk,¹ V. B. Zabolotnyy,¹ D. S. Inosov,¹ D. Evtushinsky,¹ B. Büchner,¹ A. N. Yaresko,²
A. Varykhalov,³ R. Follath,³ W. Eberhardt,³ L. Patthey,⁴ and H. Berger⁵



Leroux PRB 2015

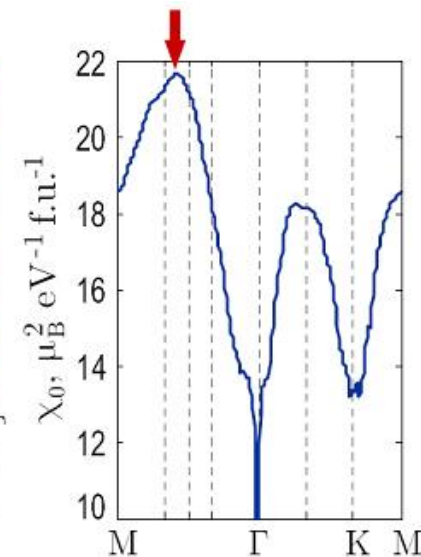
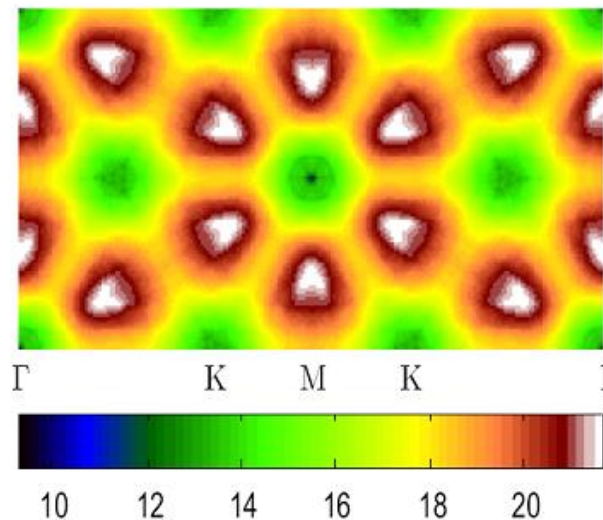
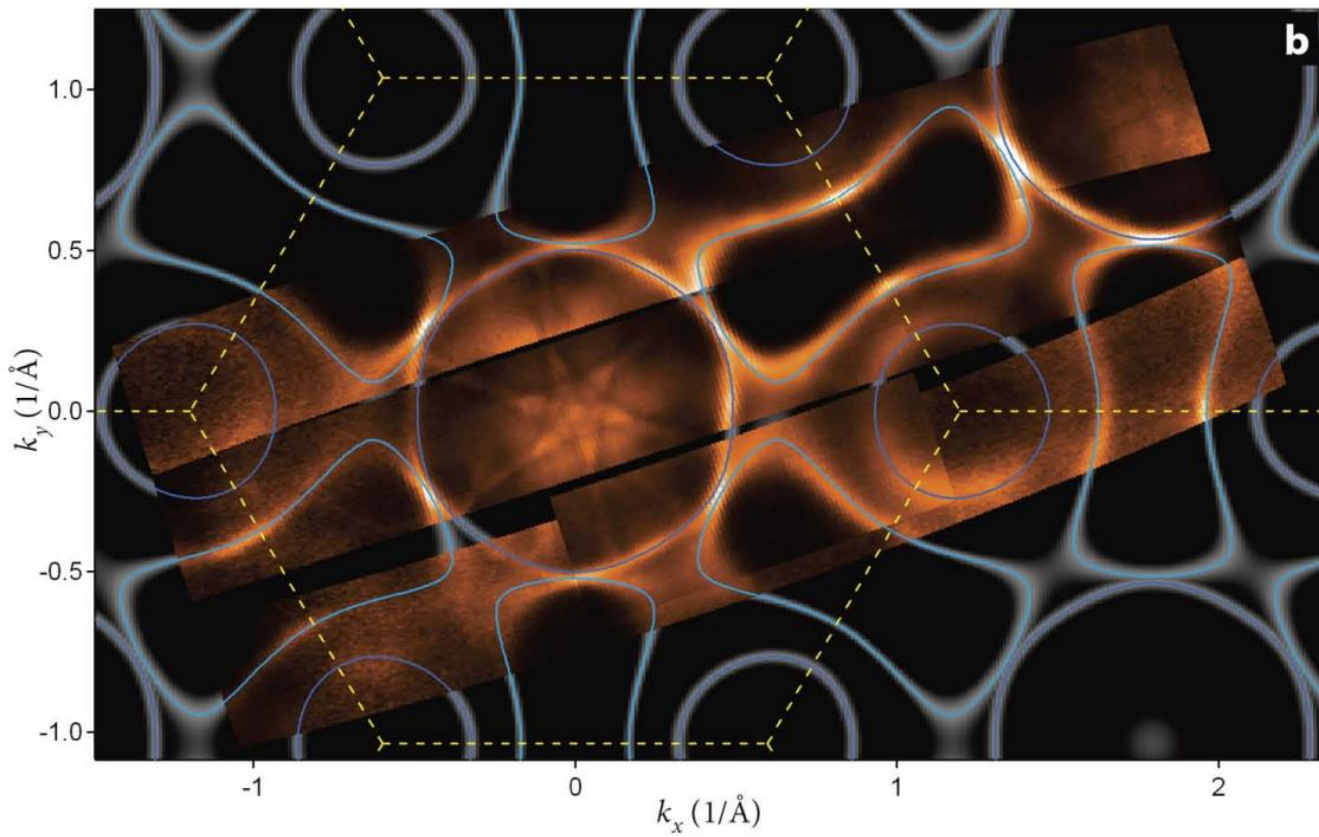
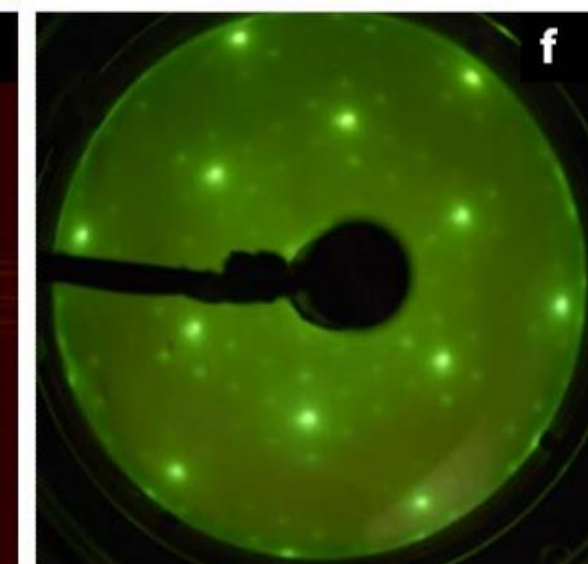
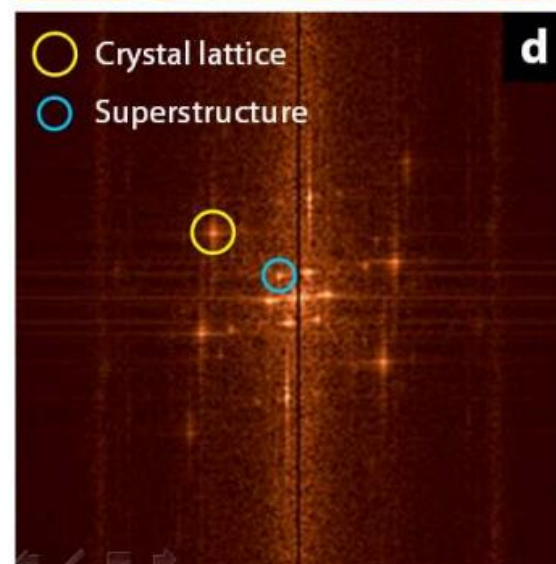
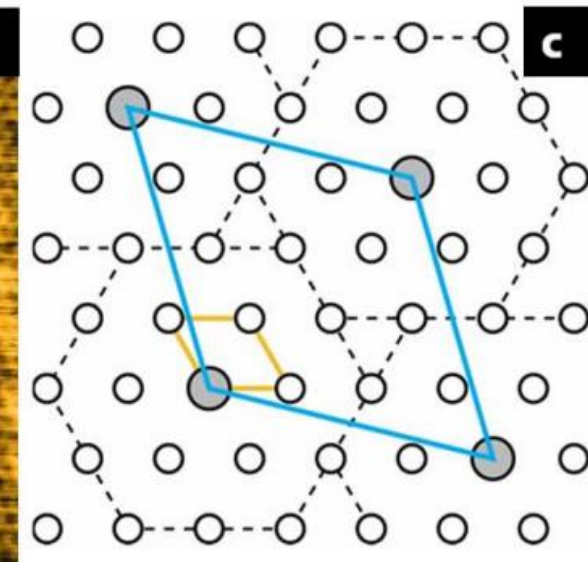
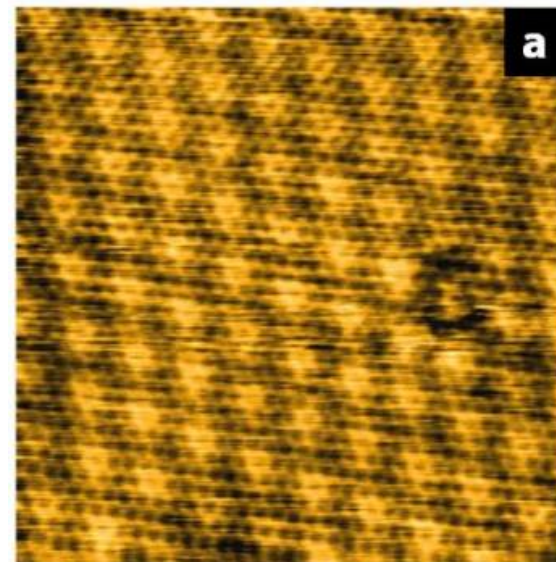


Figure S2. Real part of the Lindhard function at $\omega \rightarrow 0$ as a function of momentum and corresponding profile along high-symmetry directions, with the dominant nesting vector marked by the red arrow. The same vectors can be seen in left panel as white spots.



Cu-intercalated 2H-TaSe2
 -> 2Hb-TaSe2



Quasicrystals

Квазікристал [ред. | ред. код]

Матеріал з Вікіпедії — вільної енциклопедії.

Квазікристал — це **тверде тіло**, атоми якого впорядковані так, що не утворюють кристалічної ґратки (тобто ця структура не є періодичною, позбавлена **трансляційної симетрії**), але в той же час можуть **когерентно** розсіювати випромінювання.

Найважливішою рисою квазікристалів є те, що вони дають чіткі **бреґґівські піки** при **дифракції рентгенівських променів і електронів**, причому **осі симетрії** цих піків мають заборонені для кристалів порядки, наприклад 5-ий. В загальному ж випадку неперіодична структура (наприклад, аморфне тіло, рідина тощо), не обов'язково дає чіткі брегґівські піки.

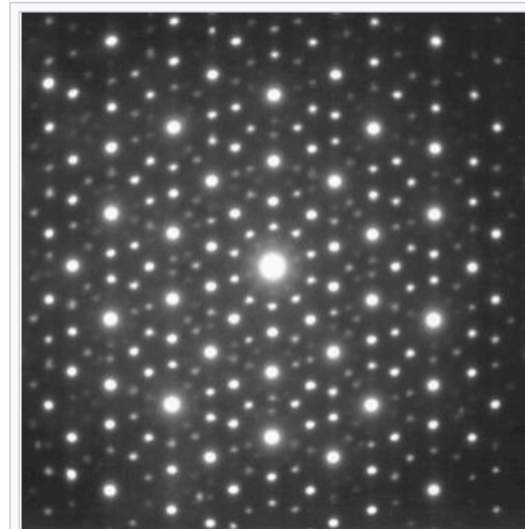
Є два типи квазікристалів: 1) структура періодична по одній осі, а у площині перпендикулярній до цієї осі — квазікристалічна; 2) структура квазікристалічна в усіх трьох напрямках.

Здебільшого квазікристали утворюються при швидкому охолодженні **розплавлених сплавів металів** (Al-Li-Cu, Al-Mn-Si, Al-Ni-Co, Al-Pd-Mn, Al-Cu-Fe, Al-Cu-V, Cd-Yb, Ti-Zr-Na, Zn-Mg-Ho, Zn-Mg-Sc, In-Ag-Yb, Pd-U-Si тощо), і є нестабільними, однак виявлені також стабільні квазікристалічні речовини.

Історія [ред. | ред. код]

Математично можливість заповнення простору кількома простими комірками з утворенням неперіодичної структури відкрив у **1970-их Роджер Пенроуз**.

Квазікристали були відкриті в **1984 році Даном Шехтманом**.



Дифракційна картина розсіяння електронів на ікосаедричній структурі квазікристалу Zn-Mg-Ho. Видно 10 точок по колу.

Деякі приклади нерекурсивної математики

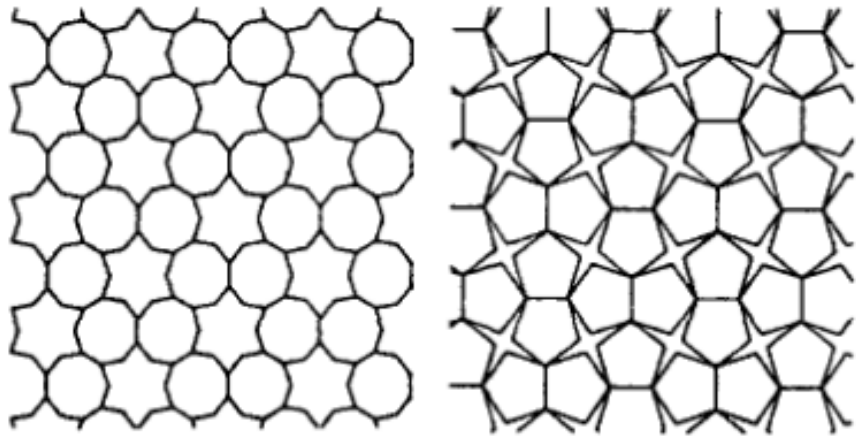


Рис. 4.7. Два примера периодического замощения плоскости фигурами двух форм

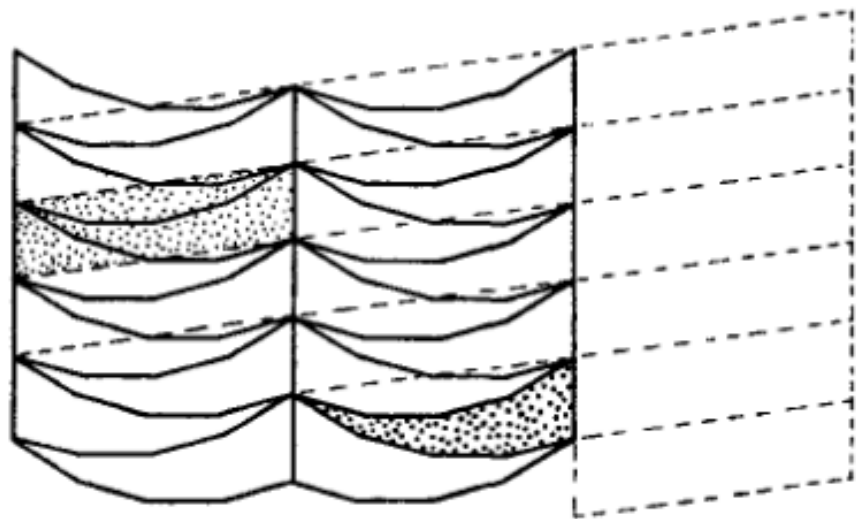


Рис. 4.8. Периодическое замощение и его параллелограмм периодов

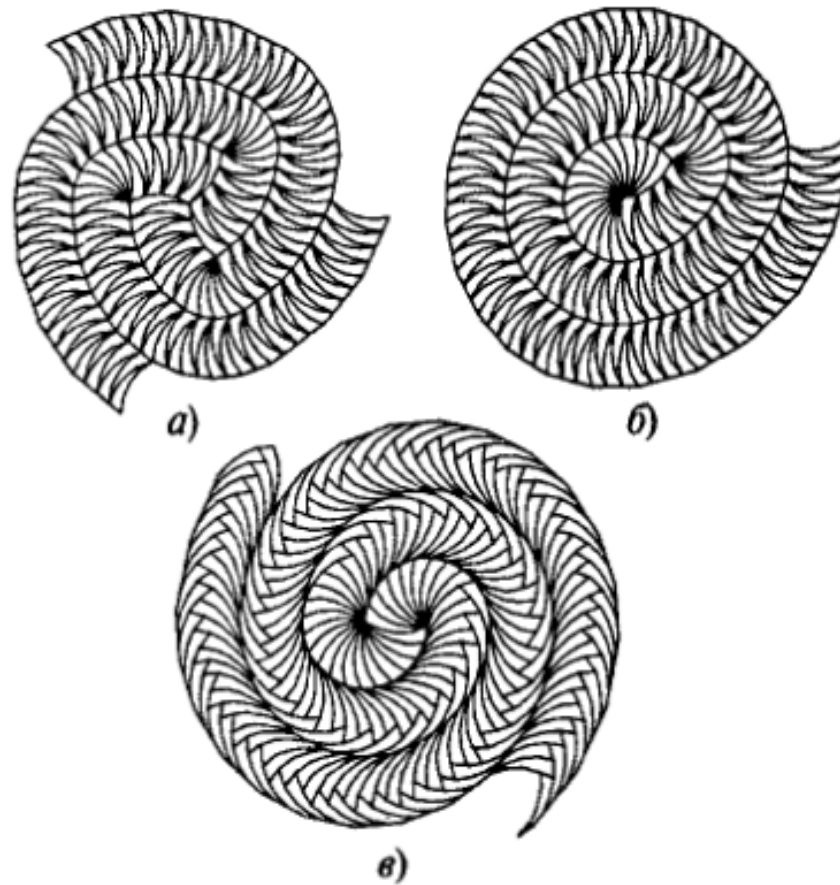
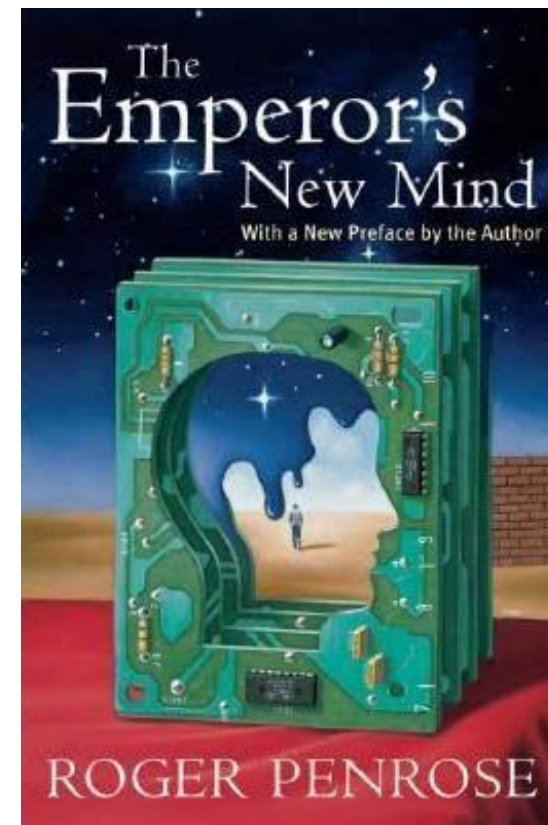


Рис. 4.9. Три неперидических «спиральных» замощения из таких же «универсальных» плиток, как и на рис. 4.8

[Пенроуз Р. Новый ум короля.djvu](http://penrose.p.novyy.um.korolya.djvu)



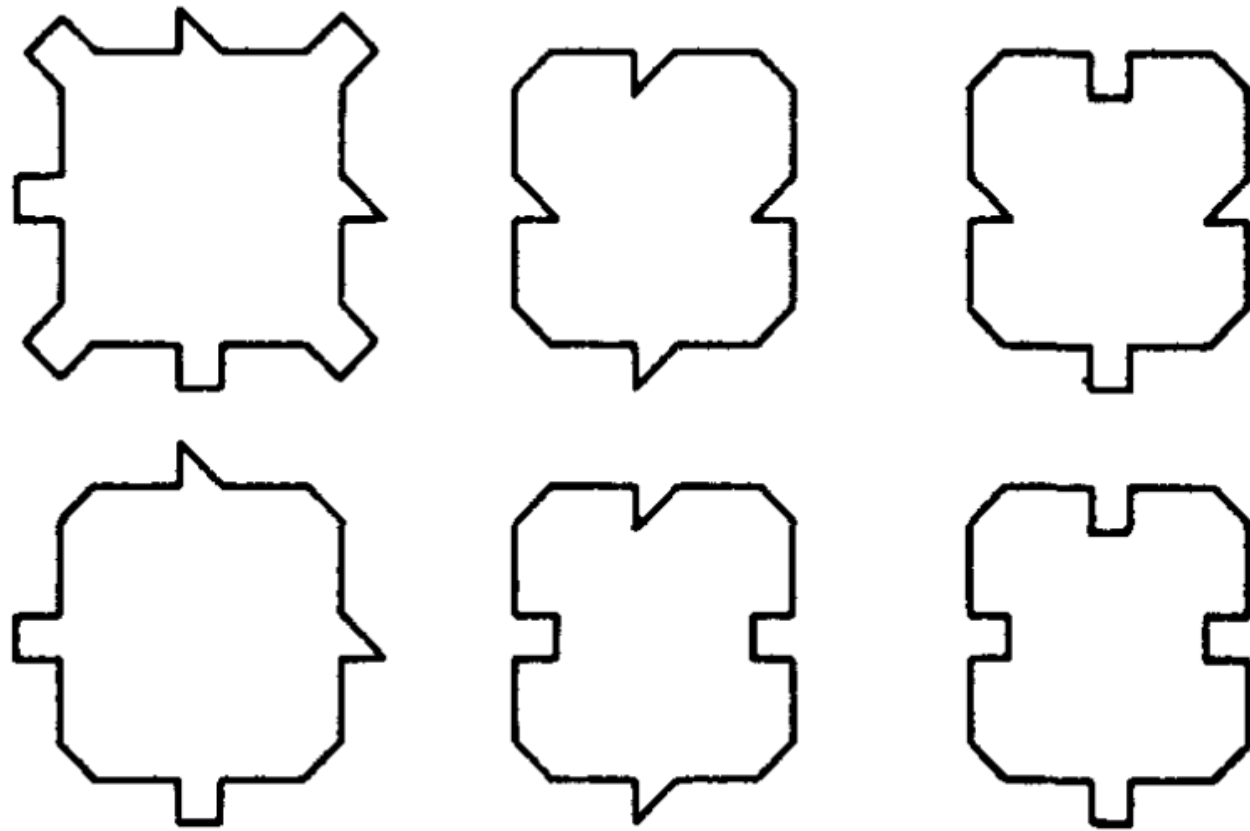
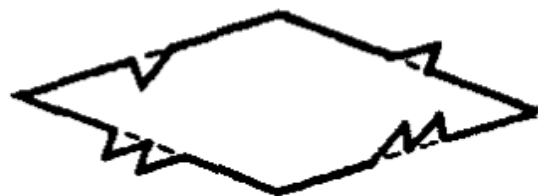
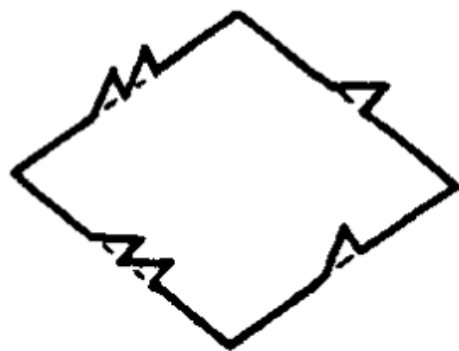
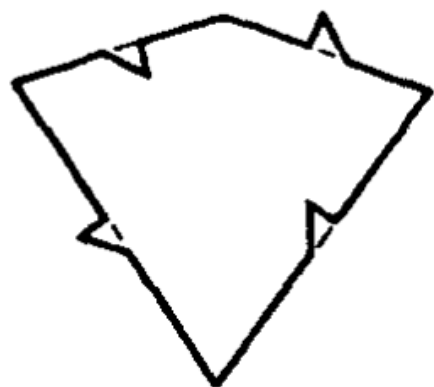


Рис. 4.10. Набор Рафаэля Робинсона из шести плиток, который покрывает плоскость только непериодически



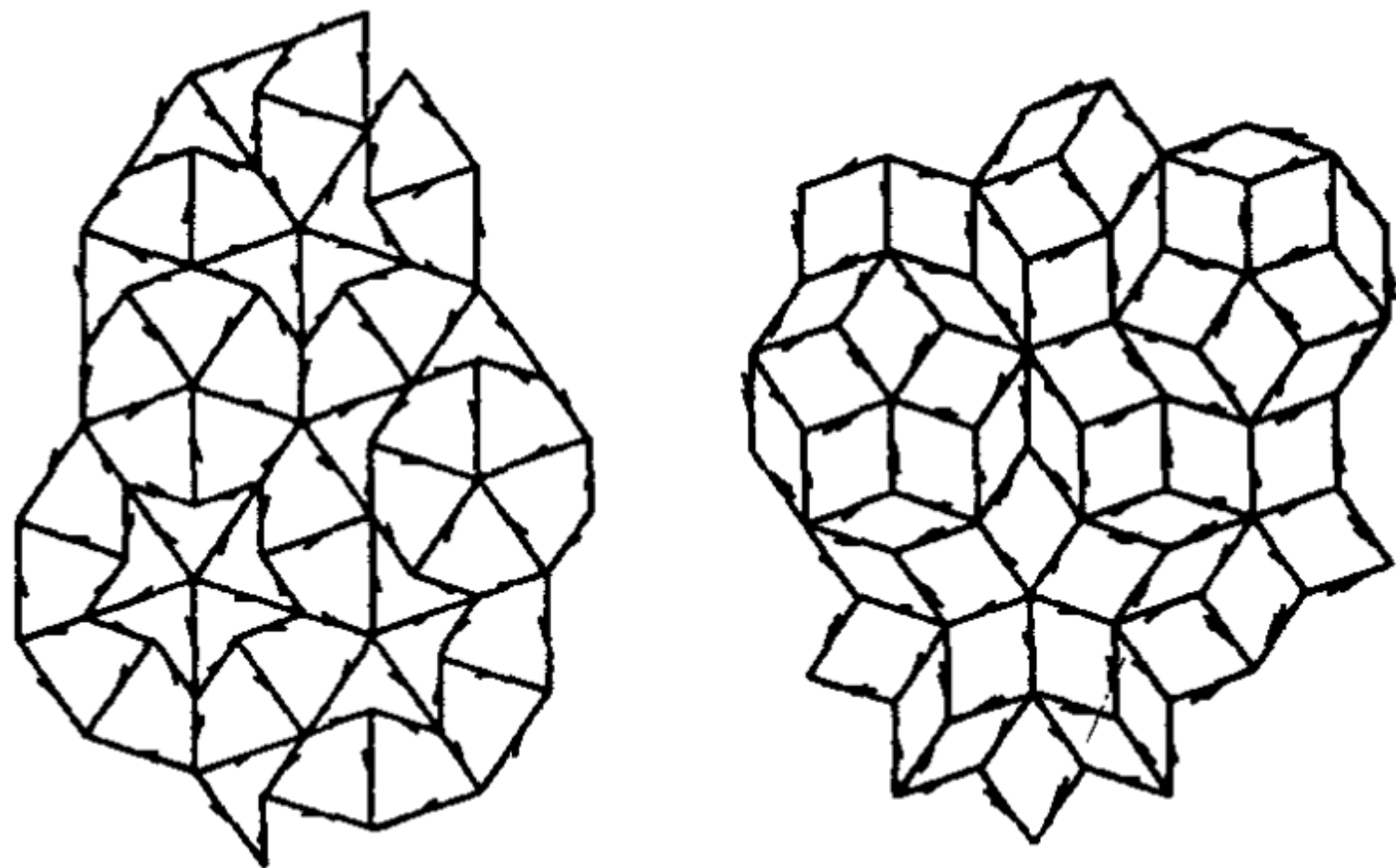
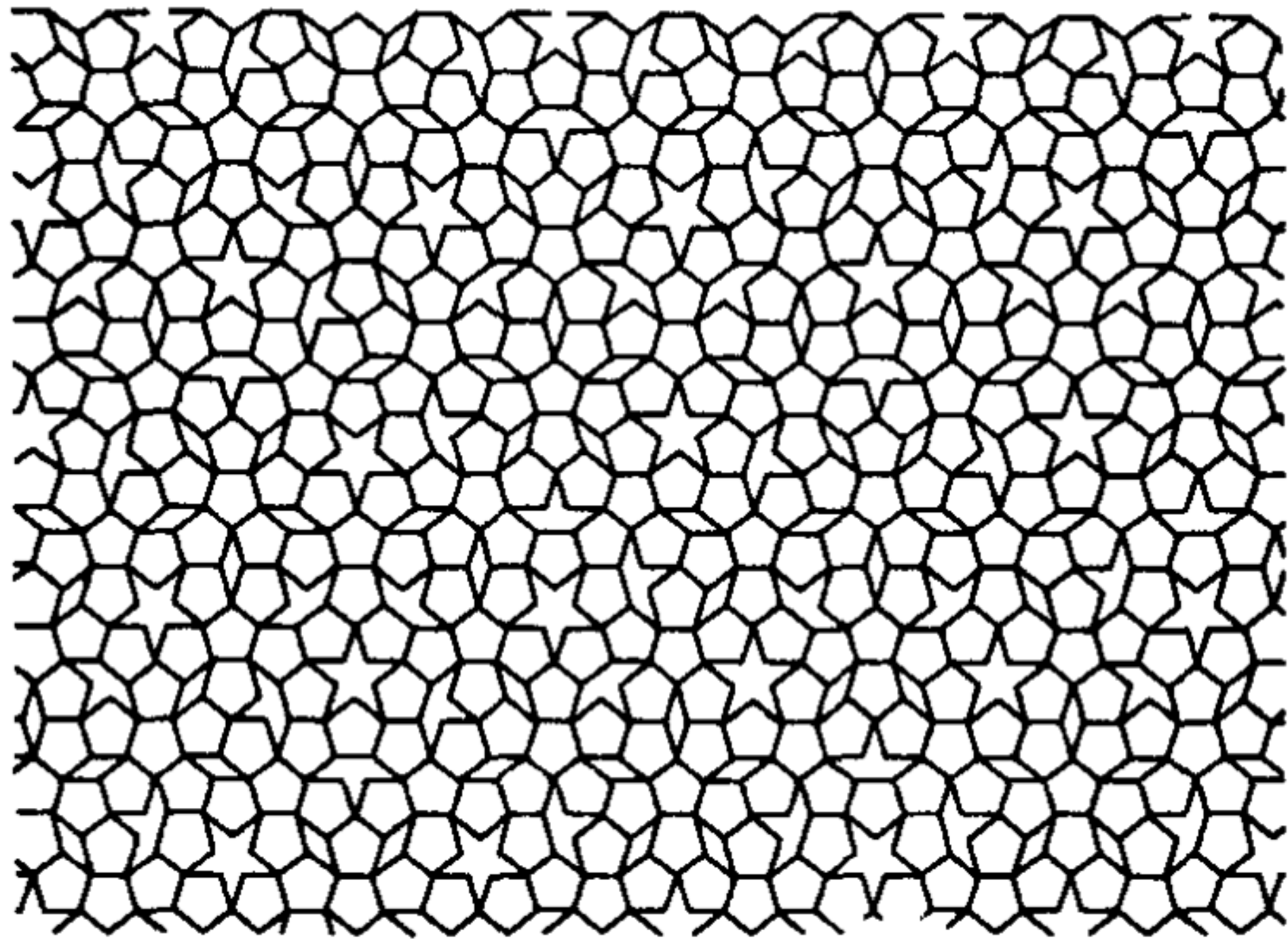


Рис. 4.12. Две пары плиток, которые покрывают плоскость только неперiodически («плитки Пенроуза»). Также показано замощение плоскости каждой из этих пар



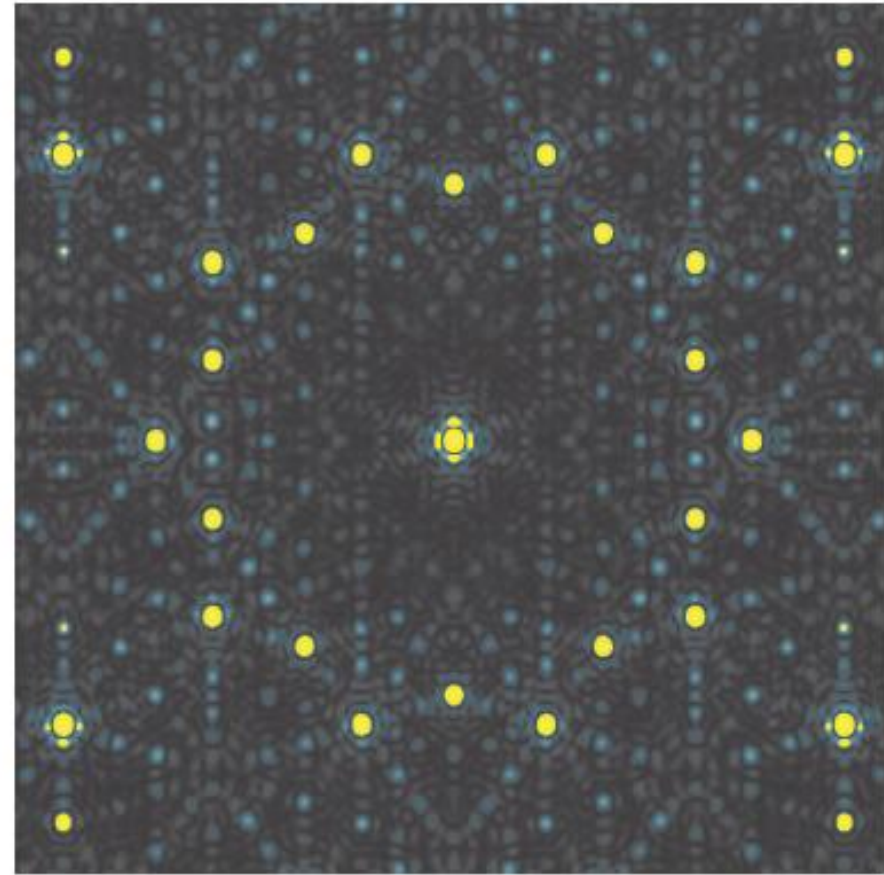
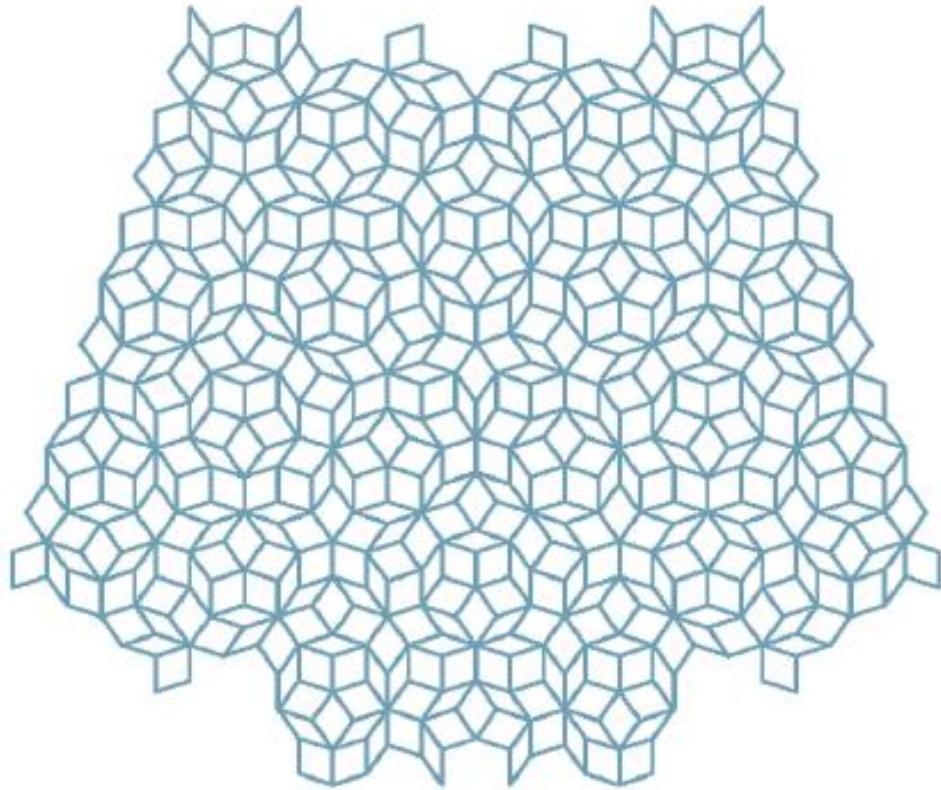
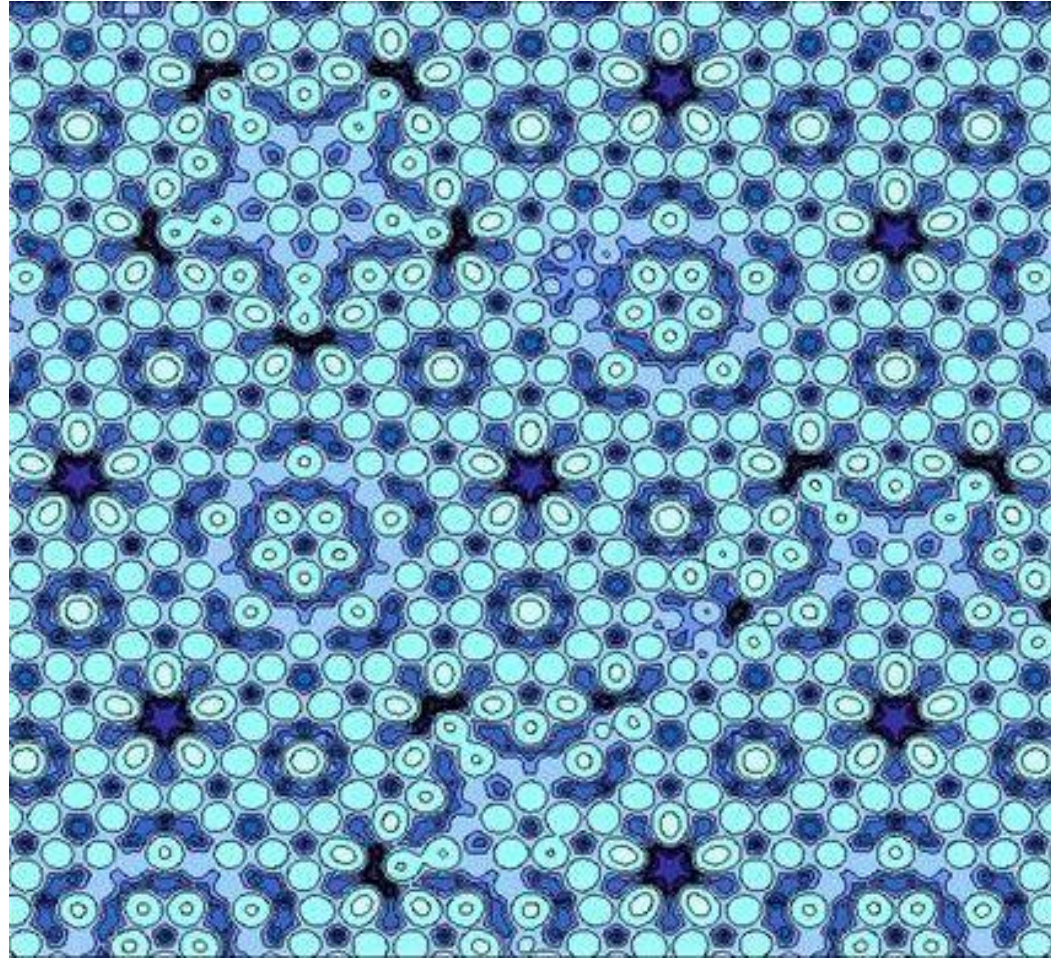
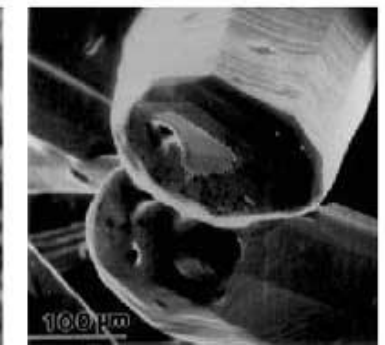
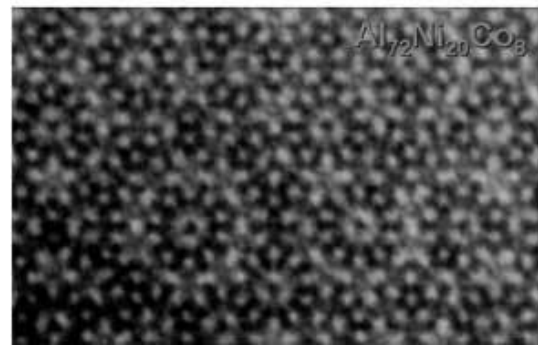
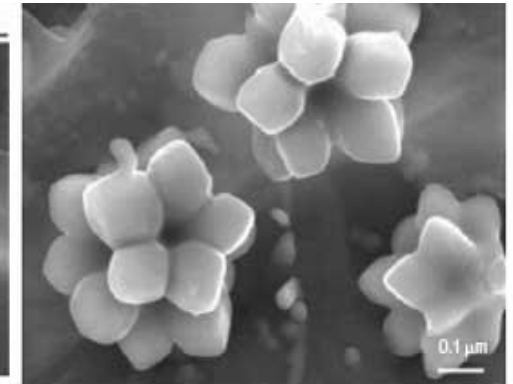
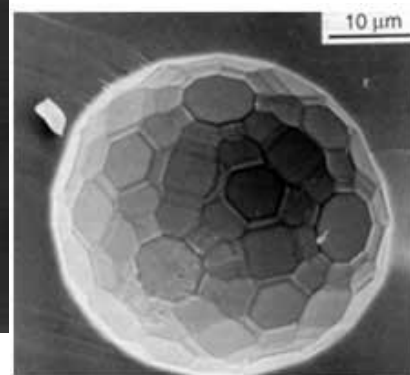
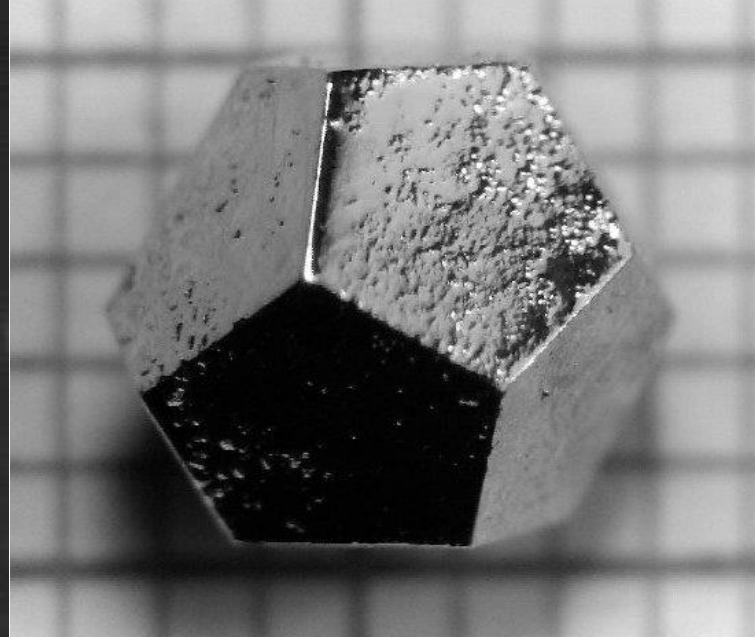
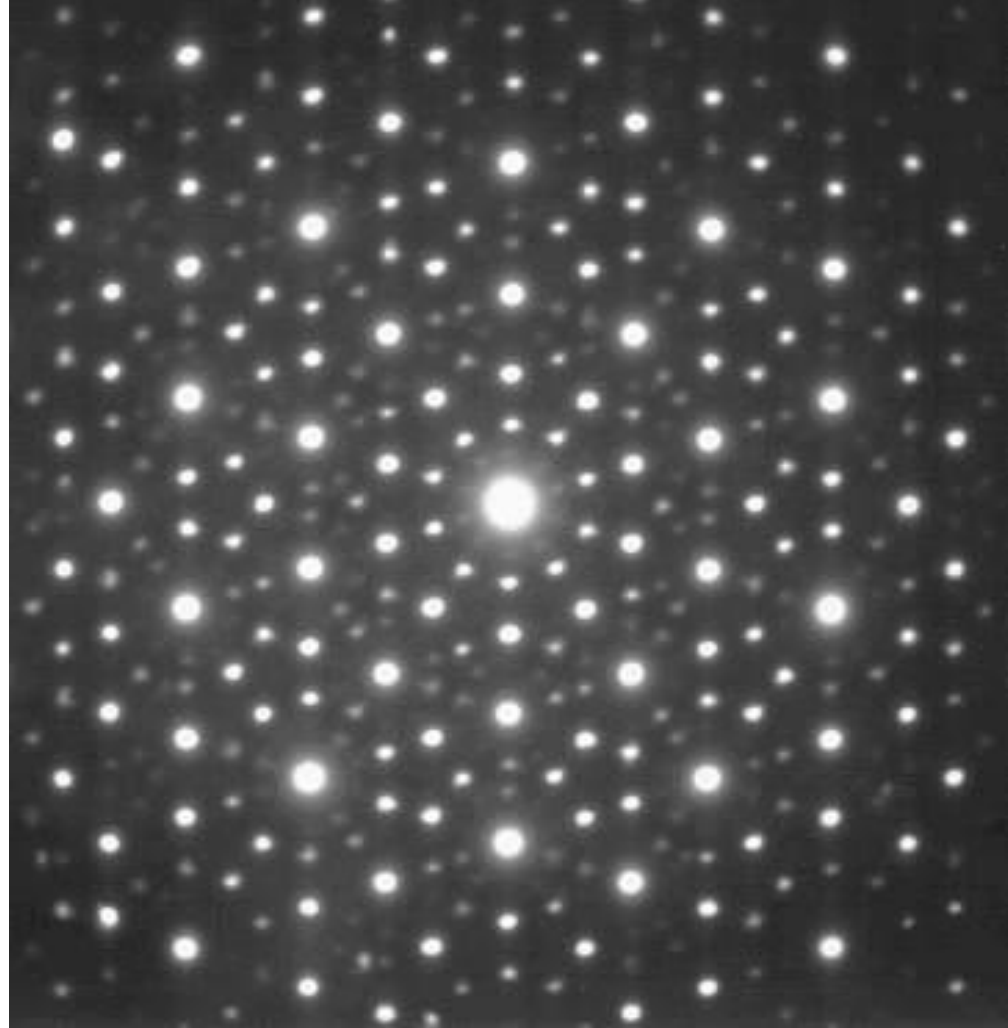


Figure 1. (a). A patch of a Penrose tiling. (b). The diffraction diagram of the vertex set V of (a) is essentially discrete; thus F is an aperiodic crystal, according to the new definition.



Atomic model of an aluminium-palladium-manganese (Al-Pd-Mn) quasicrystal surface.



Дифракційна картина розсіяння електронів на ікосаедричній структурі квазікристалу Zn-Mg-No. Видно 10 точок по колу.

